CONTRACT AF81(852)-833

7 MAY, 1968

679565

FINAL SCIENTIFIC REPORT

(IN TWO VOLUMES)

MULTILAYER FILTERS FOR THE REGION 0.8 TO 100 MICRONS

S. D. SMITH

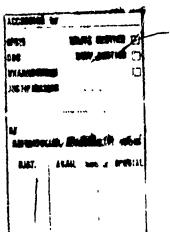
J. S. SEELEY

VOLUME 2-ILLUSTRATIONS



UNIVERSITY OF READING READING, ENGLAND

THIS DOCUMENT HAS BEEN APPROVED FOR PUBLIC RELEASE AND SALE; ITS
DISTRIBUTION IS UNLIMITED



AVAILABILITY NOTICE

Qualified requestors may obtain additional copies from the Defense Documentation Centre: all others should apply to the Clearinghouse for Federal Scientific and Technical Information.

AFCRL-68-

CONTRACT AF 61(052)-833

7th MAY 1968

FINAL SCIENTIFIC REPORT

MULTILAYER FILTERS FOR THE REGION 0.8 TO 100 MICRONS

1st NOVEMBER 1964 - 7th MAY 1968

S.D. SMITH*

J.S. SEELEY[†]

* DEPT. OF PHYSICS

DEPT. OF APPLIED PHYSICAL SCIENCES

UNIVERSITY OF READING READING, ENGLAND.

THIS DOCUMENT HAS BEEN APPROVED FOR PUBLIC RELEASE AND SALE. ITS DISTRIBUTION & UNLIMITED.

THIS RESEARCH HAS BEEN SPONSORED BY THE AIR FORCE CAMBRIDGE RESEARCH LABORATORIES UNDER CONTRACT AF61(052)-833 THEOUGH THE EUROPEAN OFFICE OF AERO-SPACE RESEARCH, OAR, USAF, AS PART OF THE ADVANCED PROJECTS AGENCY'S PROJECT VELA-UNIFORM.

LIST OF ILLUSTRATIONS

		•
Section 2		
	2.1	Dispersion at an absorption peak
	2.2	Energy gap of IV and III-V semiconductors
Section 3.1		
An September September September September September 34	1.8	Fringe amplitude for a Si substrate
	3.2	PbTe films
	3.3	PbTe film (cooling)
	3.4	Optical thickness of PbTe films
	3.5	Ge films
	3.6	Optical thickness of Ge films
	3.7	ZnS films
	3.8	Optical thickness of ZnS films
	3.9	Si0 films
	3.10	Optical thickness of Si0 films
	3.11	Film of CsI
	3.12	Optical thickness of CsI film
	3.13(€	a)-(j) Shortwave spectra of films of new low-index materials
	3.14	Preliminary results on TlI, TlBr films
	3.15	Preliminary results on CdI, InI films
Section 3.3		
	3.16	High Vapour Pressure deposition method
	3.17	Gas flow deposition method
	3,18	Comparison of ground and polished silicon substrates
	3.19	Polyethylene spectrum
	3.20	Polypropylene spectrum
	3.21	Polystyrene spectrum
	3.22	P. T. F. E. spectrum
	3.23	Melinex spectrum

Section 3.3 contd.

	3.24	Polycarbonate spectrum
	3.25	Mica spectrum
	3.26	Silicon/polyethylene-sandwich spectrum
	3.27	Spectrosil B spectrum
	3.28	Germanium/Spectrosil F. P.
Section 4.1		
	4.1(a) and (b)	Grubb Parsons Balzer-BA500 Plant (Photographs)
	4.2(a) - (c)	Design performance of radiometer filters
	4.3	Arrangement of sources in Grubb Parsons , plant
	4.4	Reflectance monitoring characteristics
	4.5(a) - (b)	PbTe, 2nS deposition temperatures
	4.6	F. P. filter deposited at optimum temperatures
	4.7(a) - (b)	D. H. W. filters, temperature-cycled deposition
	4.8	D. H. W. filter deposited at one temperature
	4.9	Calculated distribution of evaporant
	4.10	Uniformity of F. P. filter
Section 4,2		
	4.11	Transmittance of CsI film
	4.12	Transmittance of thin plate of Spectrosil B
	4.13	Ge/ZnS F. P. filter at 60 µ
	4.14	Ge/ZnS D. H. W. filter at 80 μ
	4.15	Ge/ZnS F. P. filter at 90 μ
	4.16	Ge/ZnS filter by modified deposition
	4.17	2-layer Ge/CsI stack
	4.18	4-layer Ge/CsI stack
	4.19	Ge/CsI F. P. filters at 75 μ

	Section 4.2 contd.		
		4.20	Ge/CsI F. P. filters at 85 µ
		4.21	Blocking filter (including quartz)
		4.22	Longway, transmittance of blocking filter
		4,23	Preliminary lowpass fliter at 50 #
•		4.24	Stop region of 55 m lowbass fixer
		4.25	Lowpass filter with moduled anticeflection
•		4.26	Interferogram of combined F. P. /lowpass filter
	Section 4.3		
		4.28	Shortwave transmittatice of PbTe/ZnS single blocking stack.
		4.29	Longwave transmittance of PbTe/ZnS stack
		4.30	Shortwave transmission of PbTe/CsI stack
		4.31	Longwave transmission of PbTe/CsI stack
		4.32	CsI antireflection at 75 μ
		4.33	CsI antireflection at 85 μ
		4.34	Longwave transmission of PbTe/CsBr stack
		4.35	Shortwave transmission of PbTe/CsBr stack
		4.36	CsBr antireflection
		4.37	Equal-ripple PbTe/ZnS lowpass filter
		4.38	Comparison of antireflection systems on Ge
•	Section 4.4		
•		4.39	Separate collection of PbTe and ZnS from a filter deposition
		4.40	"Annealing" of F. P. filters containing PbTe
		4.41	F. P. filter annealing at various temperatures
		4.42	Annealing time vs temperature-1
		4.43	Calculated F. P. shift vs change in n in PbTe
		4.44	F, P. maximum transmittance vs sin PbTe
			^

4.45

Resistance of PbTe during anneal at 319°C

Section 4.4		
	4.46	Anneal of PbTe in vacuo, nitrogen, air
	4.47	PbTe monolayers with high and low free carrier absorption
	4.48(a)	Dispersion curves for PbTe
	4.48(b)	Reflectance of PbTe monolayer
	.49	Transmission of single mesh
Section 4.5		
	4.50	Finesse of mesh F.P. filters
	4.51	Melinex-spaced mesh F.P. filter
	4.52	Air-spaced improvement of 4.51
	4.53	Mesh D. H. W. filter
	4.54	Mesh filter construction
	4.55	Effect of resolution on measurement of mesh filter
	4.56	Uniformity of mesh filter
	4.57	Mesh F. P. filters at 75, 85, 95μ
	4.58	D. H. W. filter using identical meshes
	4.59	D. H. W. filter using 2 grades of mesh
Section 5. l		
	5.1	Idealised filter characteristics
	5.2	Interface description
	5.ა	$\underline{\mathbf{S}}$ - plane locus and construction
	5.4	Tchebyshev circuit parameters
	5.5	Computed Tchebyshev filters
	5.6	Computed Tchebyshev narrowband filter
Section 5.3		
	5.7	Spectral sensitivity of layers in F.P. filter
	5.8	Refinement of low pass design
	5 9	Refinement of high pass design

•

!

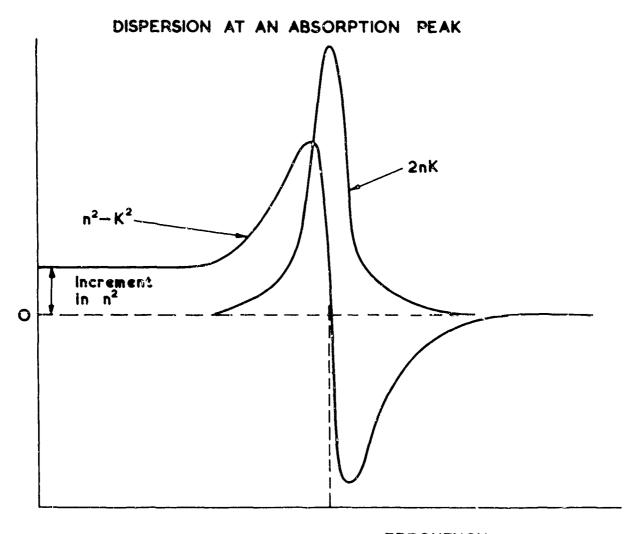
Section 5.4

5.10(a) - (d) F. P. for 2% Standard Deviation in thicknesses
5.11(a) - (d) D. H. W. for 2% Standard Diviation in Thicknesses
5.12 Peak transmittance vs halfwidth, 2%, 1.4% S. D.
5.13 Peak transmittance, halfwidth, vs peak separation in D H. W.
5.14(a) - (d) D. H. W. for 1.4% S. D. in thicknesses
6.15 D. H. W. adjusted by final layer thickness

Section 6

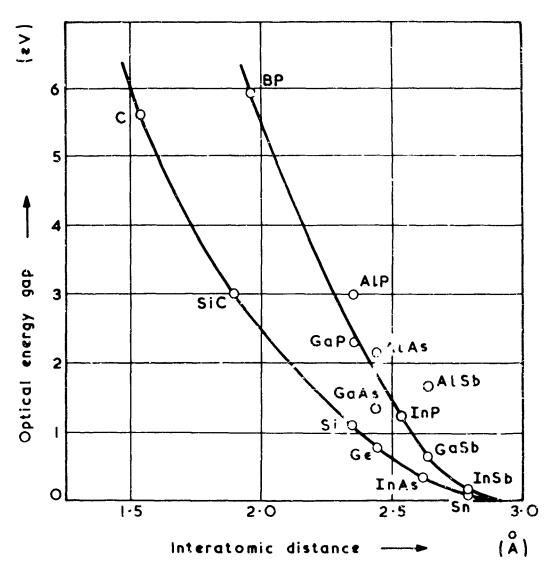
6 1 Long wave bandpass filters

6.2 Long wave lowpass filter.



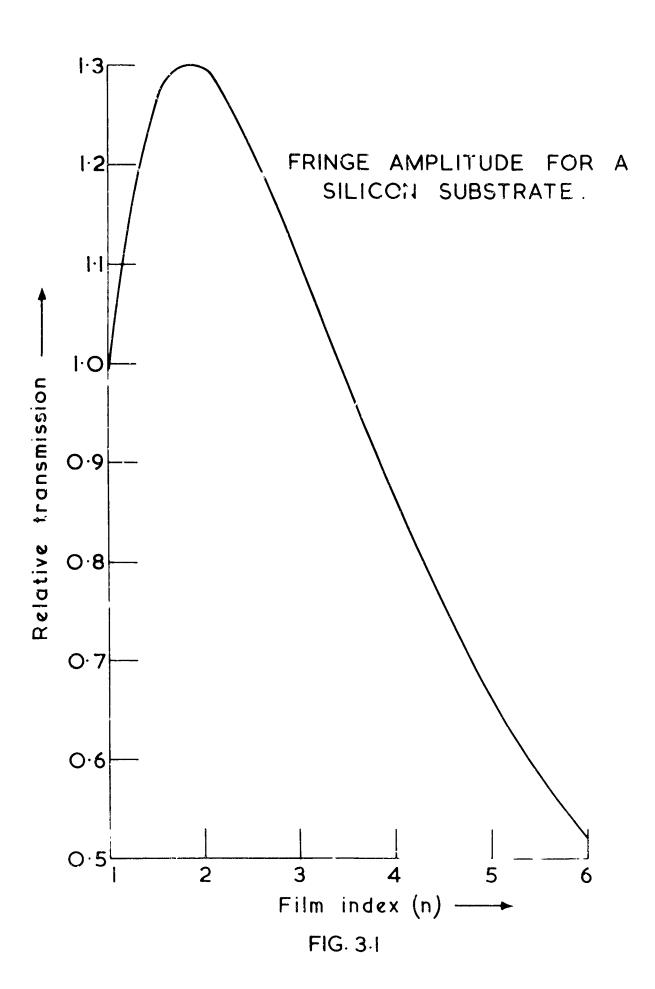
FREQUENCY ----

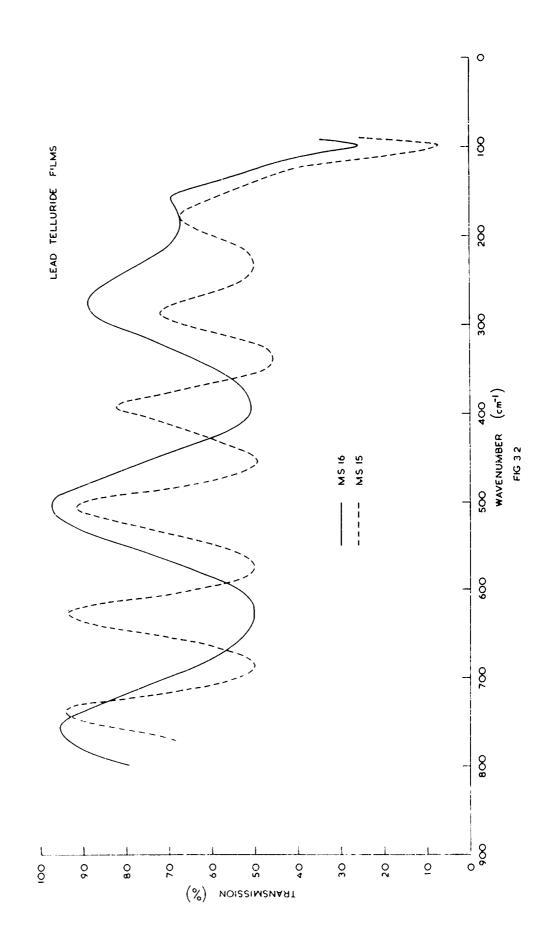
FIG. 2.1

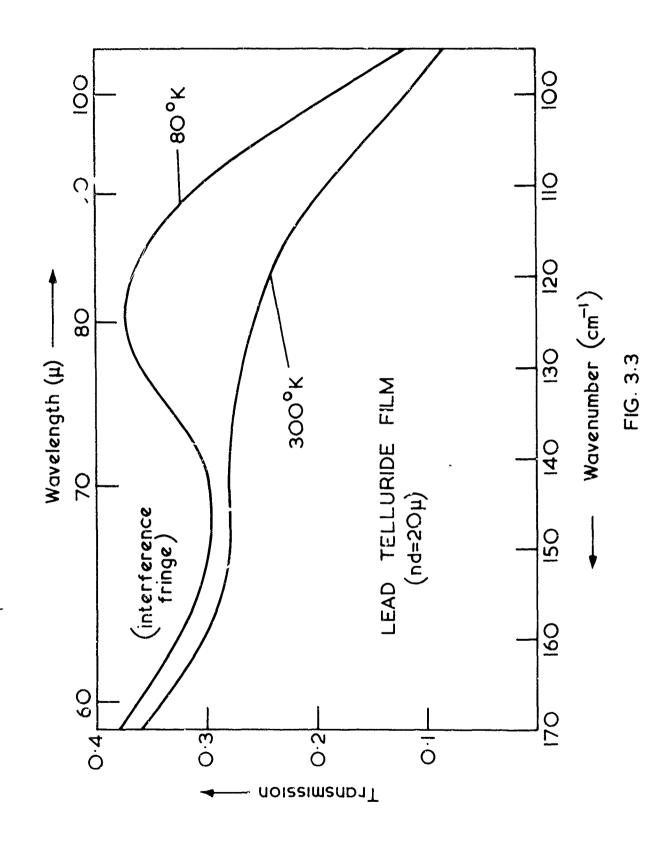


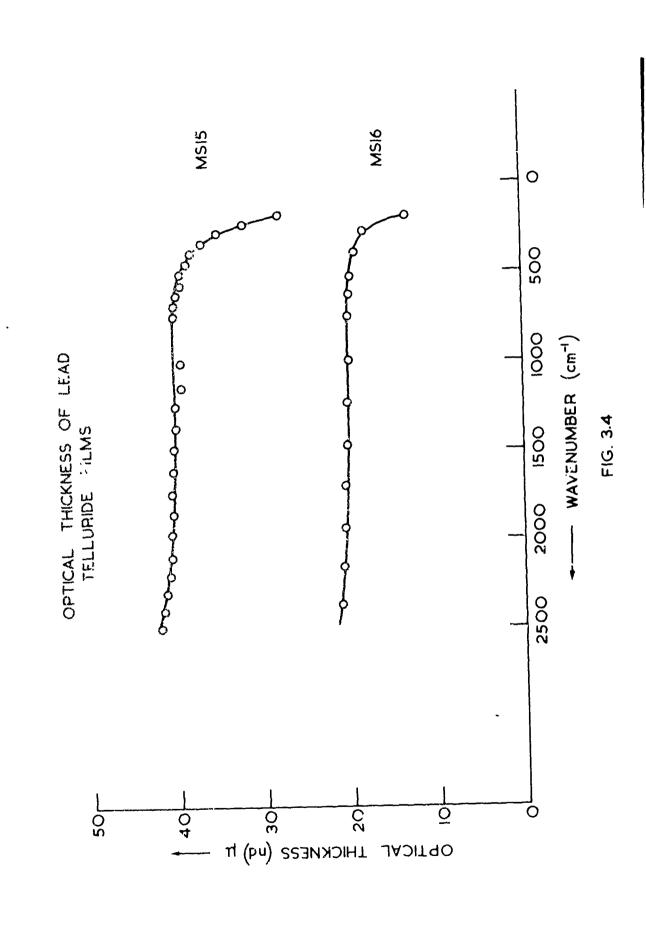
Energy gap of semiconducting Group IV elements and Group III-V compounds of diamond and zinc blende structure

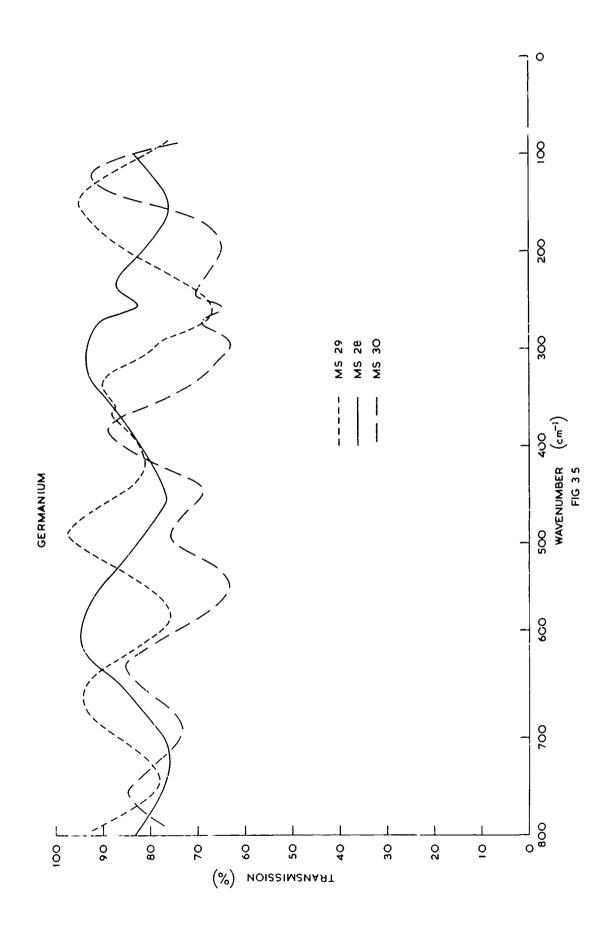
Fig. 2.2











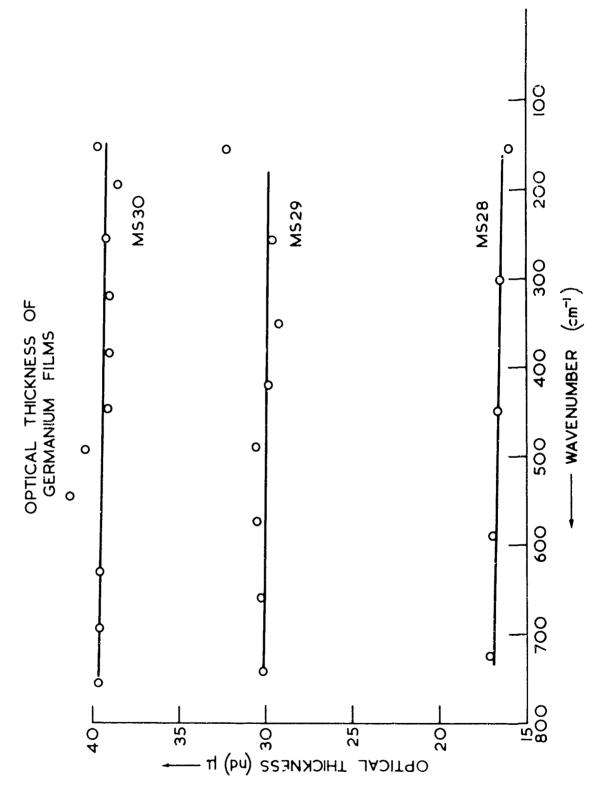
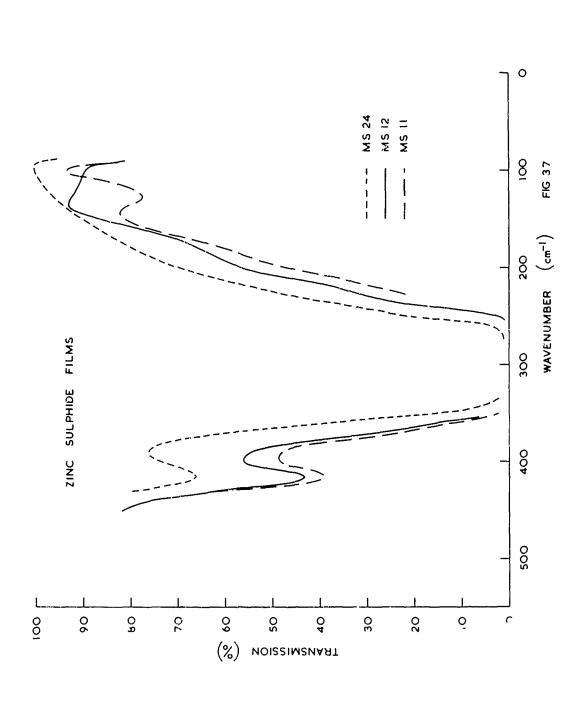
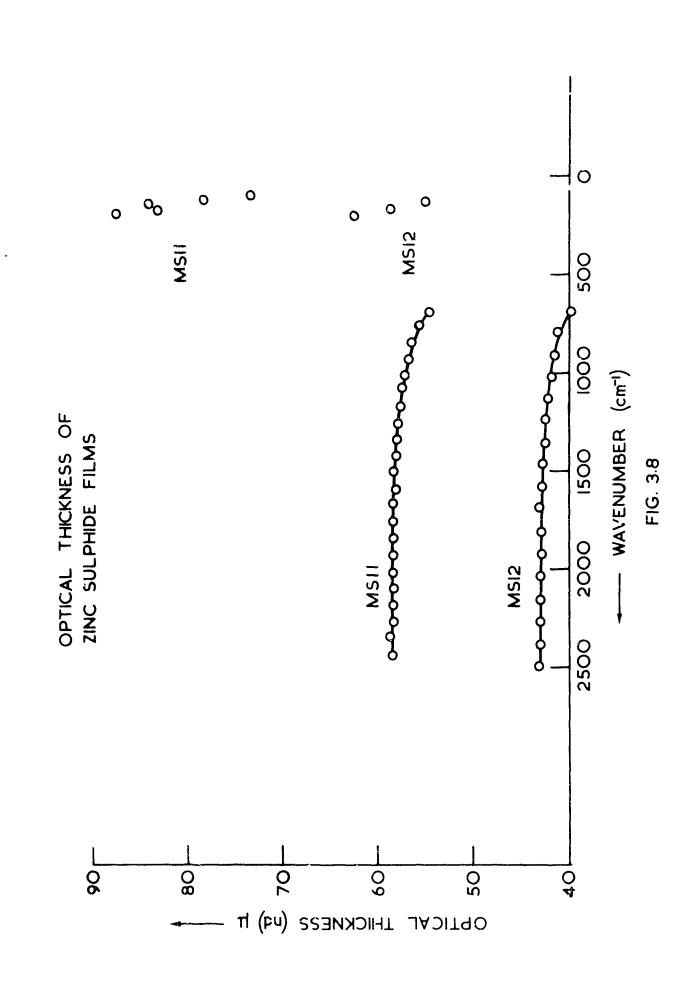
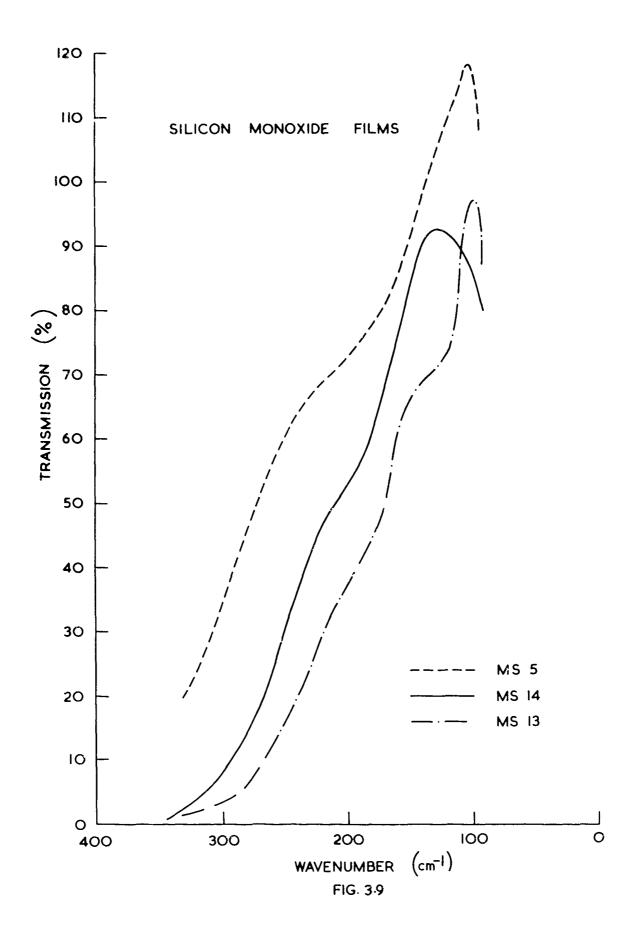
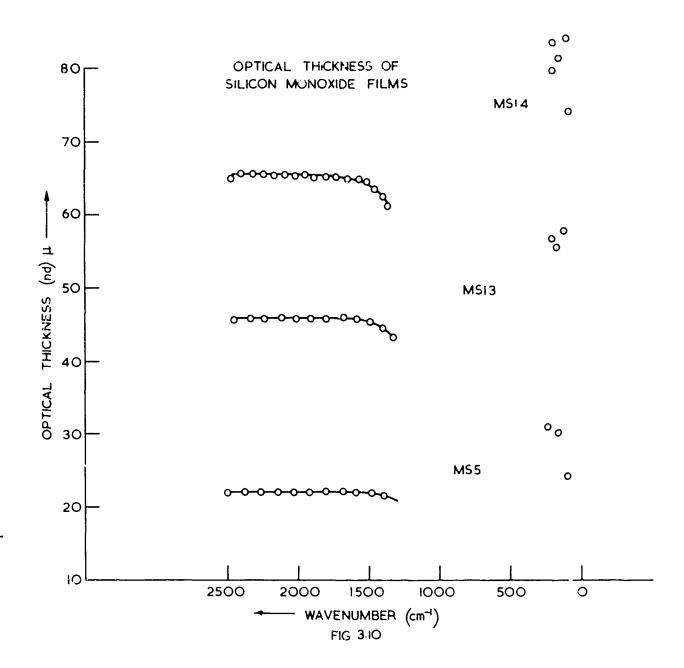


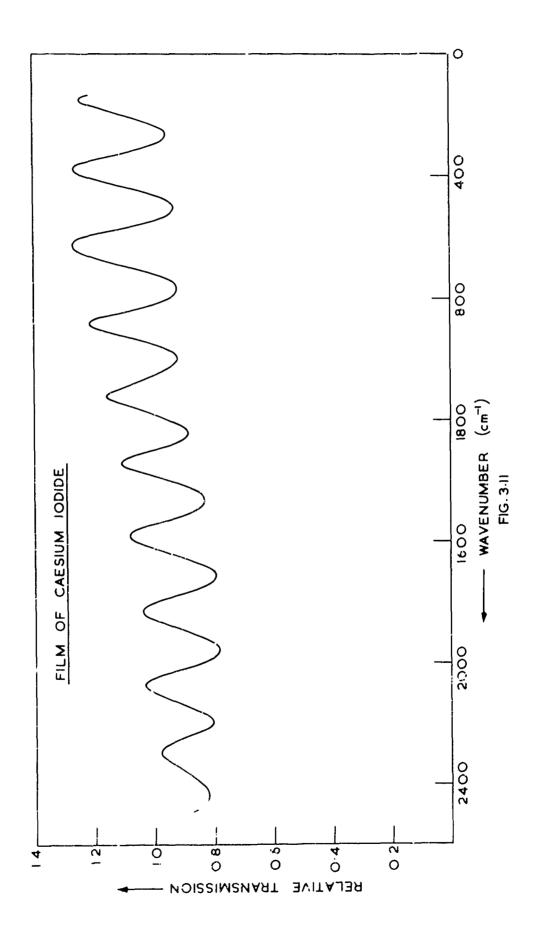
FIG. 3.6











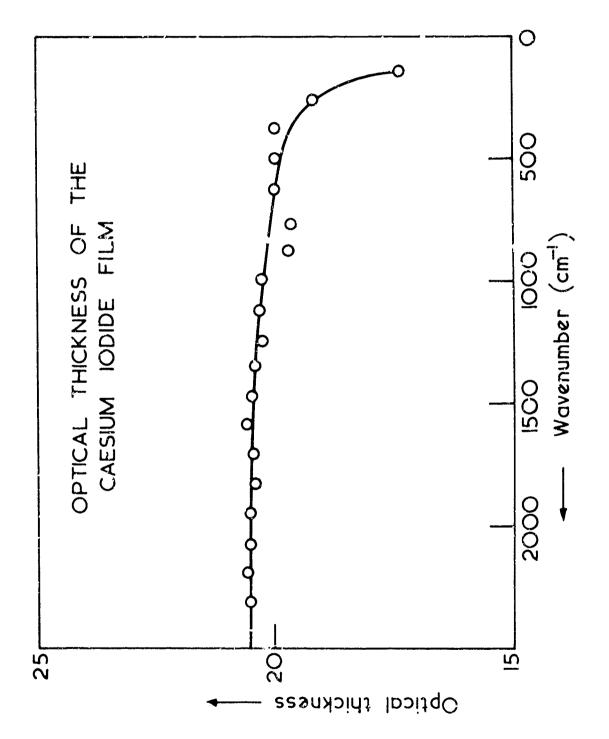
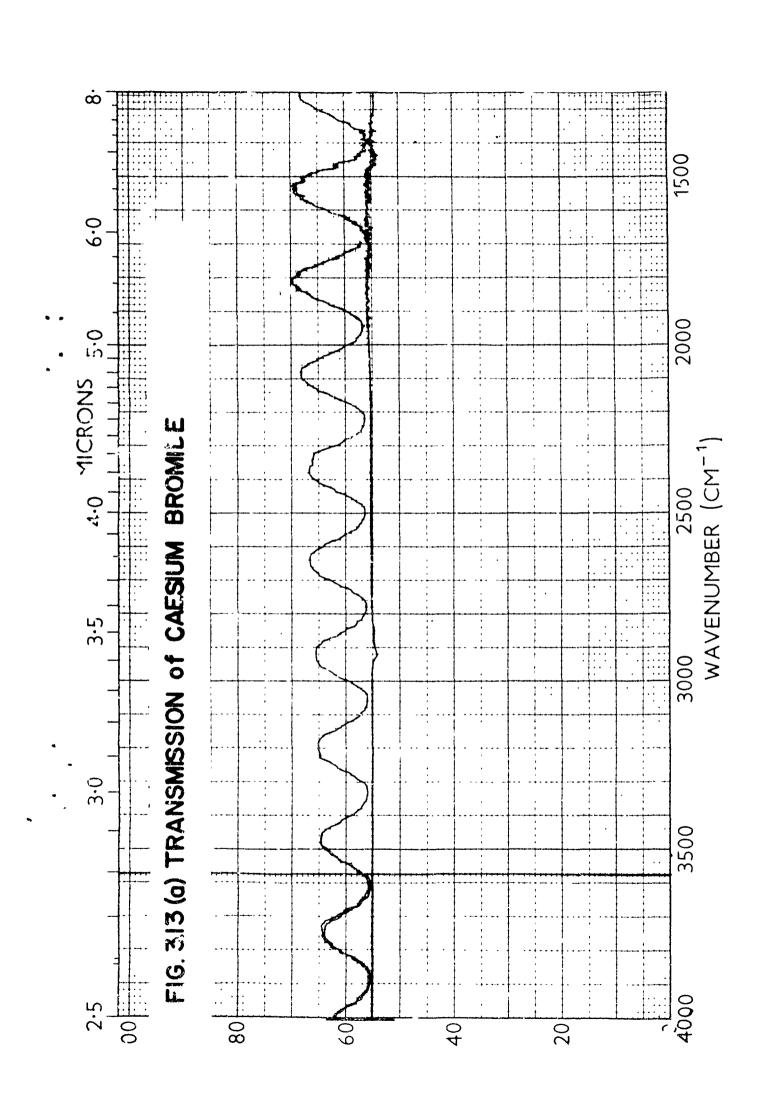
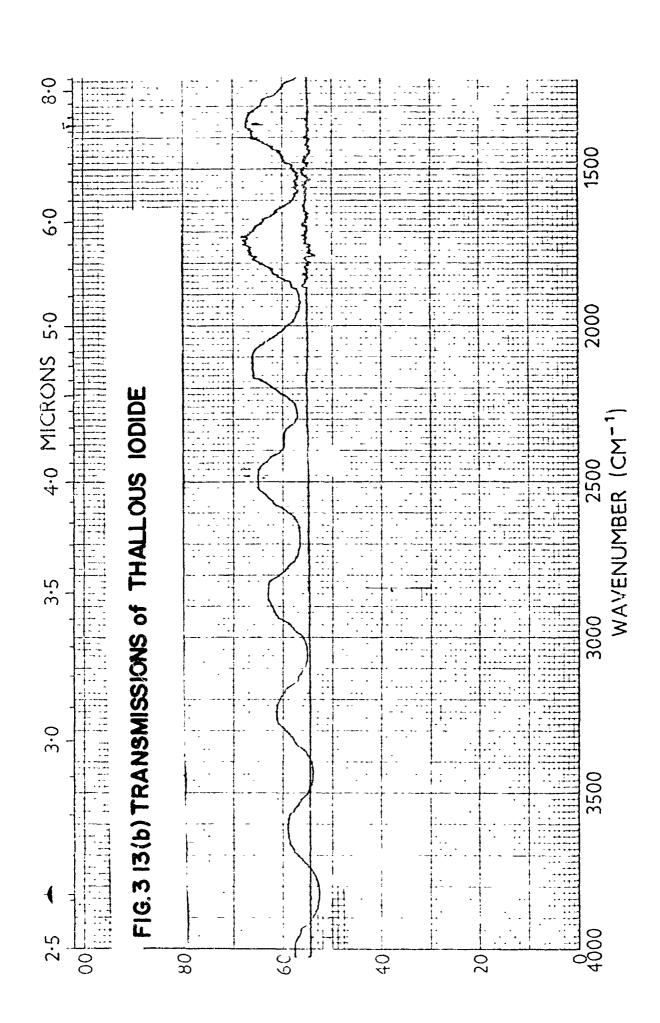
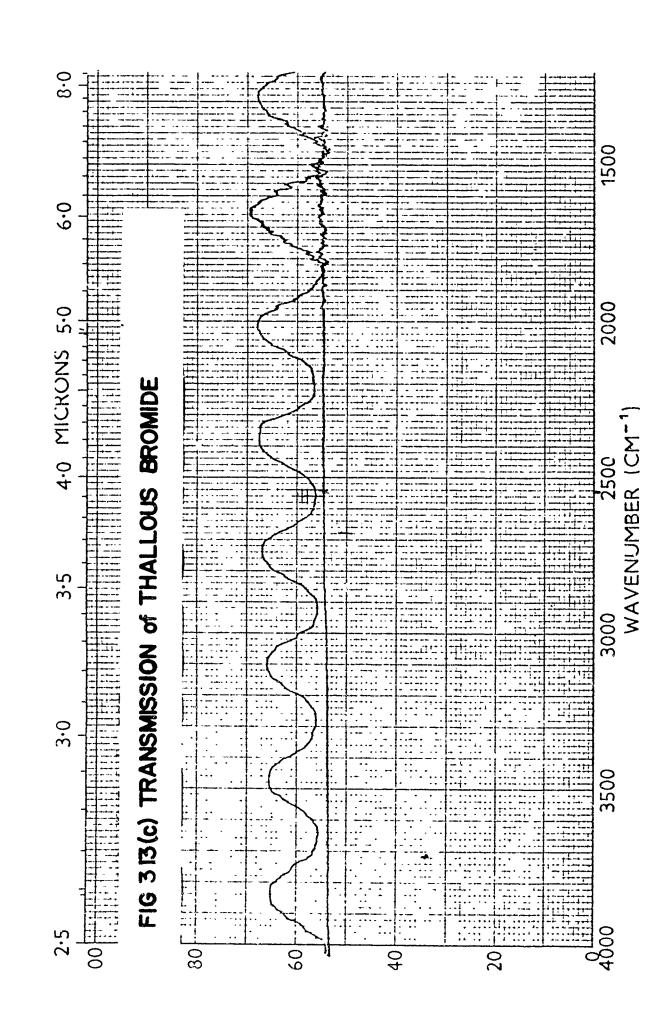
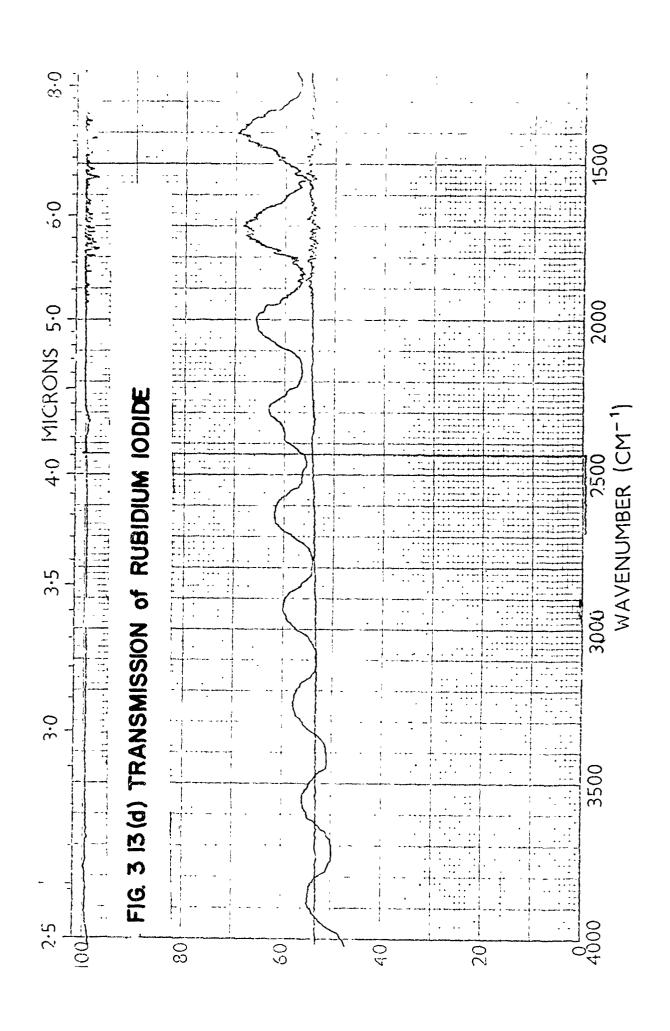


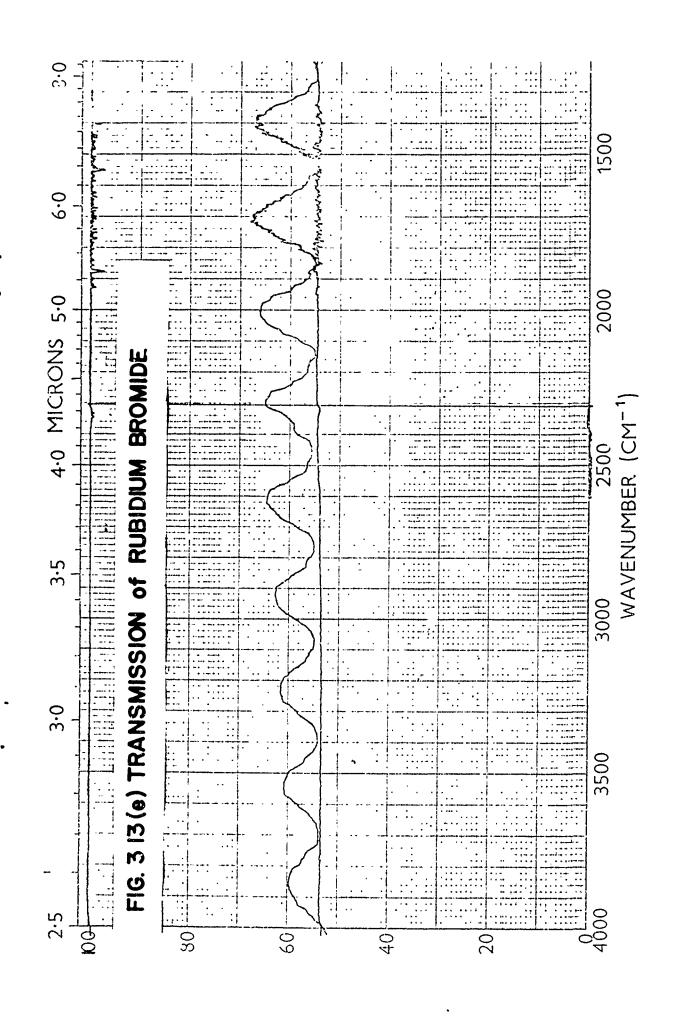
FIG. 3.12

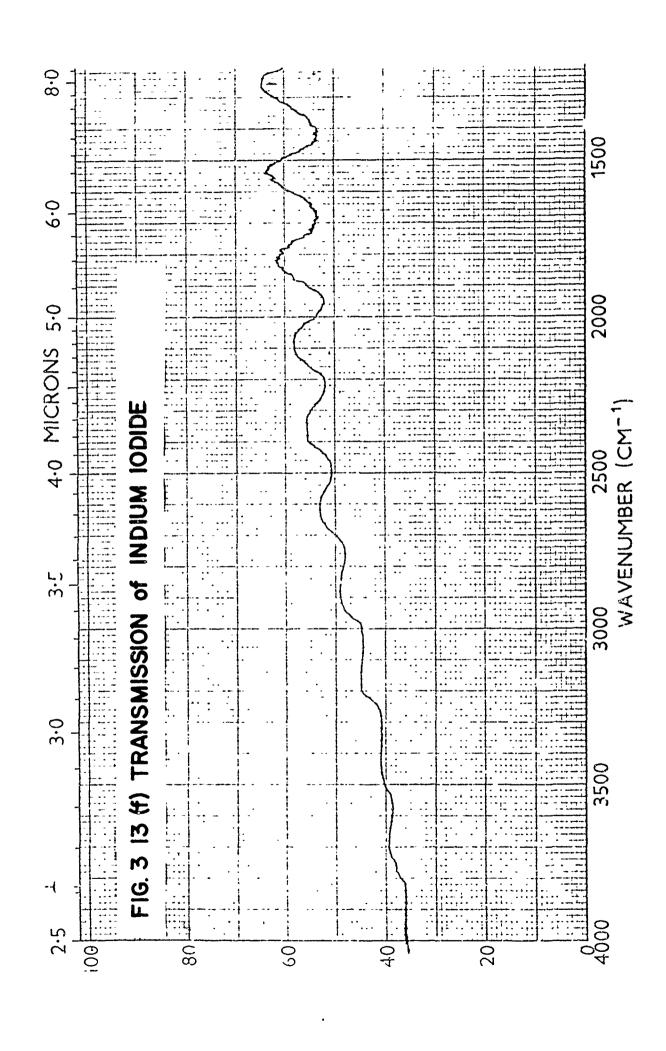


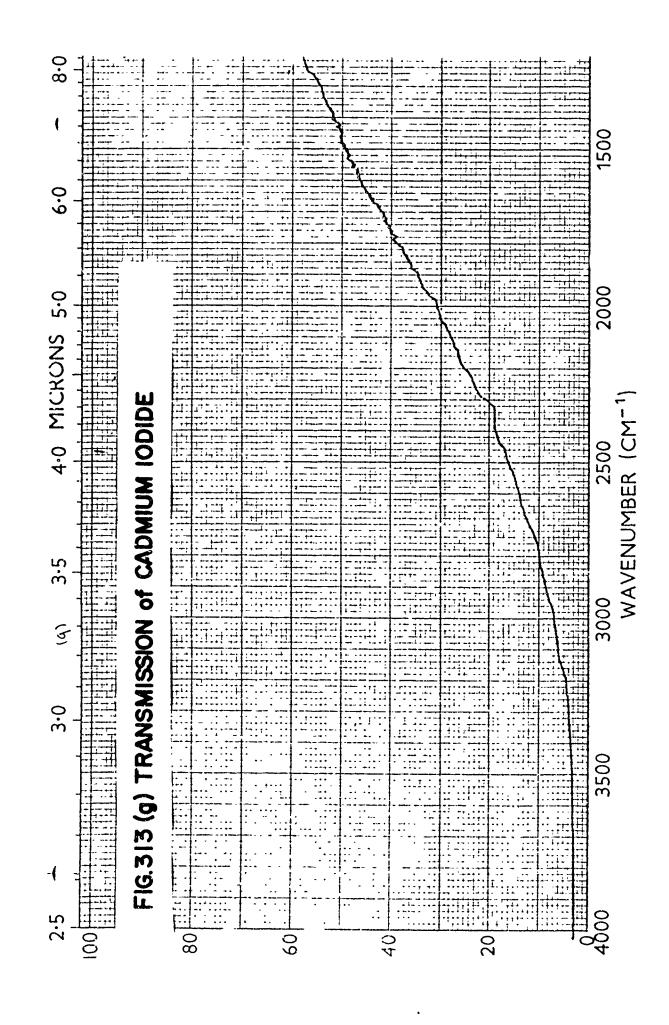


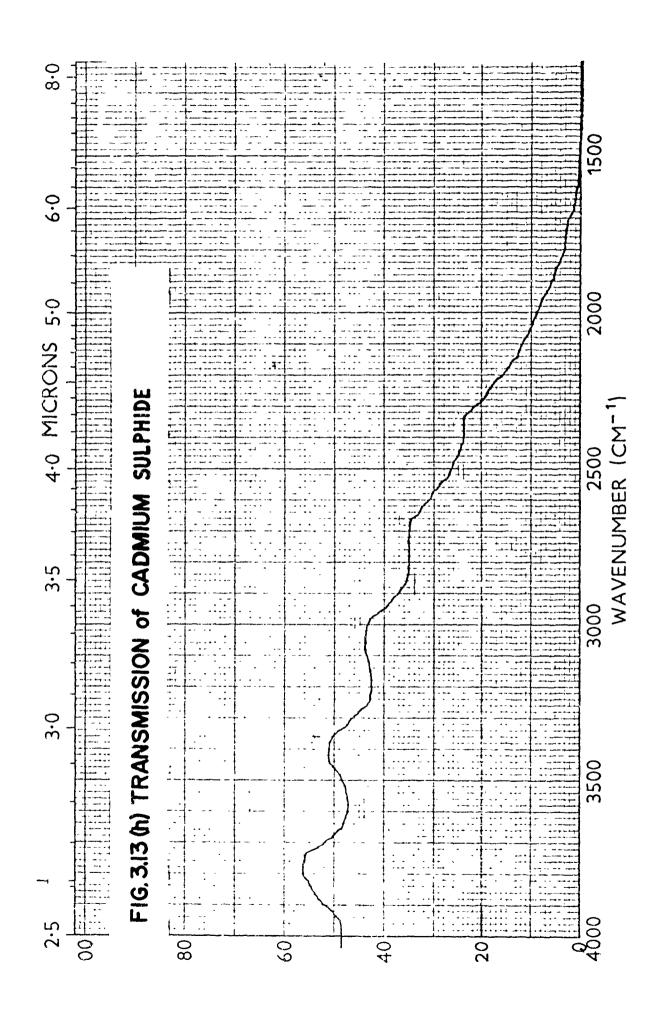


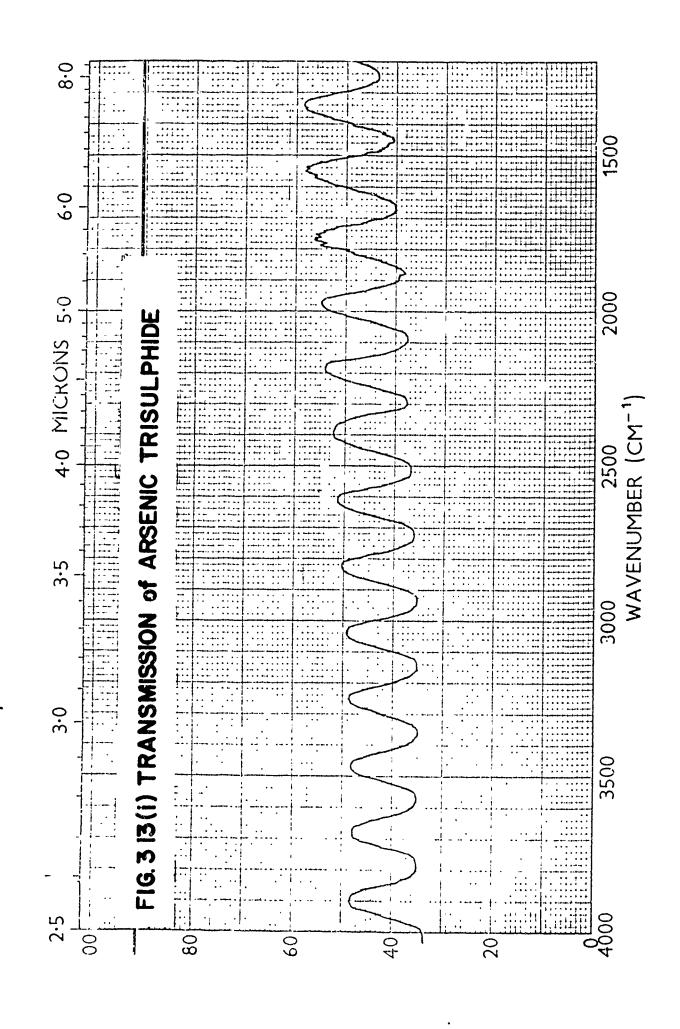


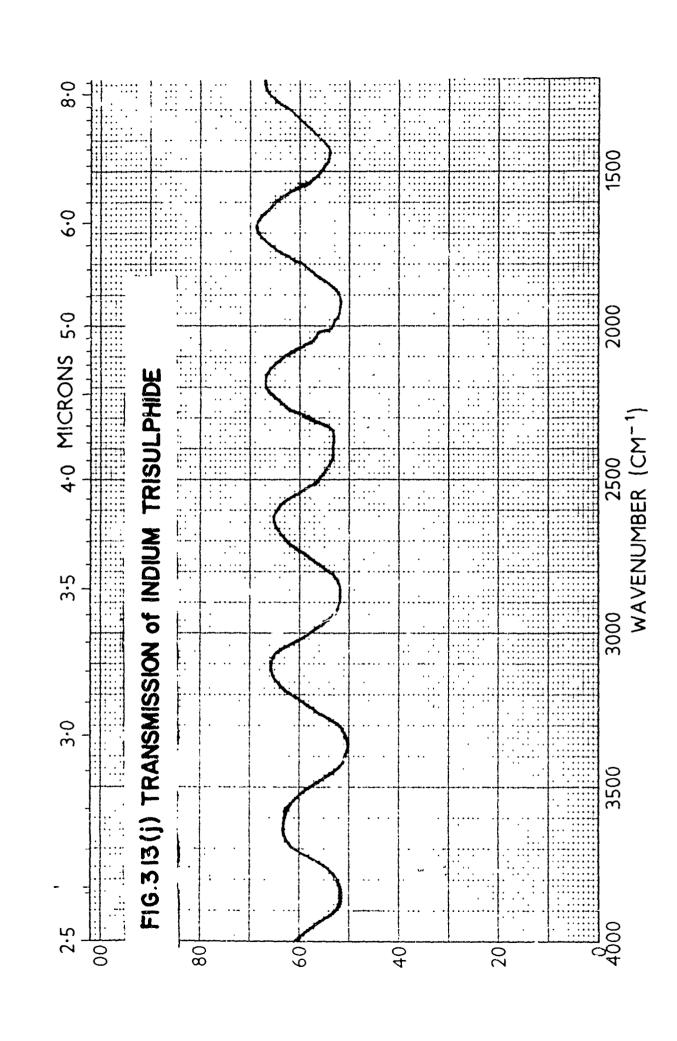


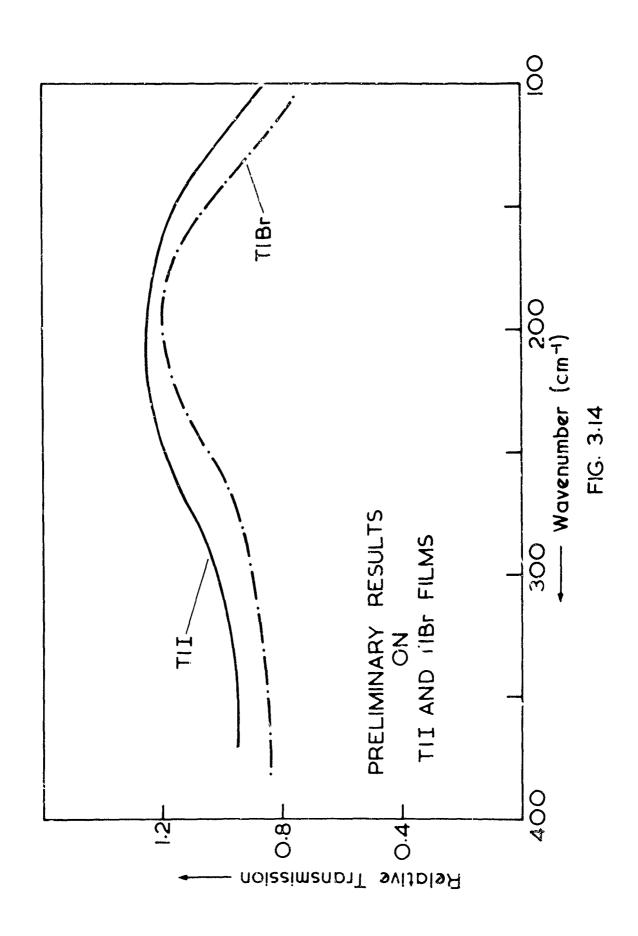












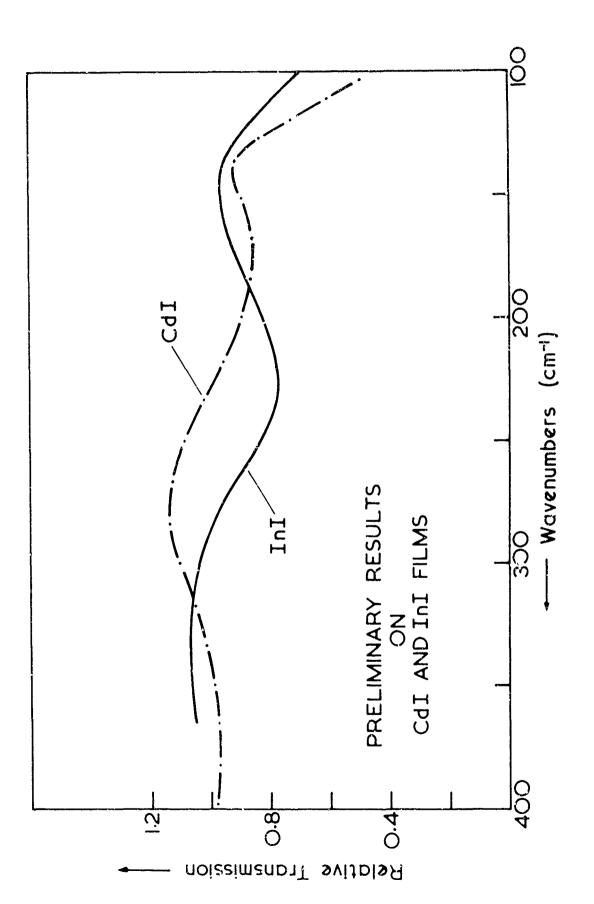


FIG. 3.15

HIGH VAPOUR PRESSURE METHOD

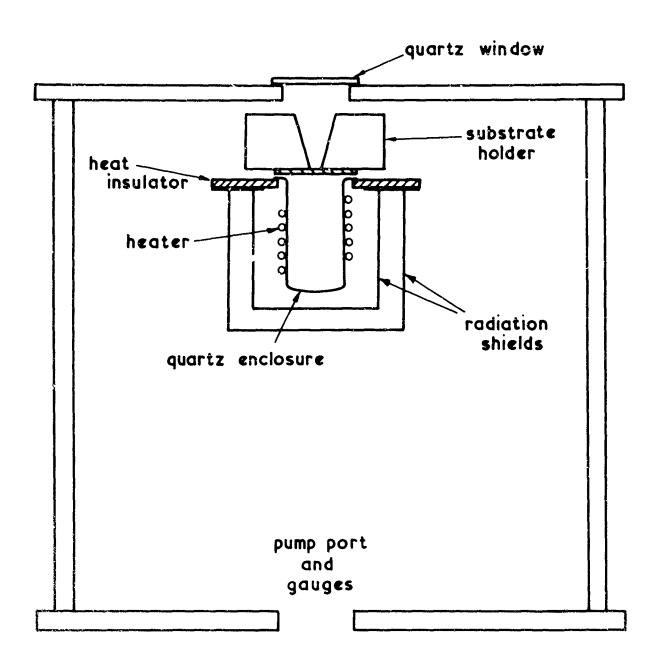


FIG. 3-16

GAS FLOW METHOD

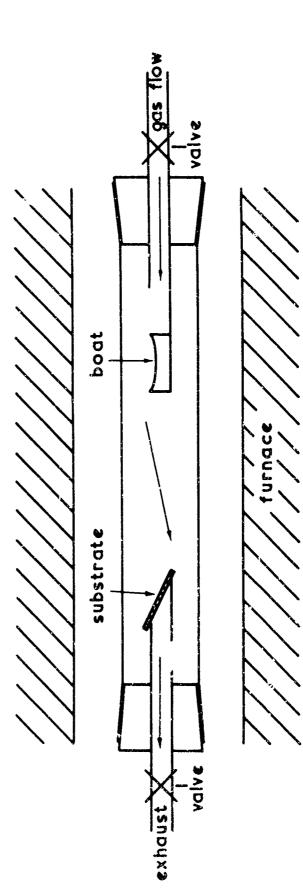
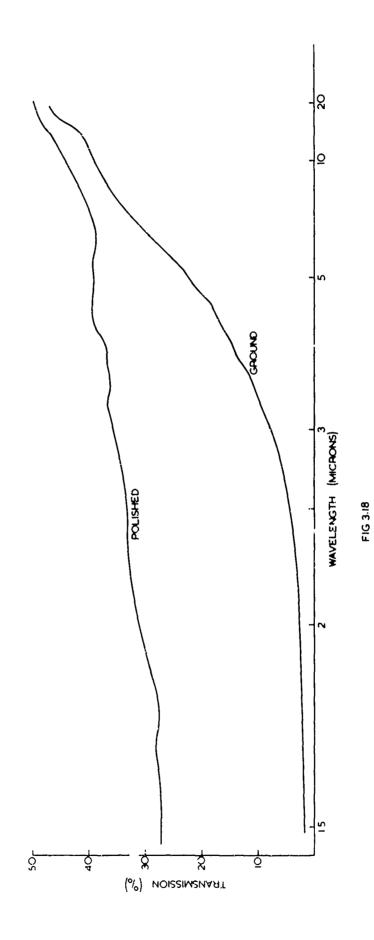
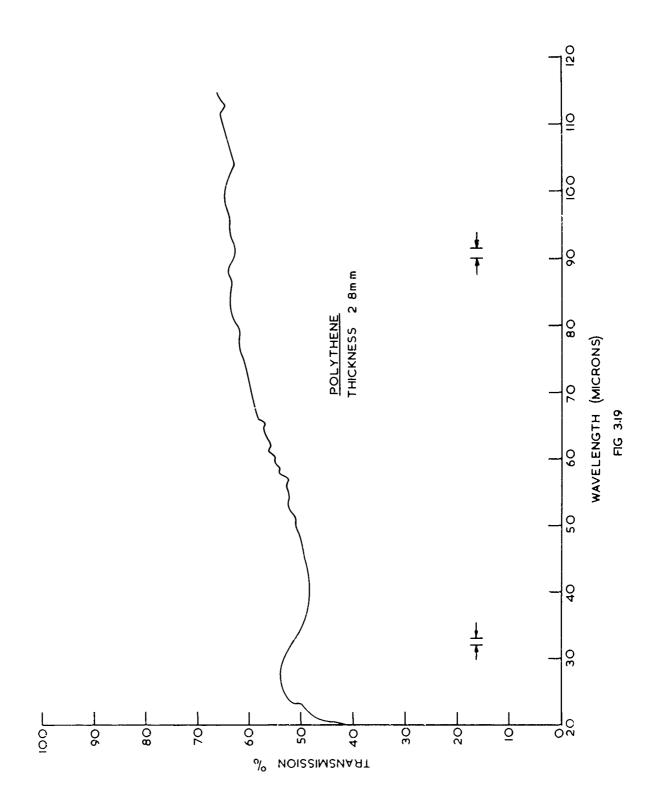


FIG. 3.17



COMPARISON OF GROUND AND POLISHED SILICON SUBSTRATES



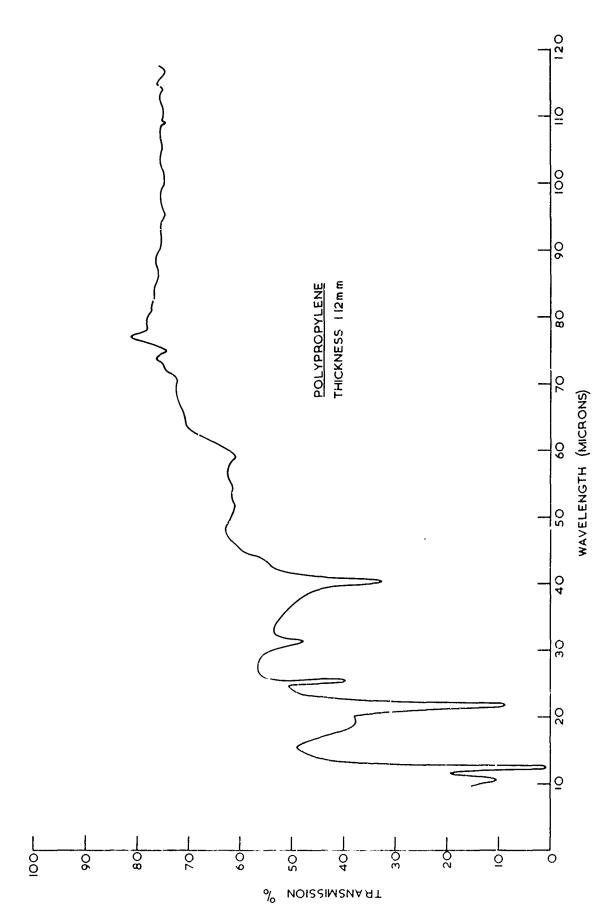
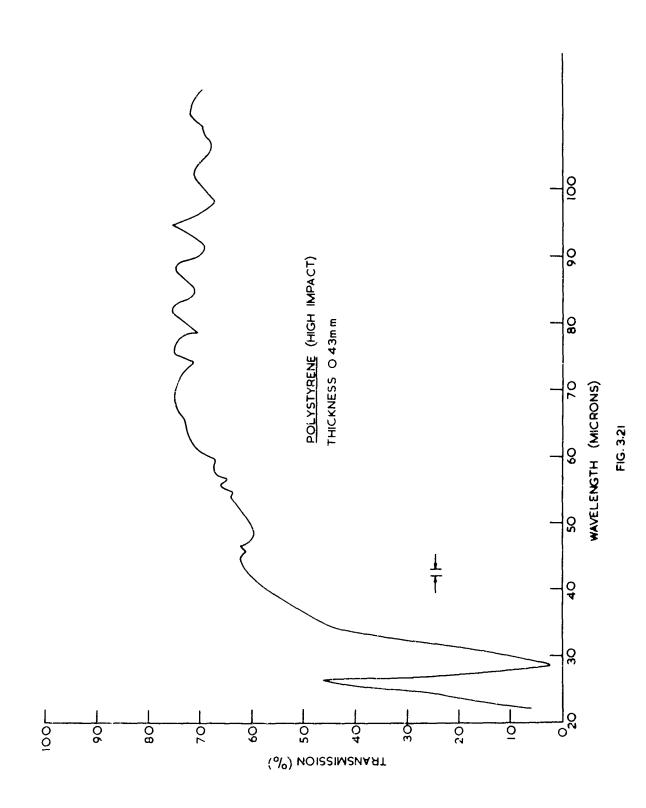
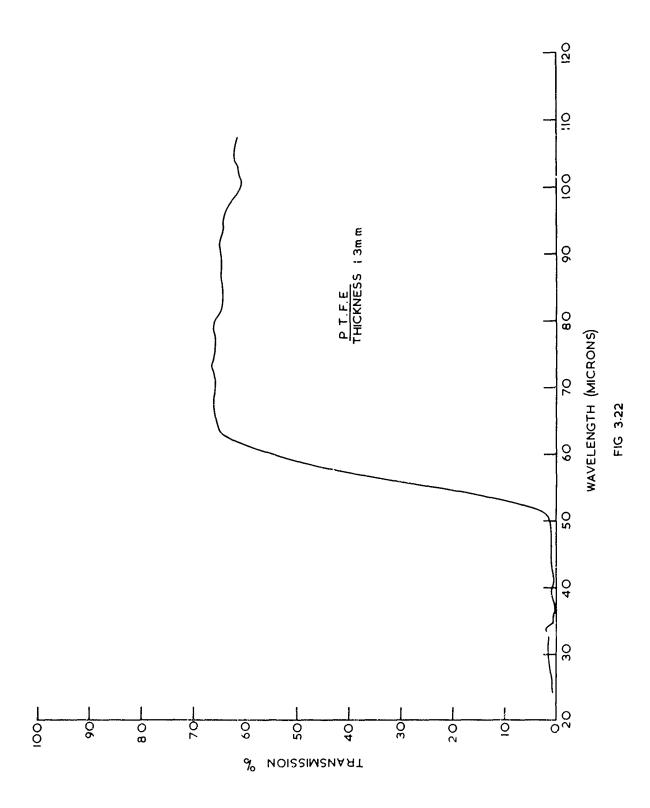
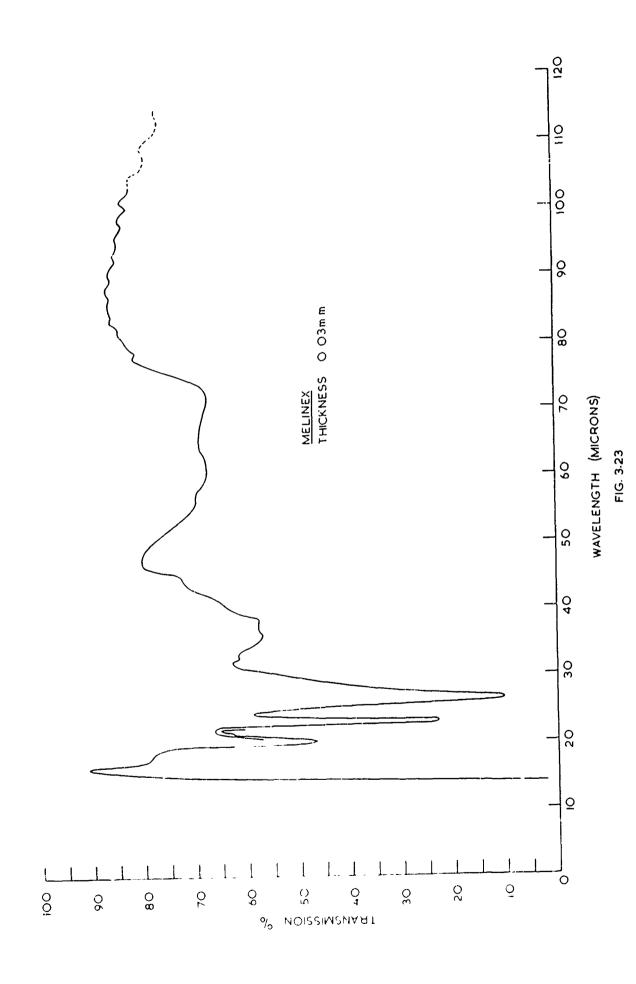
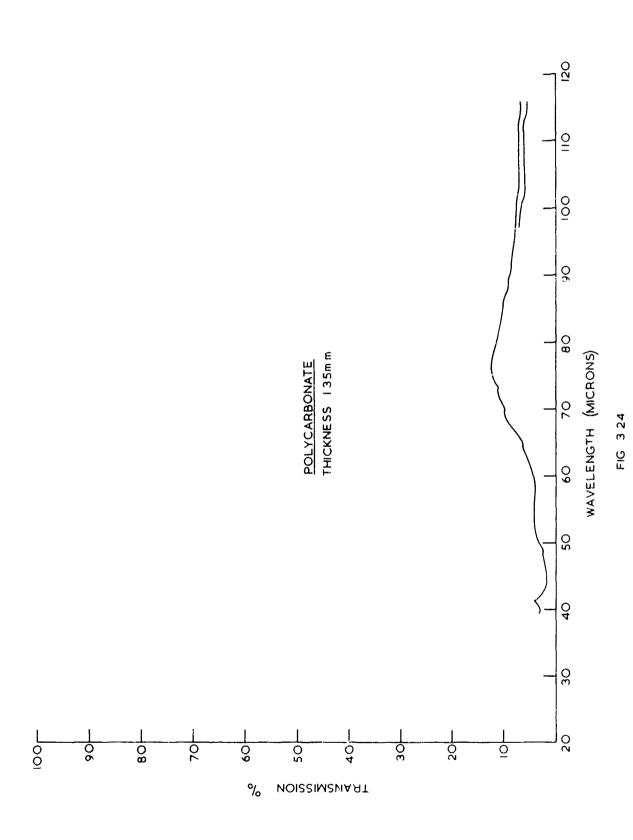


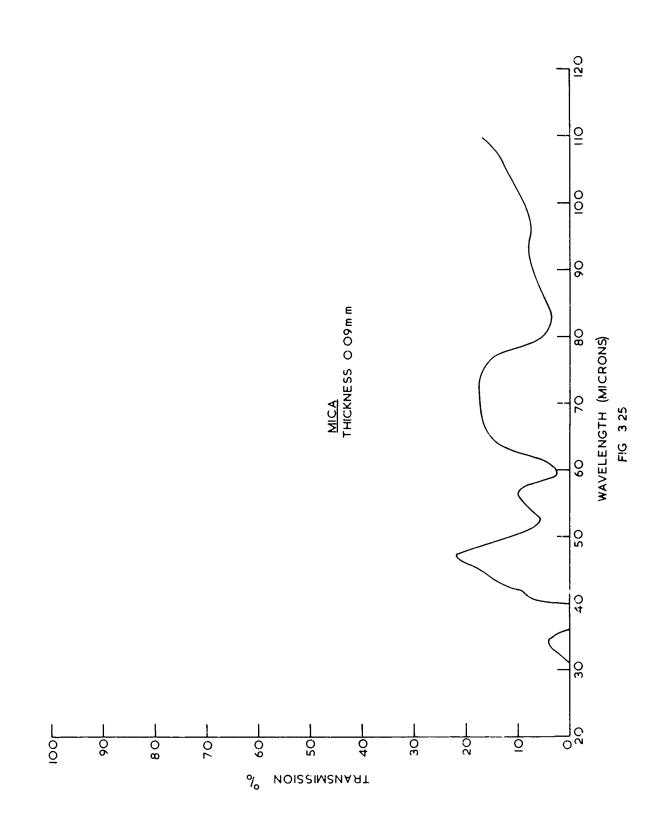
FIG. 3.20

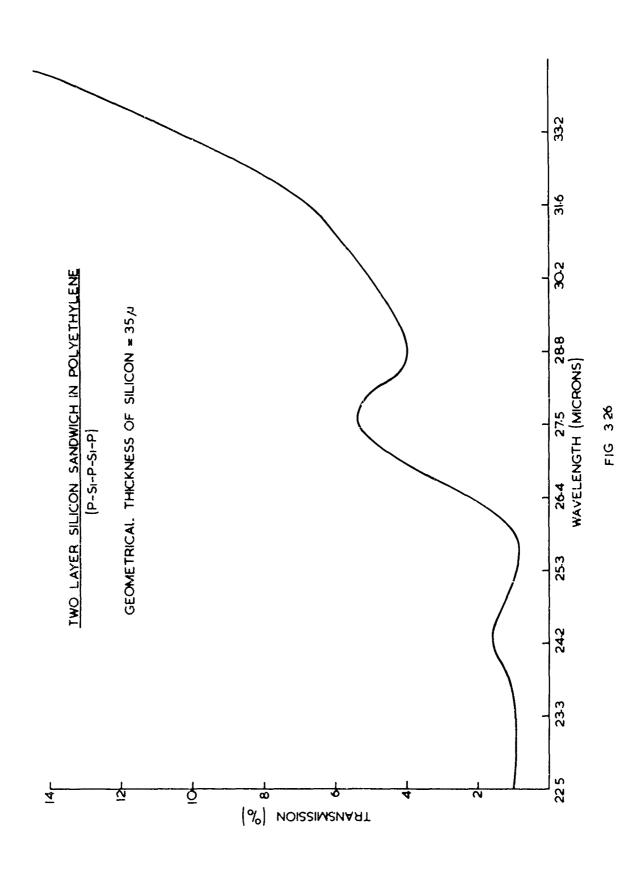


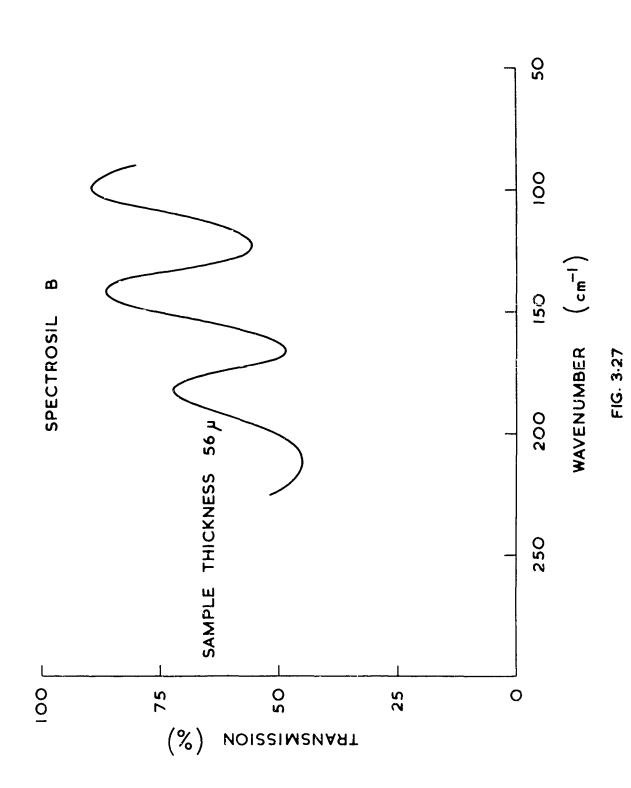


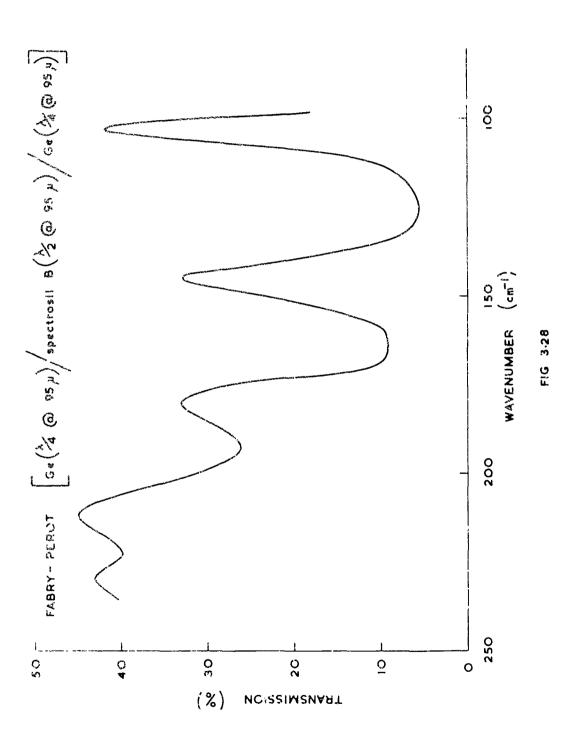












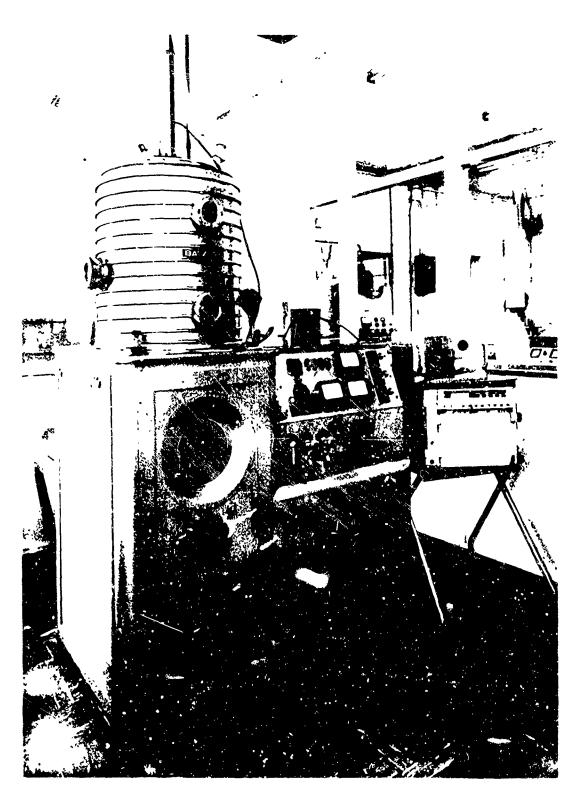


FIG: 4.1(a) BA 500 PLANT USED at GRUBB PARSONS

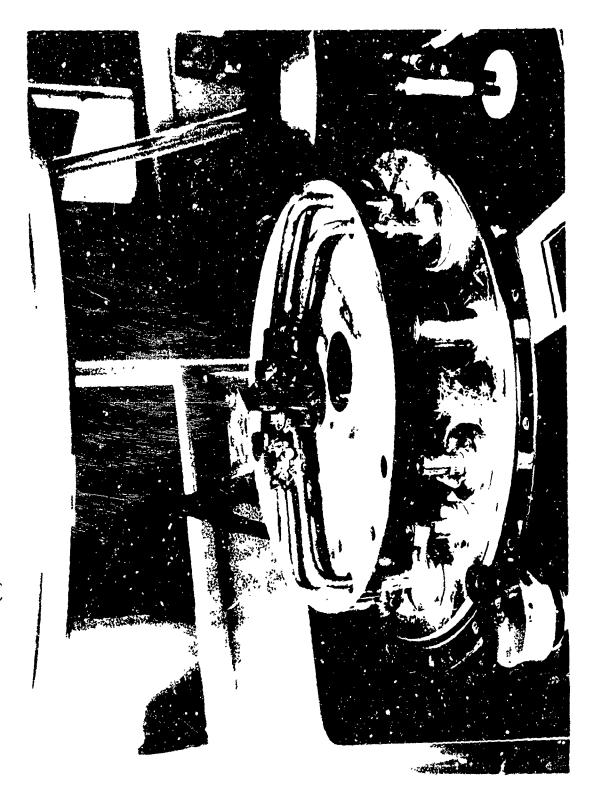


FIG: 4.1 (b) ARRANGEMENT of FIXED SOURCES

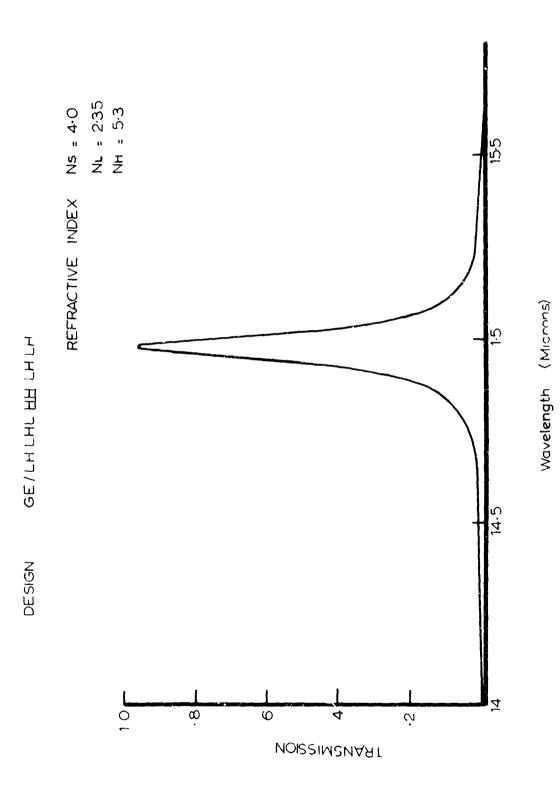


FIG 4.2 (a) COMPUTED TRANSMISSION OF FABRY PEROT AT 15µ

DESIGN Ge/LHL HHLH LH LHL HHLLH LH

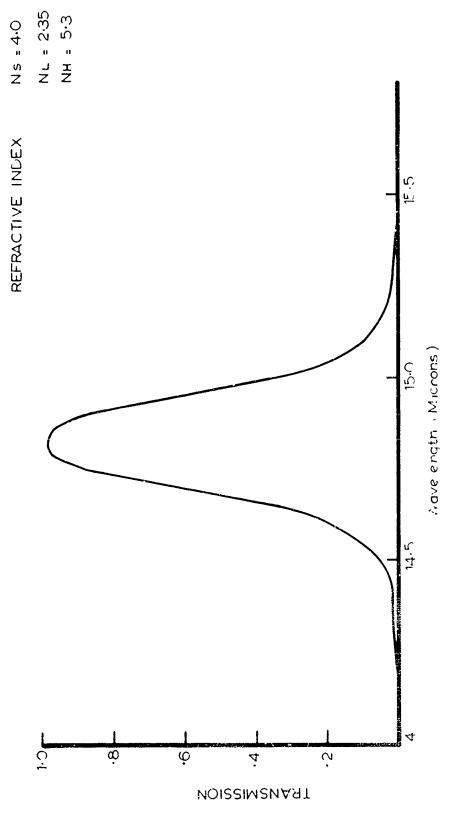


FIG 4.2 (b) COMPUTED TRANSMISSION OF D.H.W. AT 14.83µ

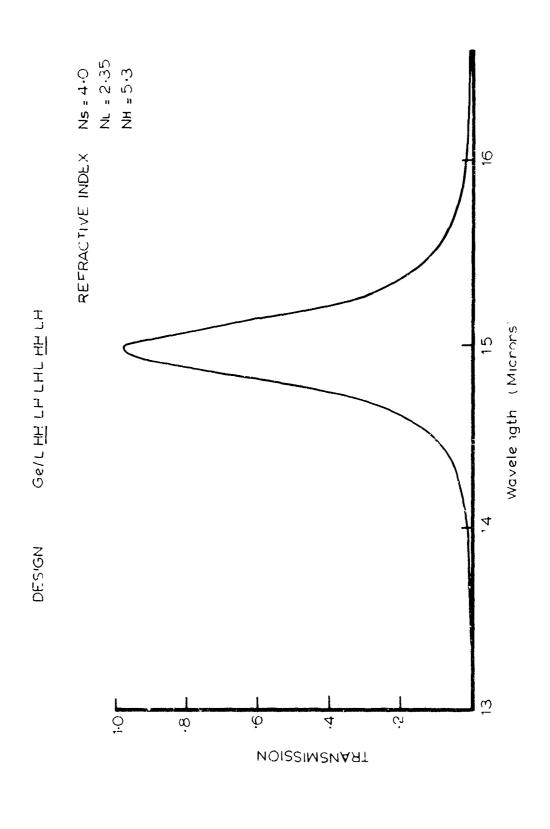
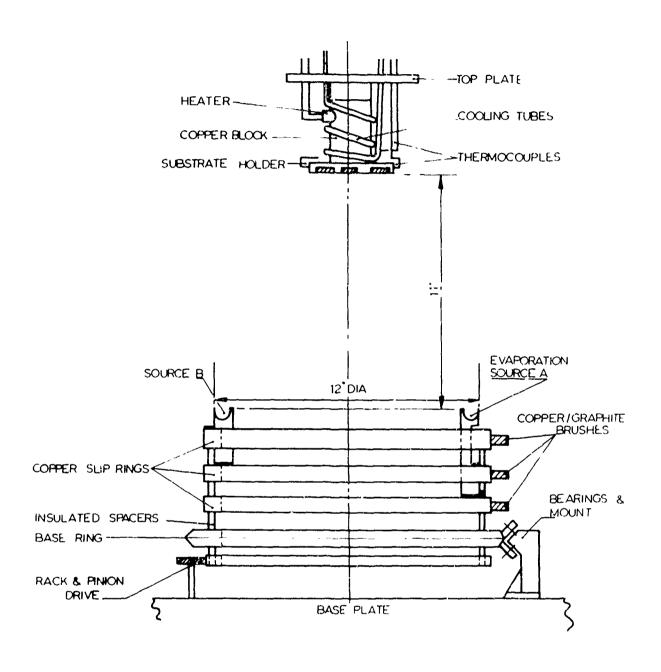


FIG 4.2 (c) COMPUTED TRANSMISSION OF D.H.W. AT 15µ



SCHEMATIC DIAGRAM OF ROTATING SOURCE ASSEMBLY & SUBSTRATE HOLDER

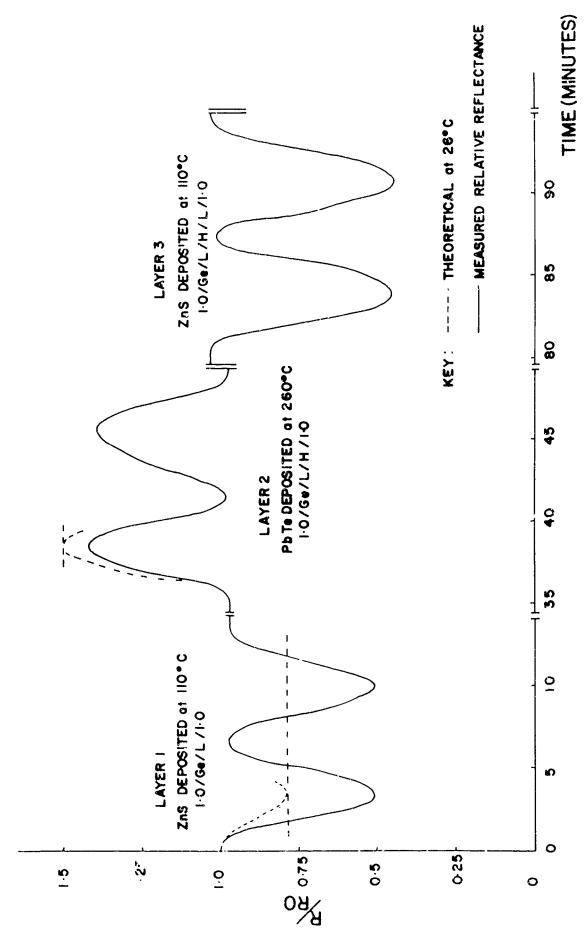
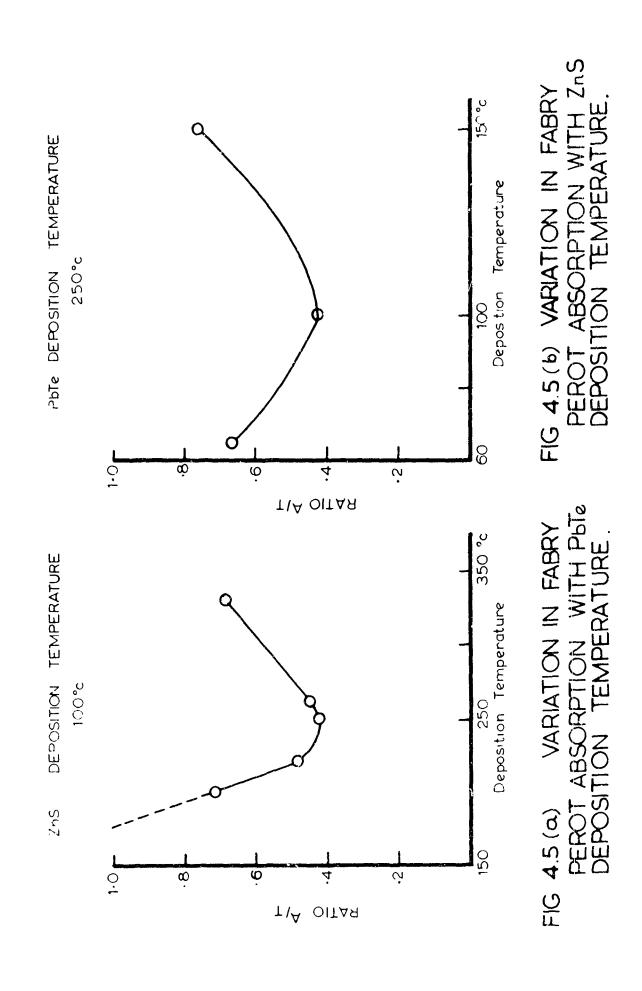
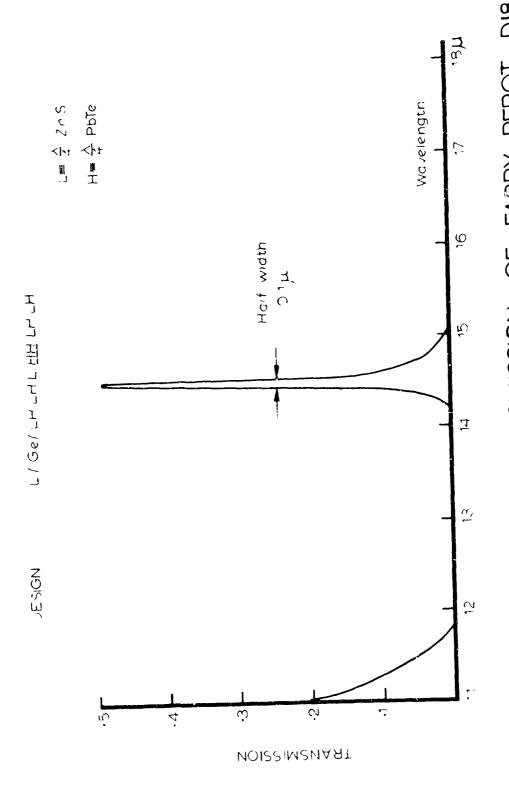


FIG 4-4 REFLECTANCE MONITORING in the 4th ORDER SCHEMATIC





MEASURED TRANSMISSION OF FABRY PEROT DIB FIG 4.6.

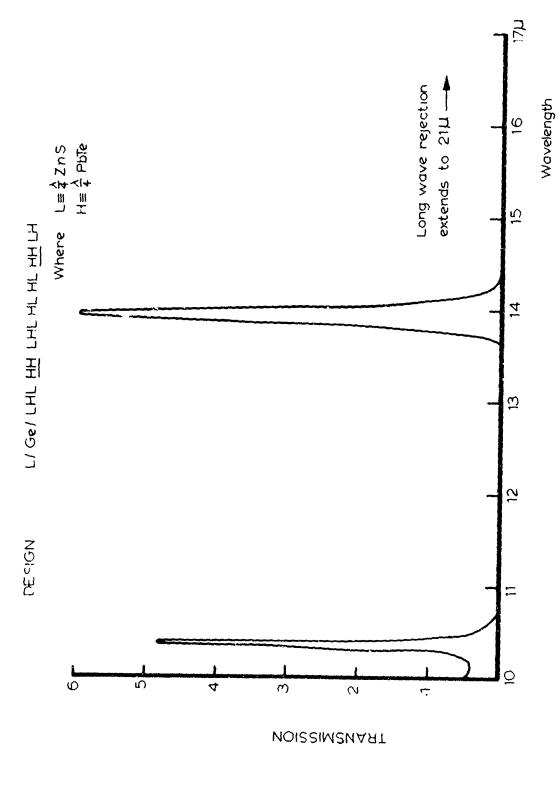


FIG. 4.7(a) MEASURED TRANSMISSION OF D.H.W. 5.

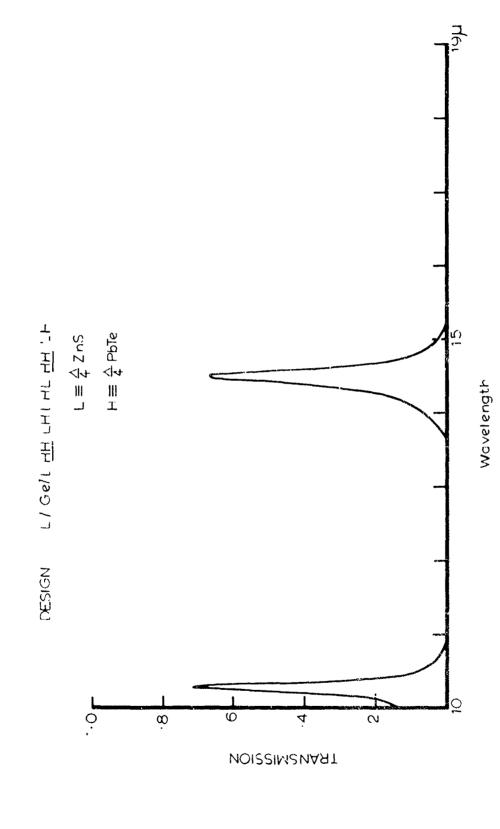


FIG 4.7(b) MEASURED TRANSMISSION OF D.H.W. 13.

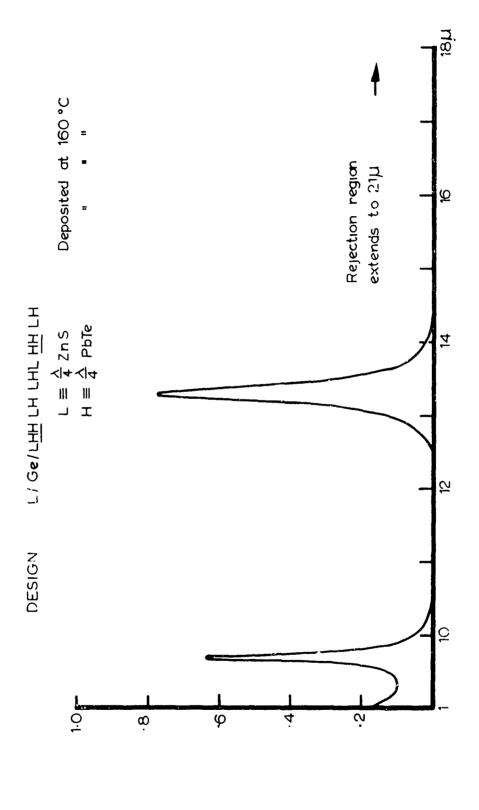


FIG. 4.8. MEASURED TRANSMISSION OF D.H.W.19.

THEORETICAL DISTRIBUTION OF EVAPORANT FROM A SMALL ROTATING SURFACE SOURCE. INCHES ő SOURCE RADIUS OF ROTATION = HEIGHT OF RECEIVING PLANE ABOVE SOURCE 5 RADIUS FROM CENTRE ö POSITION OCCUPIED BY SUBSTRATES 0 ئ FIG .4.9. -1:2 0:1-9 æ g 0 PERCENTAGE CHANGE NI

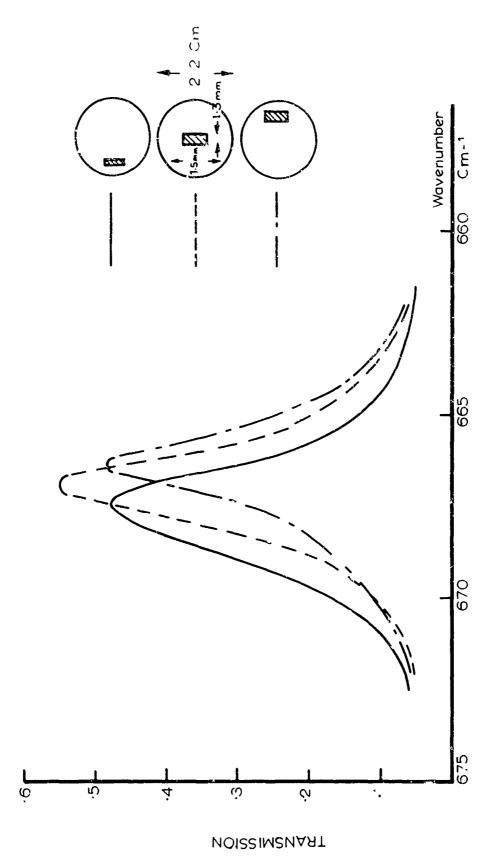


FIG.4.10. F.P. FILTER 8180/4/MONITOR. MEASUREMENTS TAKEN AT 3 DIFFERENT PLACES ON FILTER SURFACE AT A FOCUS POSITION & AT NORMAL INCIDENCE.

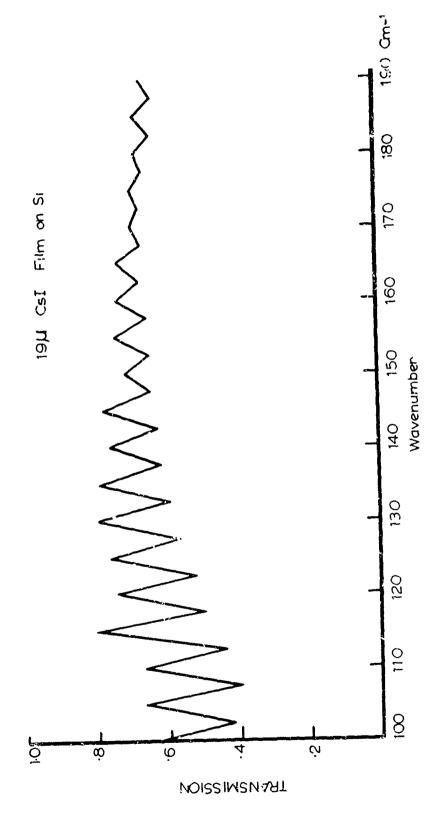
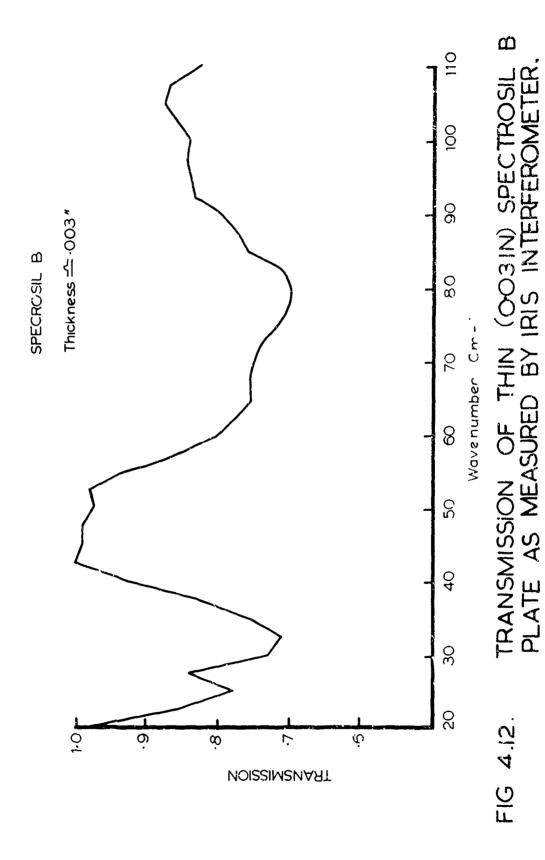


FIG.4.11. INTERFEROMETRIC MEASUREMENT OF A CST FILM ON SI SUBSTRATE AT 2.5 Cm-1 RESOLUTION SHOWING FRINGES DUE TO SUBSTRATE INTERFERENCE.



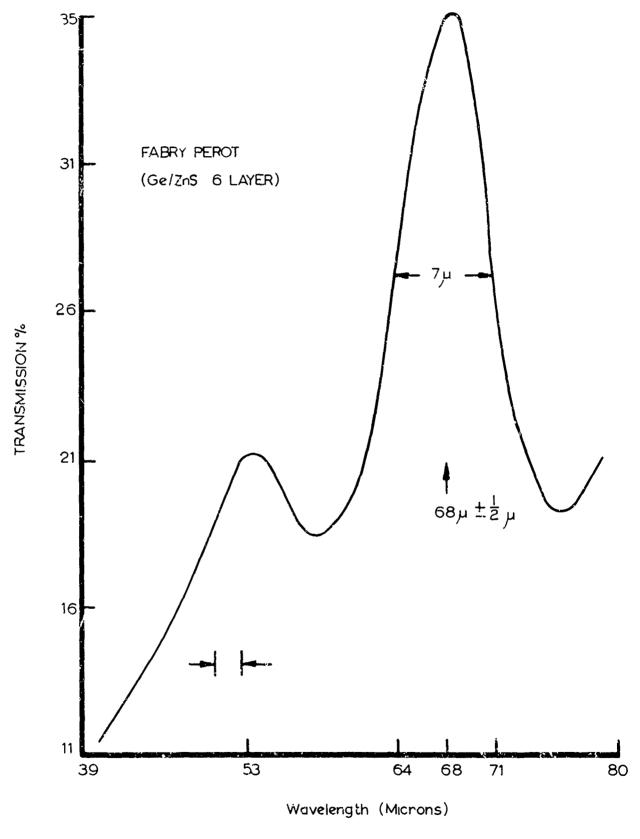
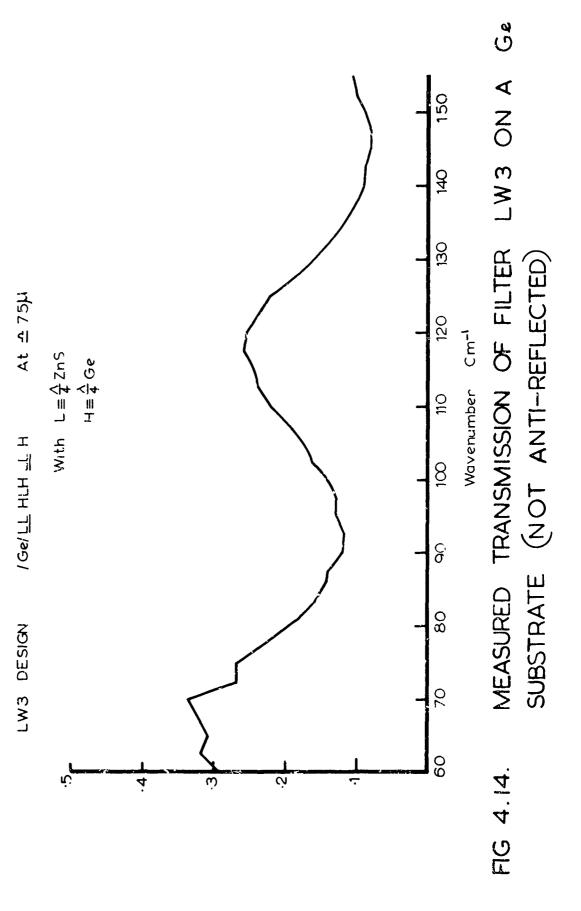


FIG. 4.13.



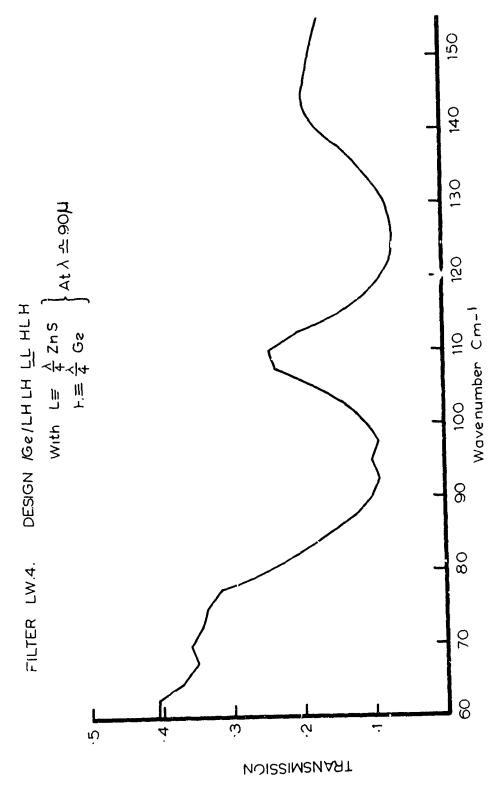
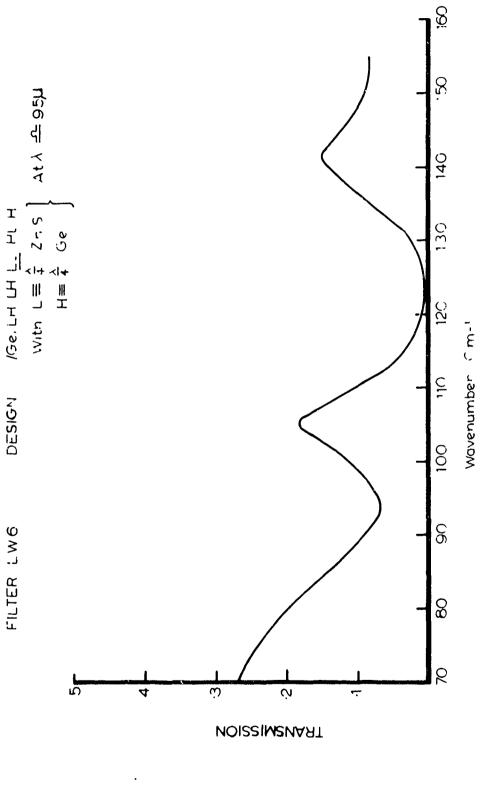
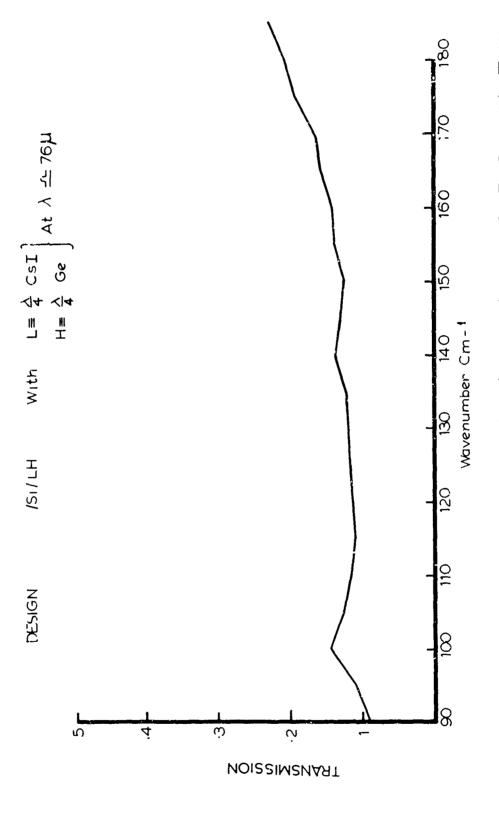


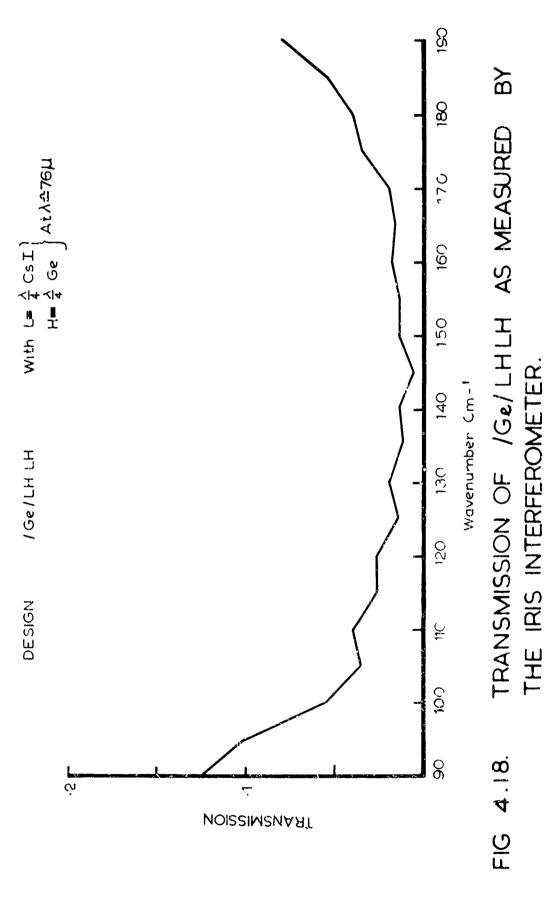
FIG 4.15. TRANSMISSION OF FILTER L.W.4 ON Ge SUBSTRATE AS MEASURED BY IRIS INTERFEROMETER.



TRANSMISSION OF LW6 ON Ge SUBSTRATE AS MEASURED BY THE GM3 SPECTROMETER. FIG. 4.16



TRANSMISSION OF / Si/LH AS MEASURED BY THE IRIS INTERFEROMETER FIG 4.17.



FILTER DESIGN L/SL/LH LL H

With
$$L = \frac{\lambda}{4} CsI$$
 $H = \frac{\lambda}{4} Ge$

At $\lambda = 75\mu$

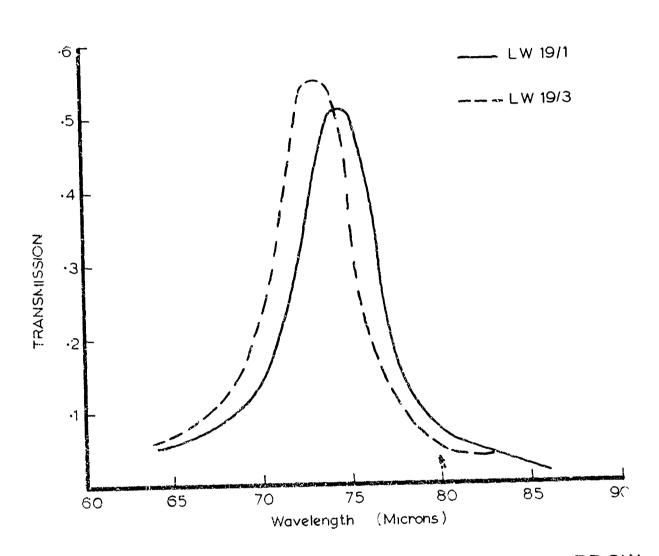
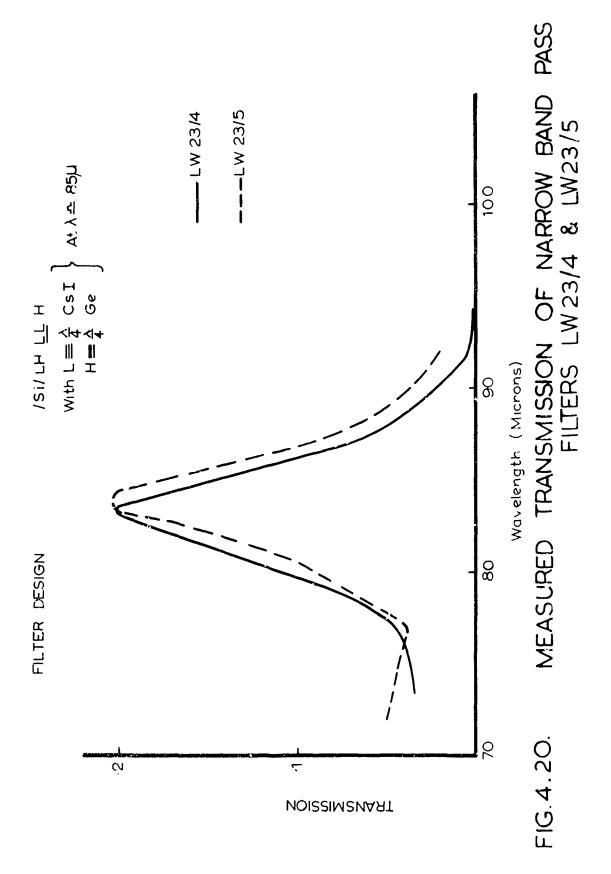
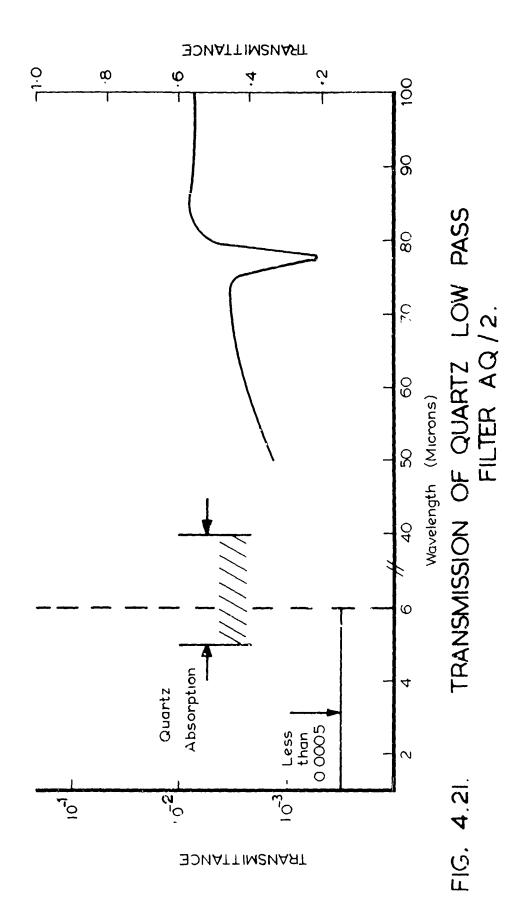


FIG. 4.19. MEASURED TRANSMISSION OF NARROW BAND PASS FILTERS LW19/1 & LW19/3.





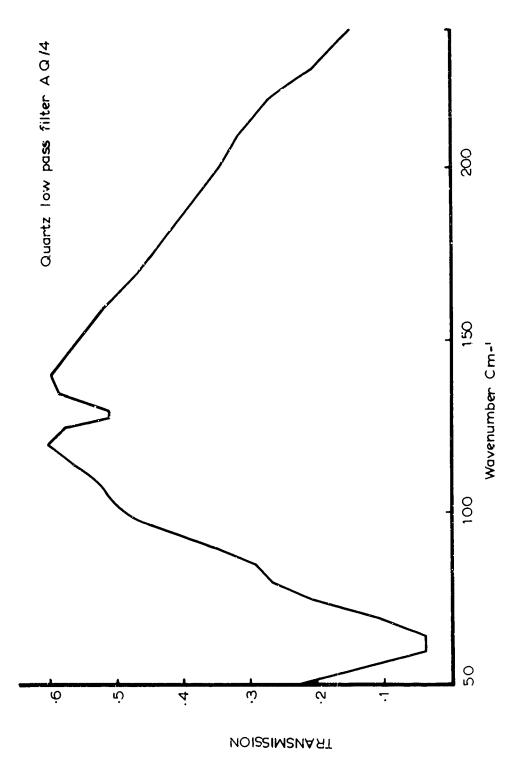
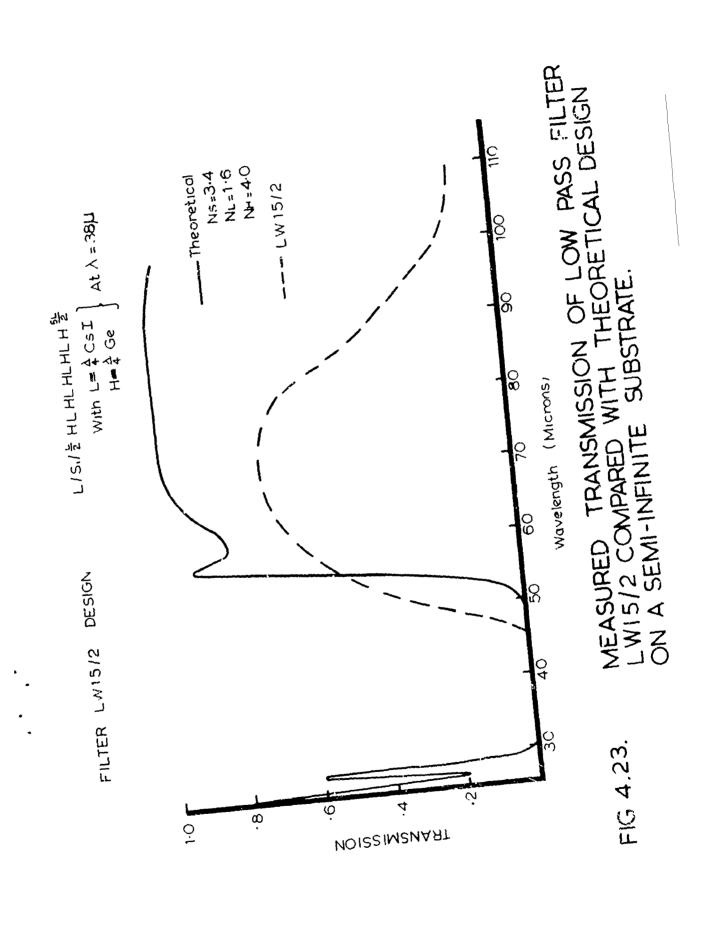


FIG.4.22. FAR INFRARED TRANSMISSION OF QUARTZ LOW PASS
FILTER AQ/4 AS MEASURED BY CUBE INTERFEROMETER.
AT 5 Cm -1 RESOLUTION.



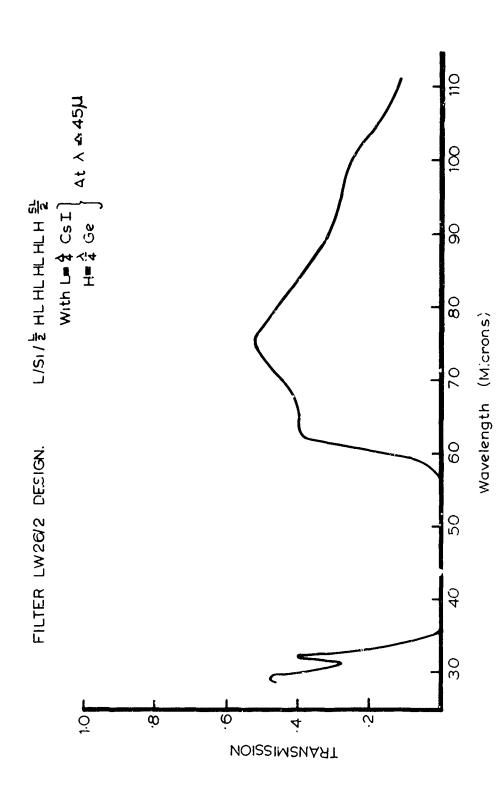
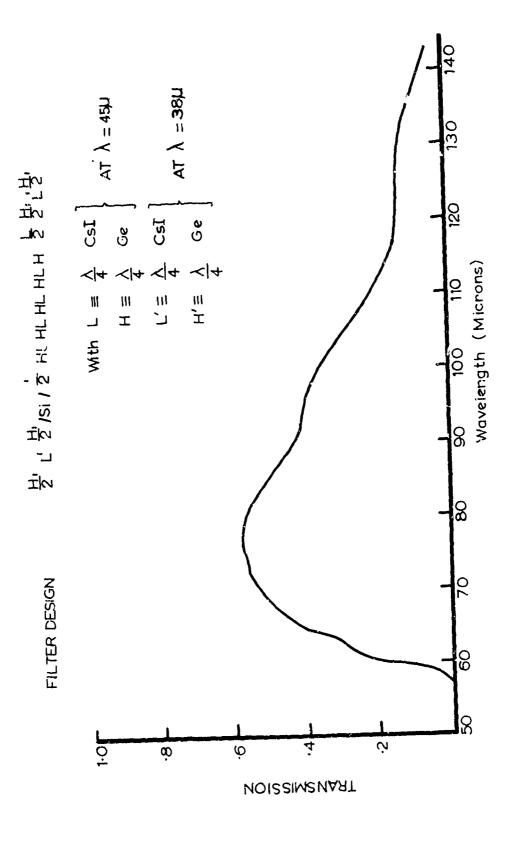


FIG. 4.24. MEASURED TRANSMISSION OF LOW PASS FILTER LW26/2 SHOWING EXTENT OF STOP REGION.



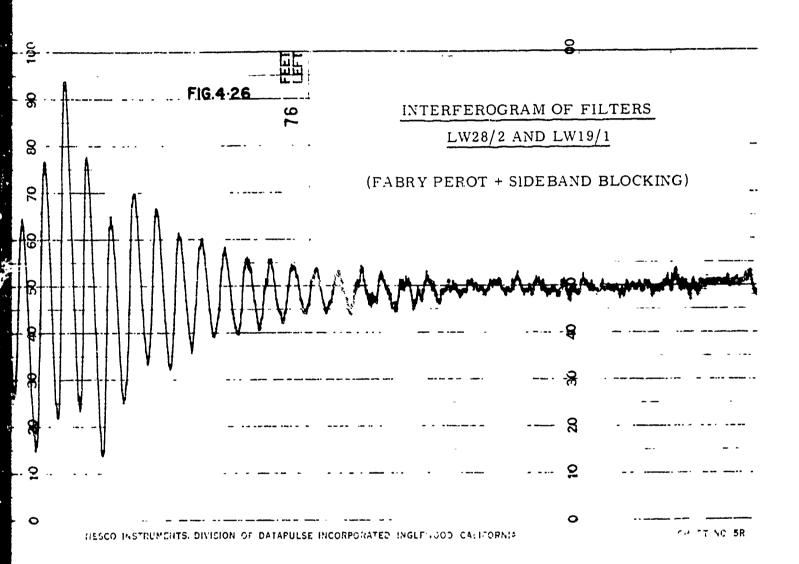
TRANSMISSION OF LOW PASS FILTER LW28/1 AS MEASURED BY THE CUBE INTERFEROMETER FIG. 4.25.

	<u>\$</u>					
	···· o n································				:	
	- 		·			_h ;
						. 1 1 1
			-		:	
philippin .	Roman	MANAY	MMM	$\Lambda M \Lambda$	$\Lambda\Lambda\Lambda$	
	. Q				AAAA	<i>[</i>
						W V 11
	0					, II.
		-				*.
						· 1
-	·· 8 · ··· -					{

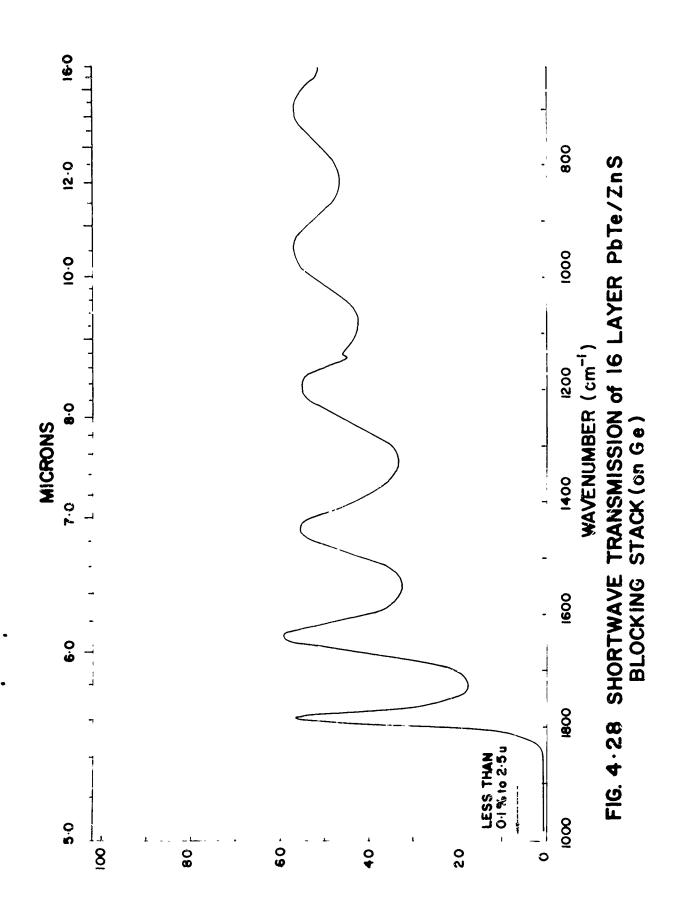
CHATT NO. 5R

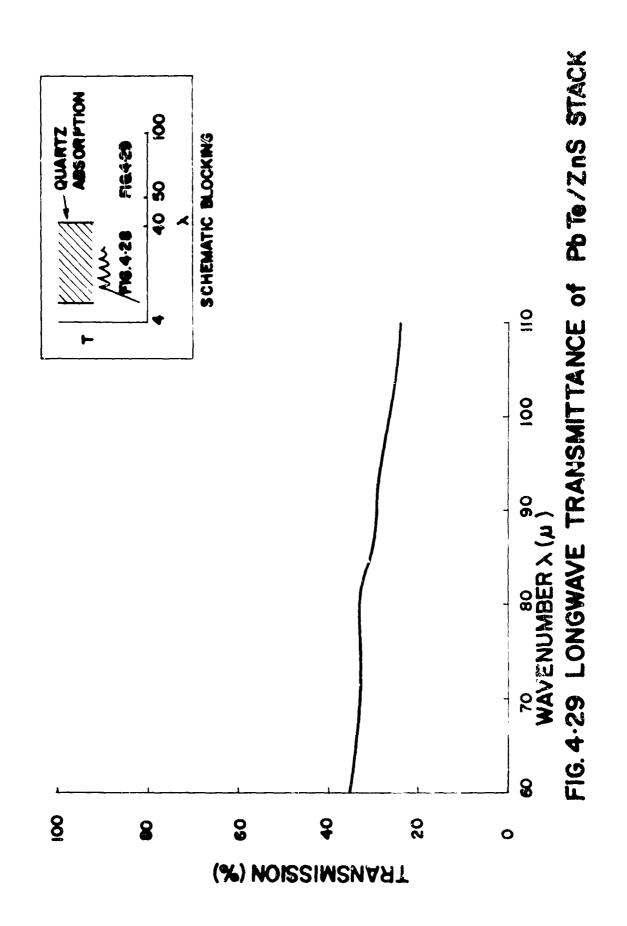
4

D. CALIFORNIA



J)





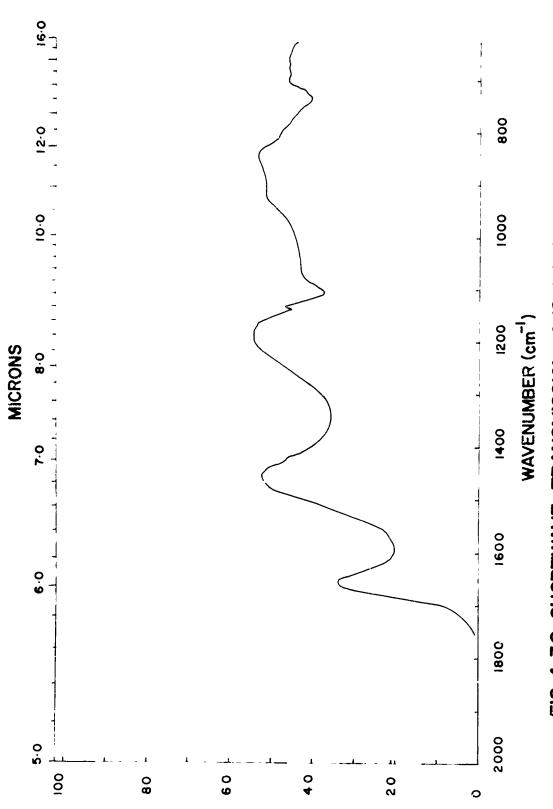


FIG. 4-30 SHORTWAVE TRANSMISSION of 12 LAYER PDTe/CSI STACK (on Si)

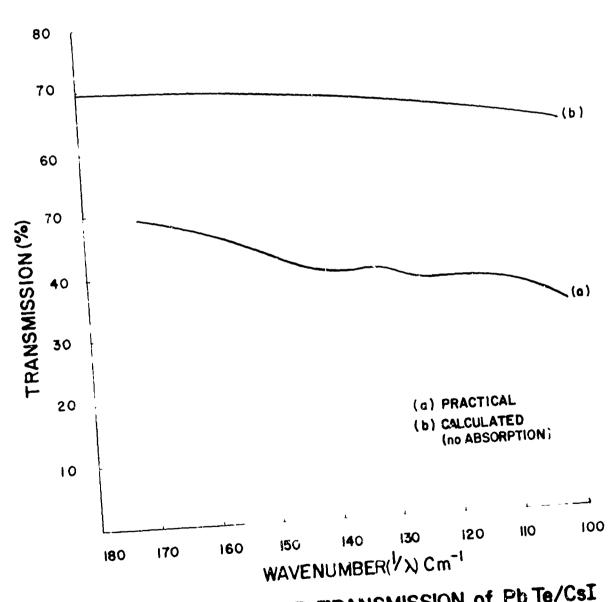


FIG. 4-31 LONGWAVE TRANSMISSION of Pb Te/CsI STACK NO. 048/1

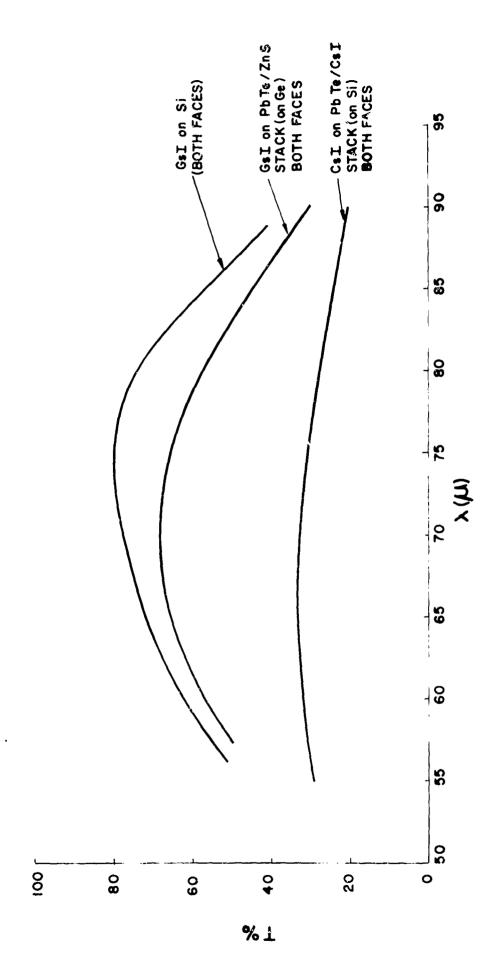
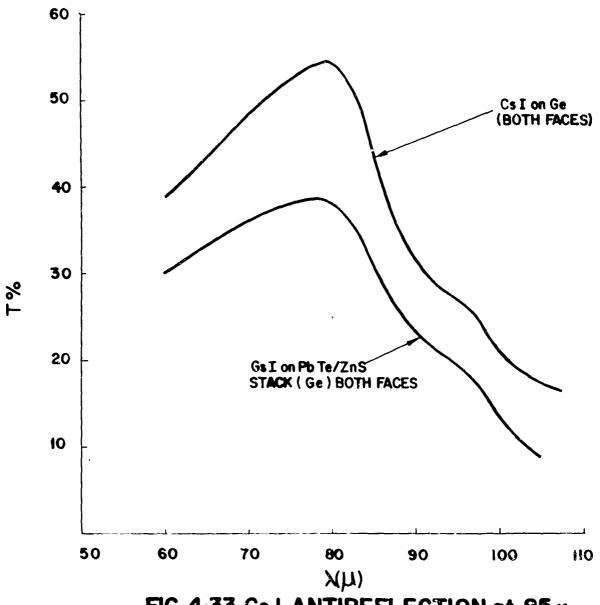
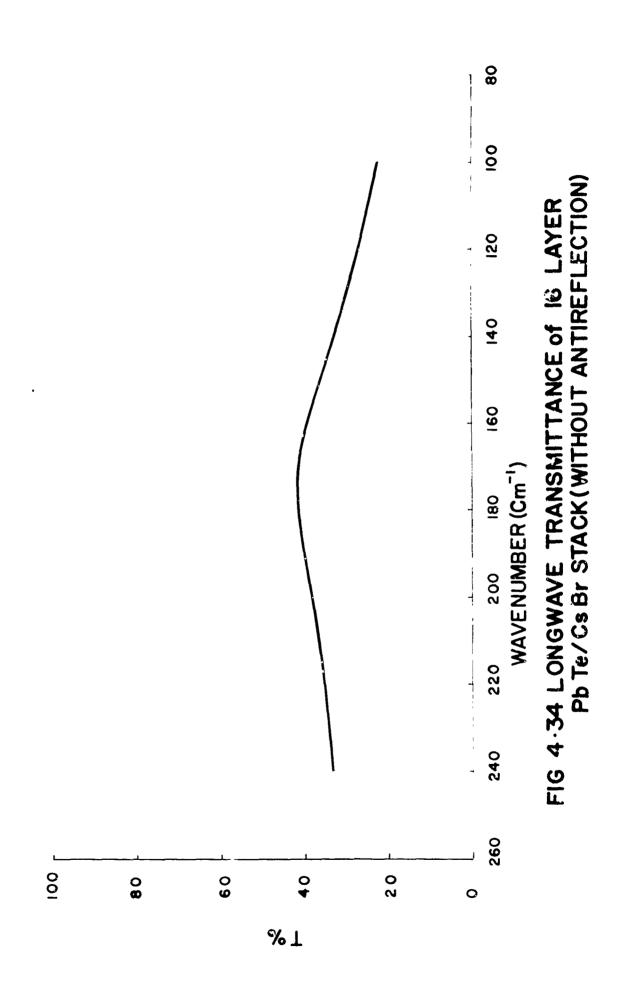
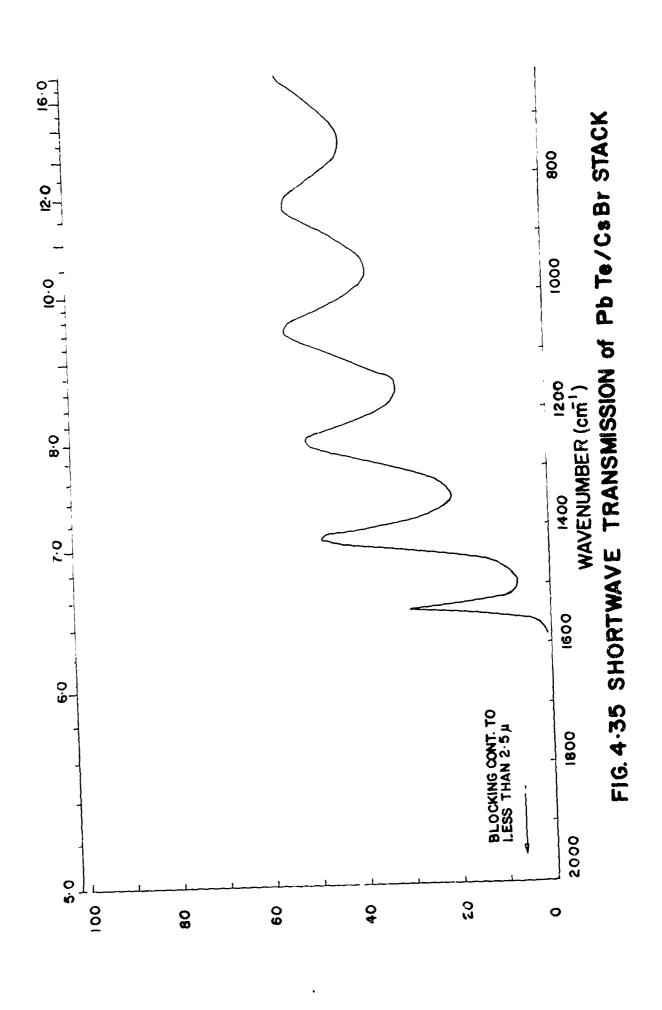


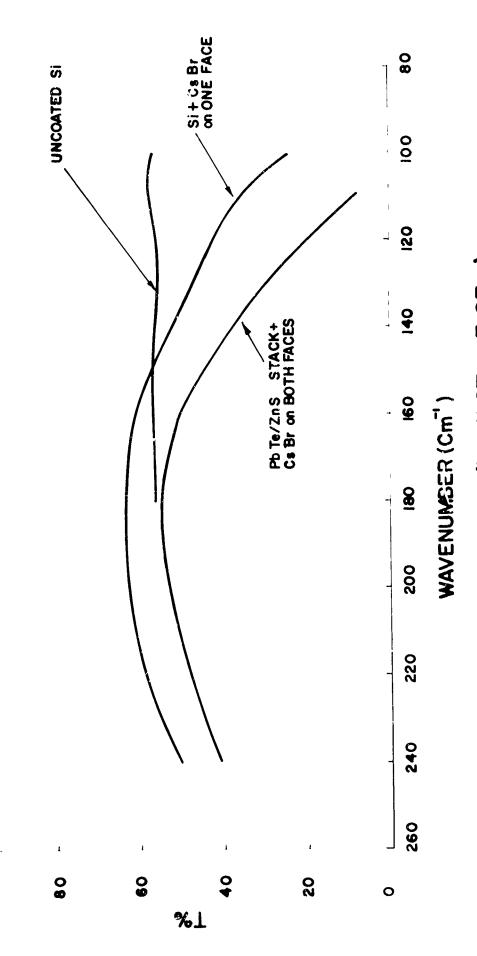
FIG. 4-32 CSI ANTIREFLECTION at 75µ (27 QWOT at 3-93 µ)



χμ)
FIG. 4·33 Cs I ANTIREFLECTION at 85μ
(33 QWOT at 3·93μ)

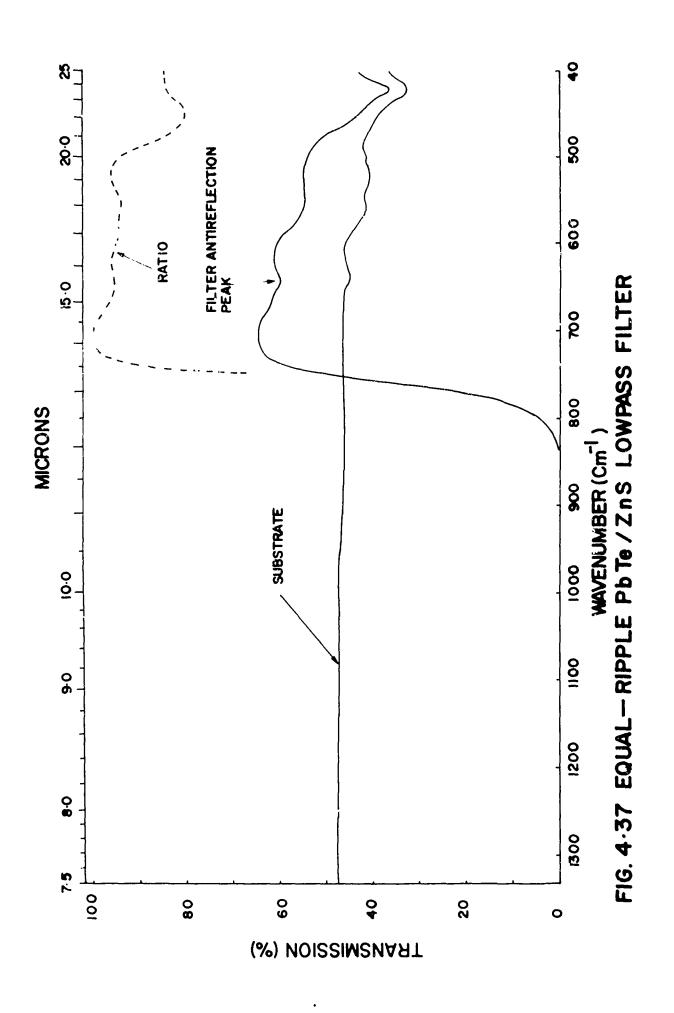






<u>0</u>

FIG 4.36 CSBr ANTIREFLECTION (19 QWOT at 3.93 µ)



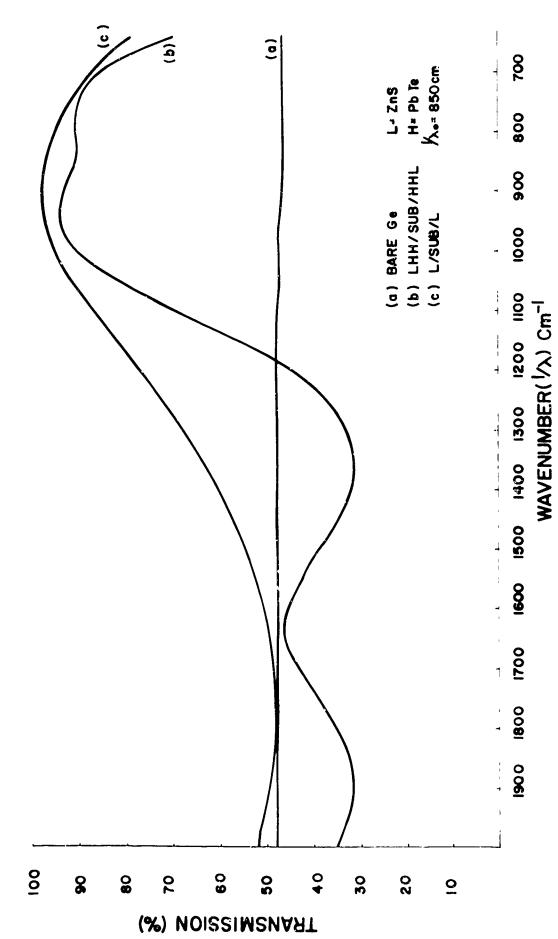
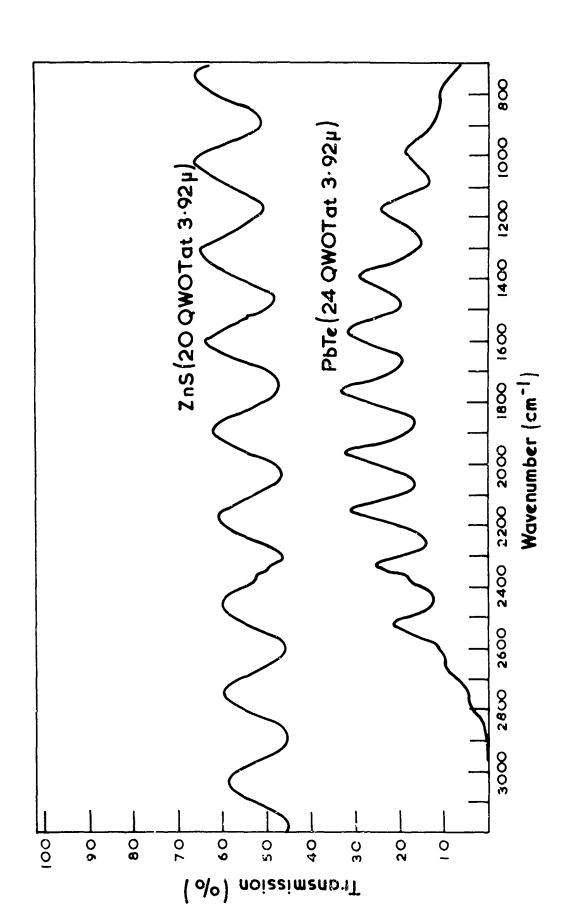
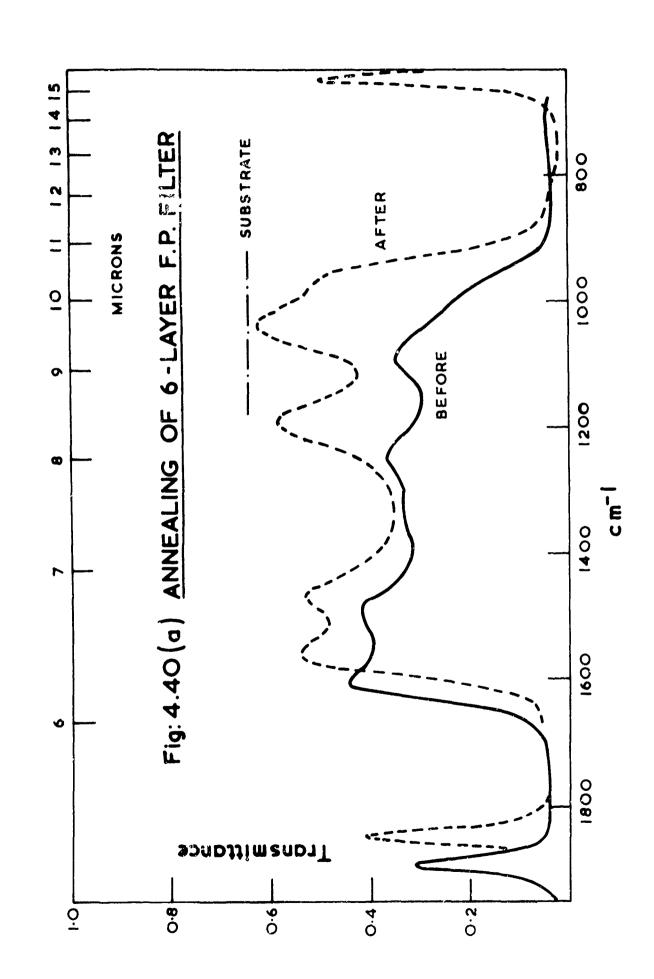
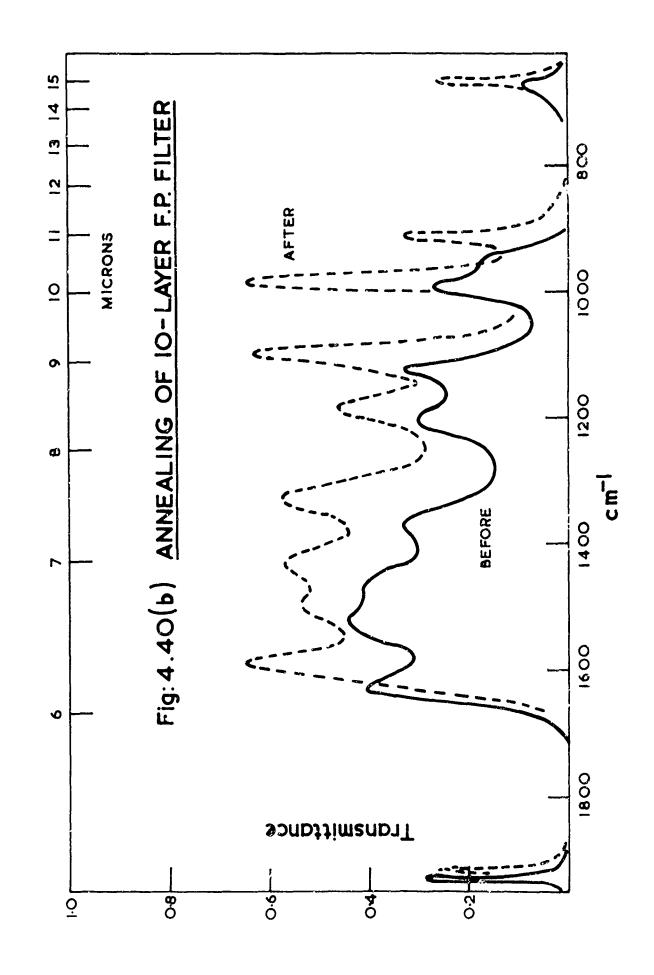


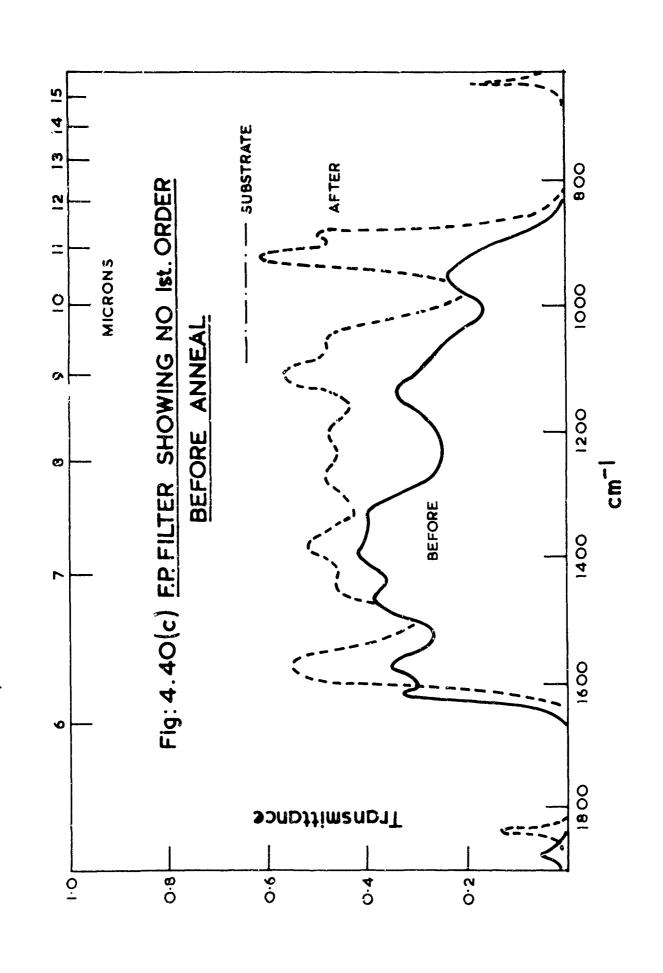
FIG. 4.38 ANTIREFLECTION of GERMANIUM



TRANSMISSION OF PbTe AND ZnS COLLECTED SEPARATELY DURING A FILTER DEPOSITION Fig: 4.39







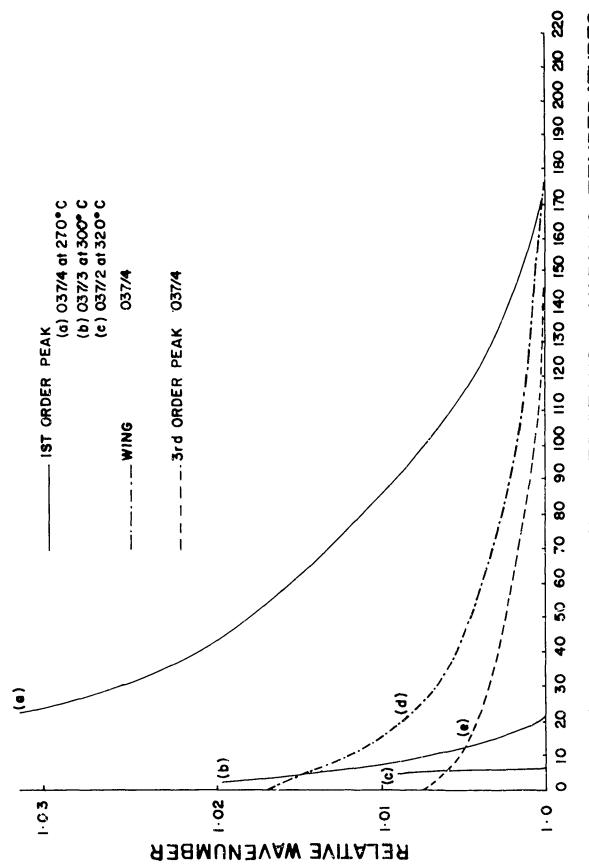


FIG. 4.41 (a) SPECTRAL SHIFT of F.P. PEAKS at VARIOUS TEMPERATURES

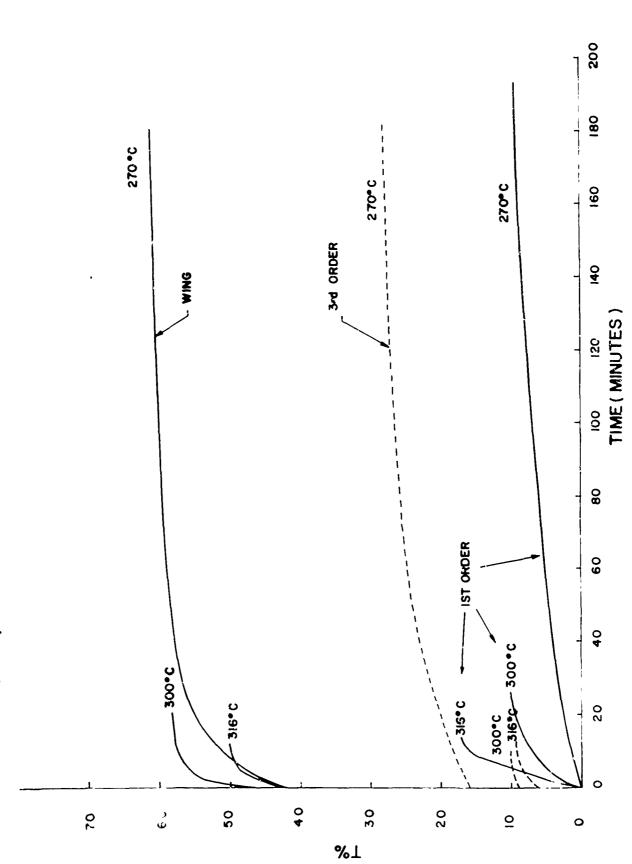


FIG. 4-41(b) F.P. INCREASED TRANSMITTANCE at VARIOUS TEMPERATURES

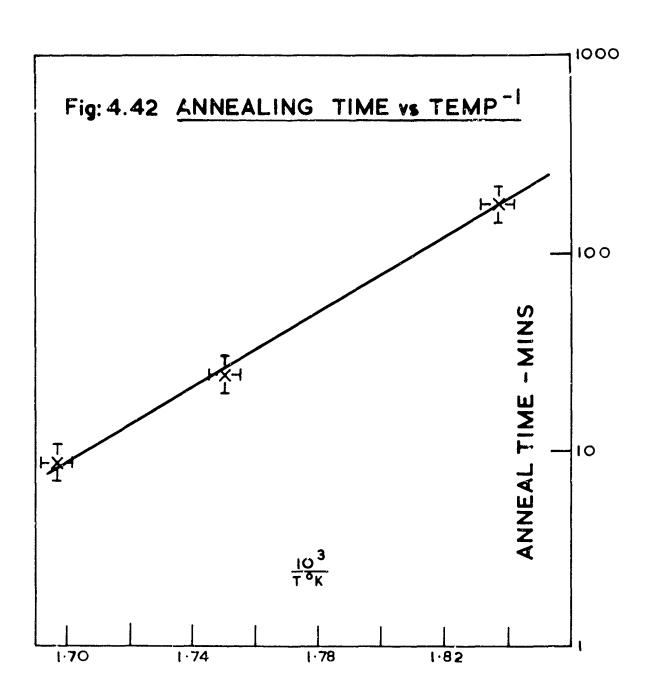
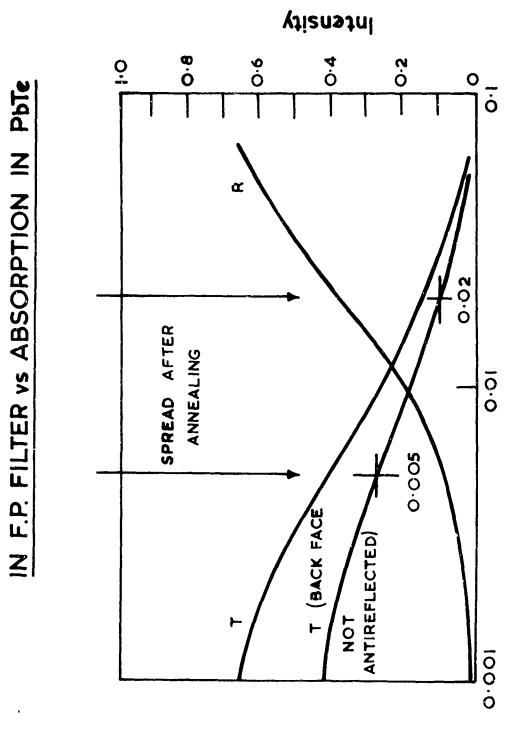
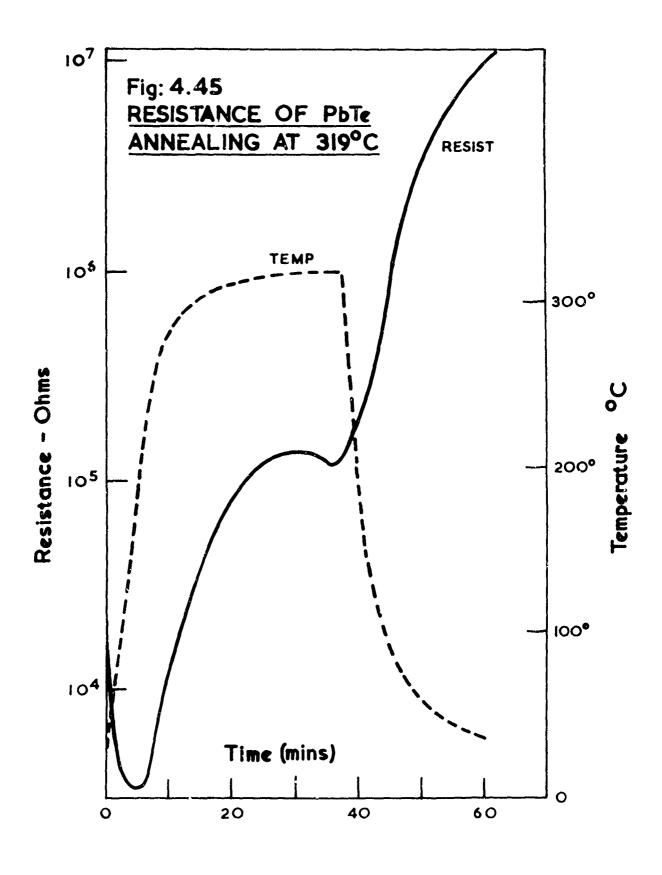


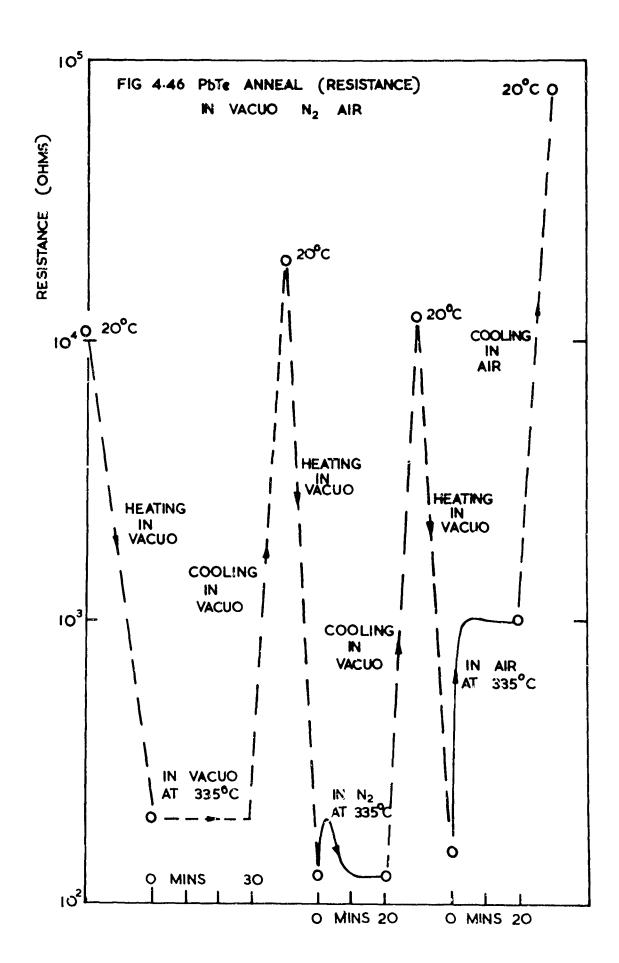
Fig. 4.43 CALCULATED Ist. ORDER SHIFT % CHANGE IN P VS CHANGE IN PLTE INDEX 7 <u>ო</u> 0 TAIHS %

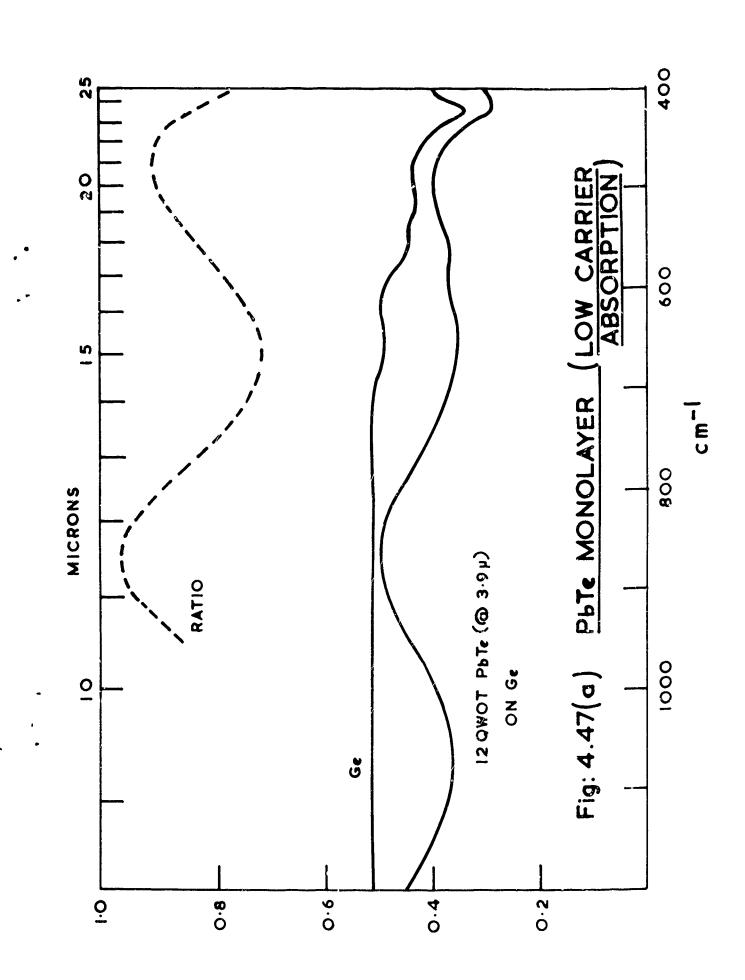
Fig: 4.44 CALCULATED TRANSMITTANCE/REFLECTANCE

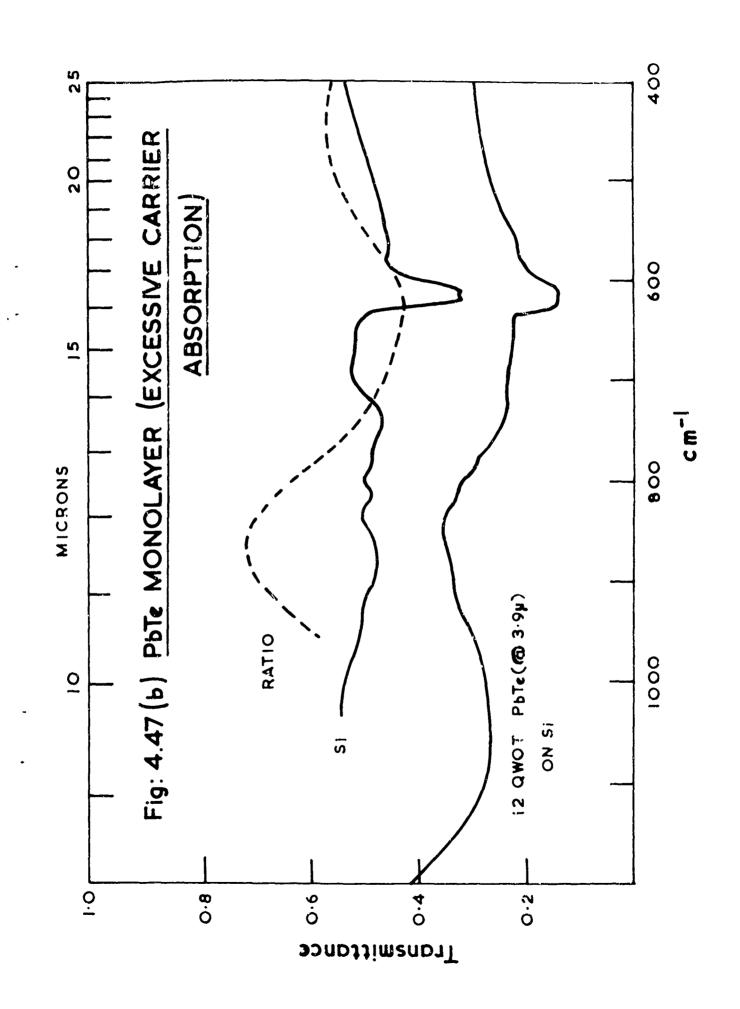


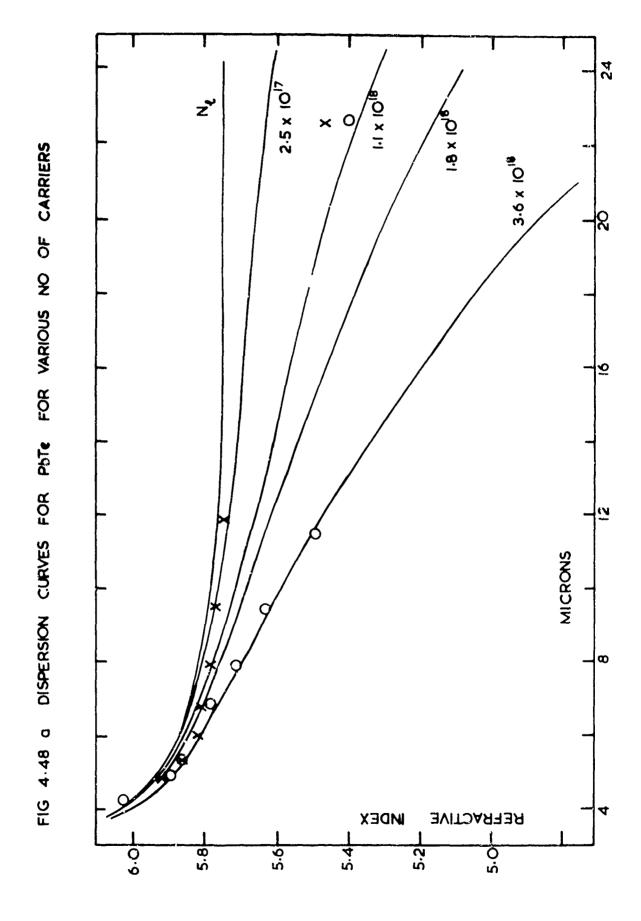
K in PbTe



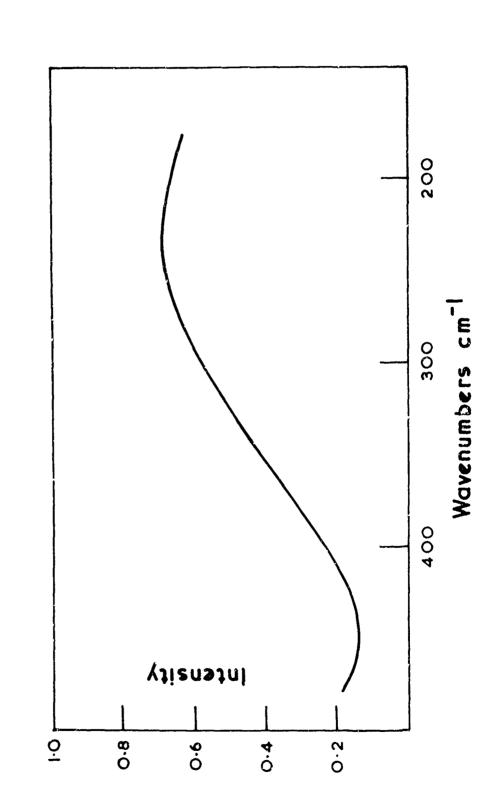


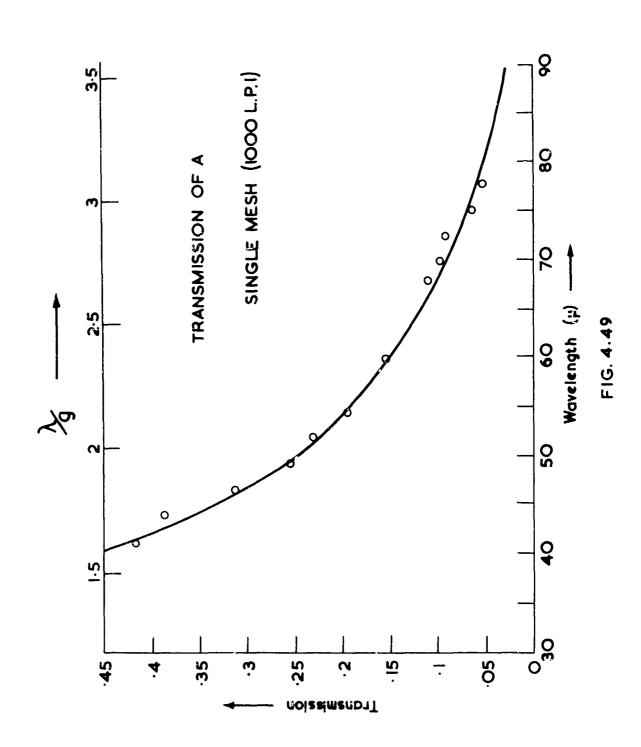


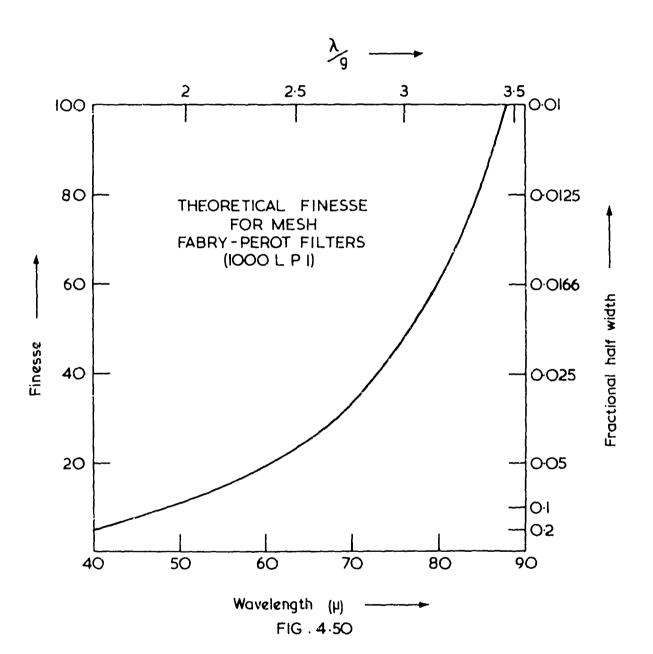


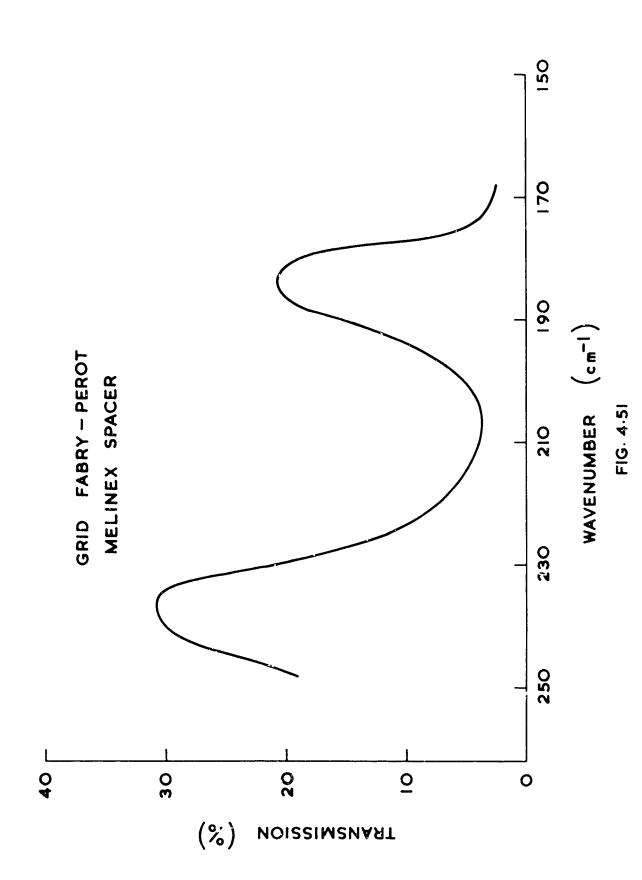


(AS FRACTION OF REFLECTANCE OF SI MIRROR) Fig:4.48(b) REFLECTANCE OF PbTe MONOLAYER

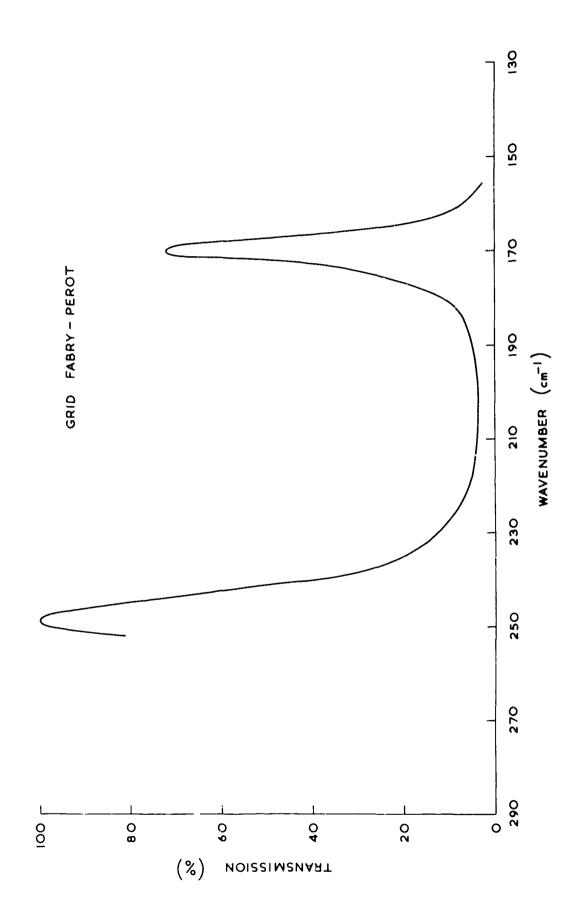


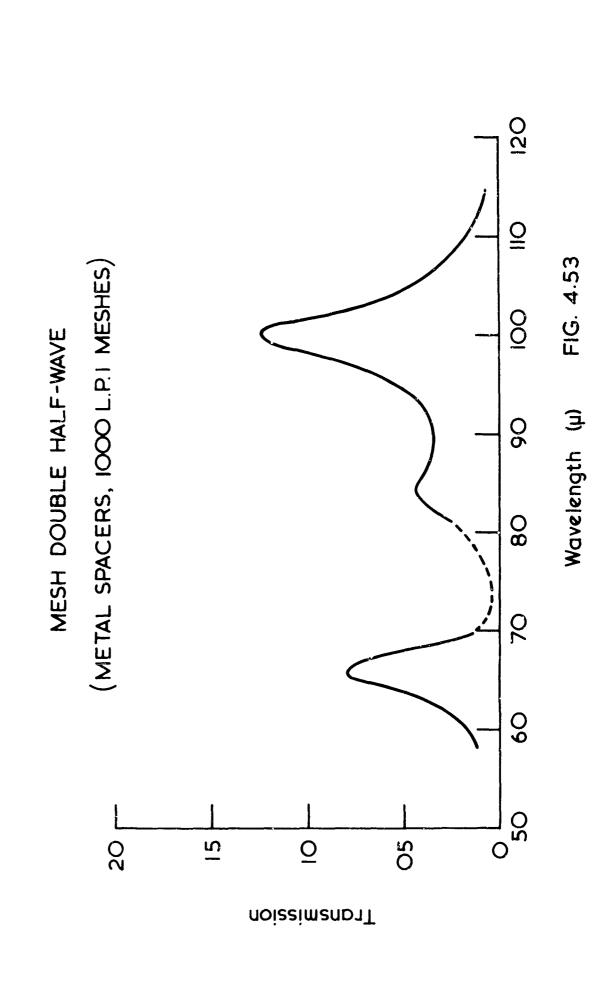












FILTER FABRICATION-EXPLODED VIEW

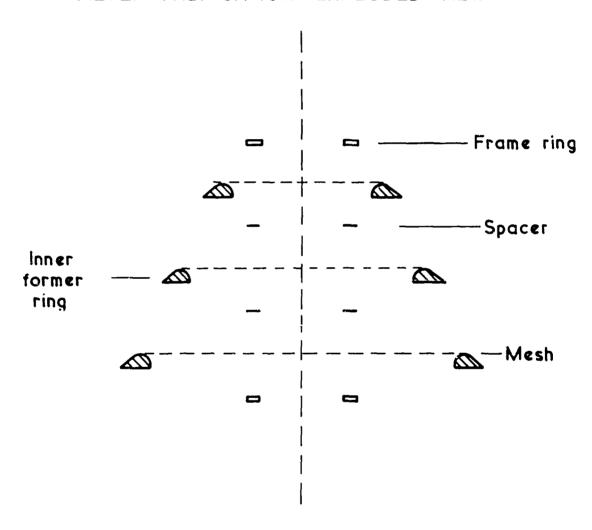
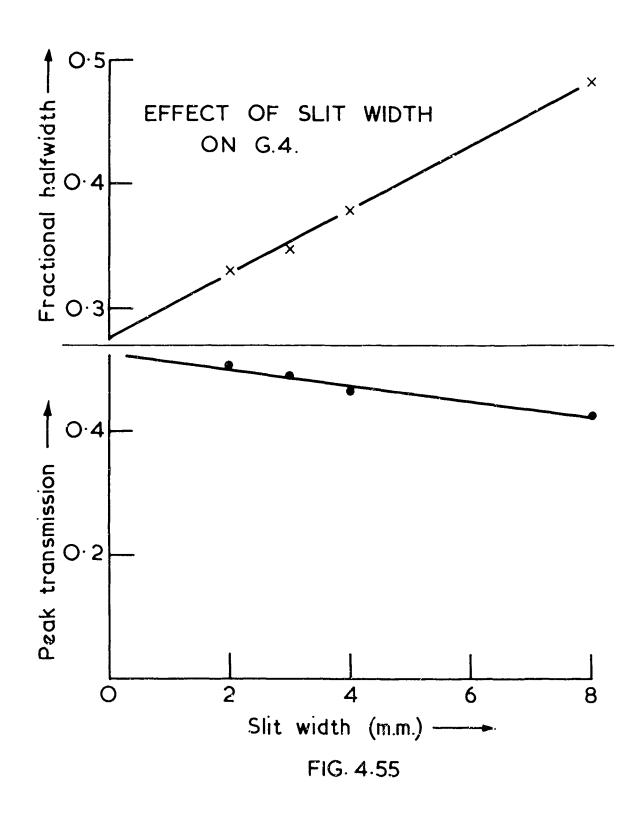
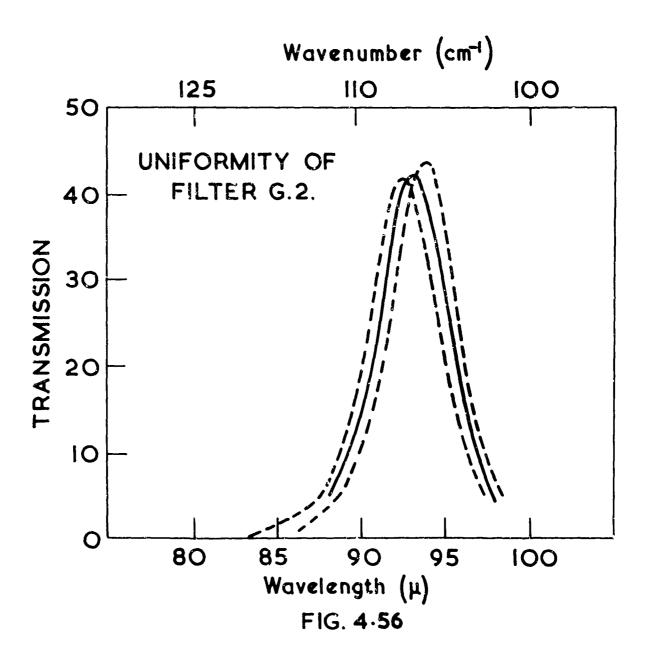
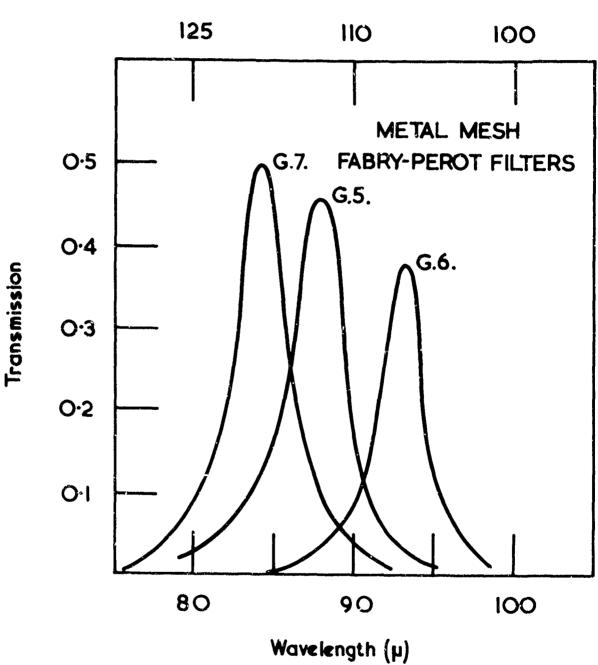


FIG. 4.54





Wavenumber (cm-1)



svelength (µ) FIG. 4.57

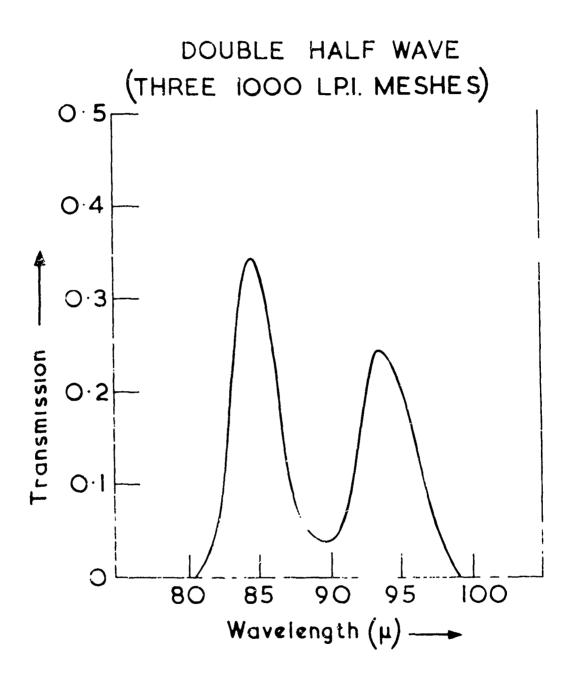


FIG. 4.58

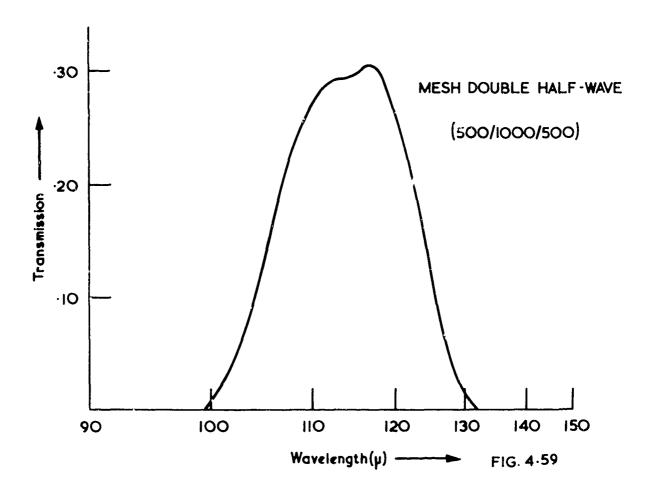
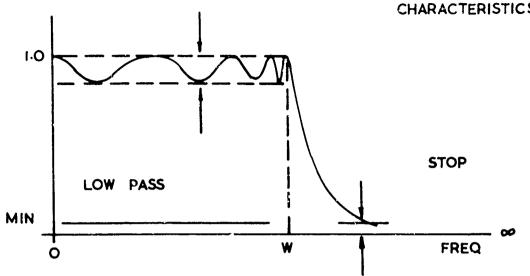
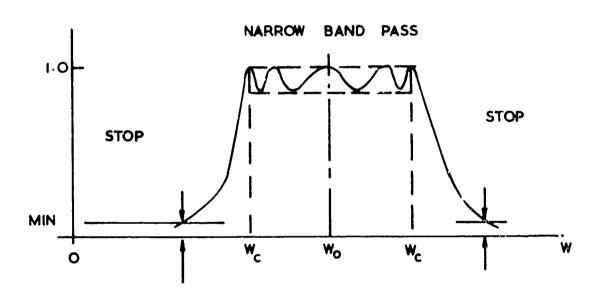
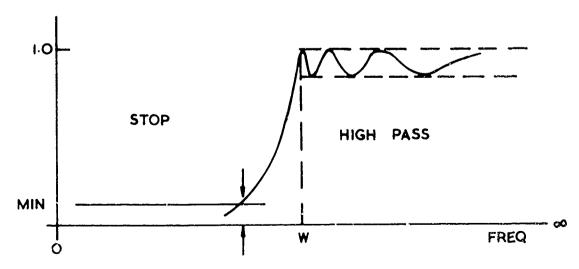


FIG 5-1 IDEALISED FILTER CHARACTERISTICS







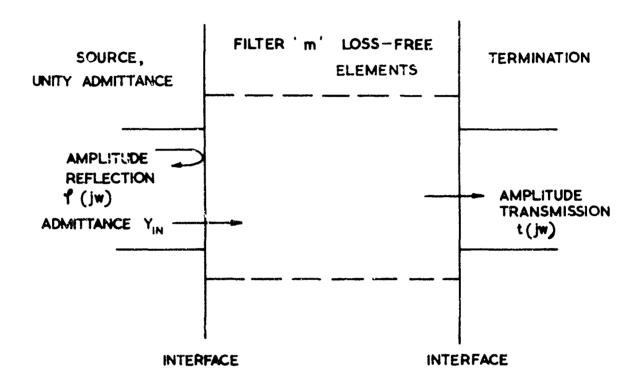


FIG 5.2 INTERFACE DESCRIPTION

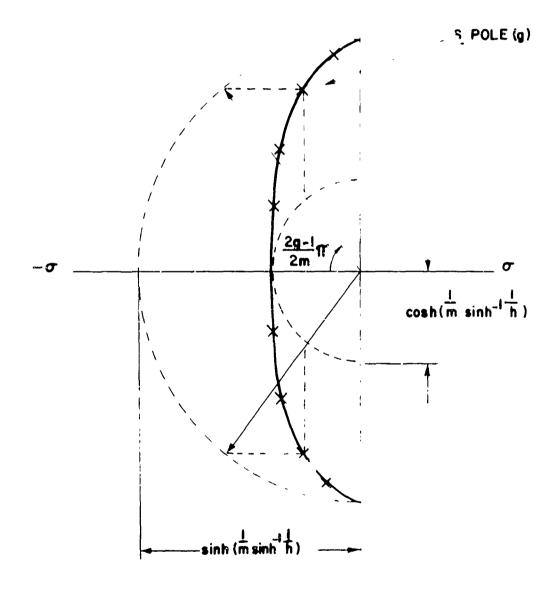
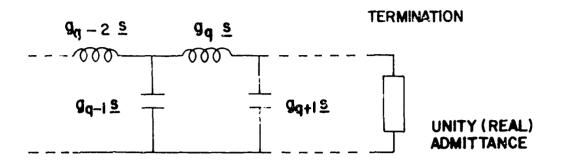


FIG. 5-3 S-PLANE LOCUS AND CONSTRUCTION



IN FIG.5.3,
=
$$-\sin\frac{(2q-1)}{2m}\pi \sinh(m^{-1}\sinh^{-1}\pm)$$

+ $j\cos(\frac{2q^{-1}}{2m})\pi\cosh(m^{-1}\sinh^{-1}\pm)$ ETC.

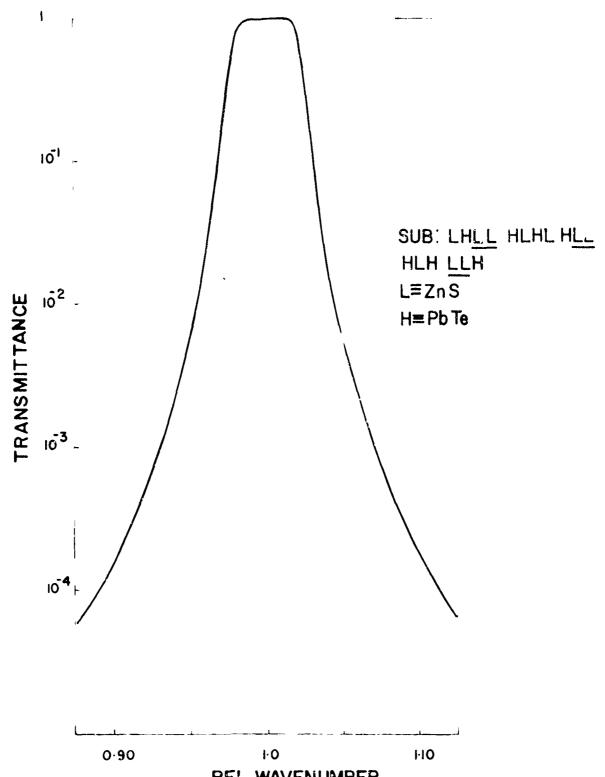
FOR the SIMPLEST LOW PASS EQUIVALENT CIRCUIT (as SHOWN) IMPEDANCE is GIVEN for SERIES ELEMENTS, ADMITTANCE for SHUNT ELEMENTS,

WHERE
$$q_1 = \frac{2 \sin \frac{\pi}{2m}}{\sinh(\frac{1}{m} \sinh^{-1} \frac{1}{h})}$$

$$q_{q-1}q_q = \frac{4\sin{(2q-1)} \pi \sin{(2q+1)} \pi}{\frac{2m}{\sinh^2(\frac{1}{m}\sinh^{\frac{1}{2}}) + \sin^2{\frac{q}{m}}}}$$
 ETC.

FIG.5-4 TCHEBYSHEV CIRCUIT PARAMETERS

FIG 5 5 COMPUTED TCHEBYSHEV FILTERS TABLE 5-1) (PARAMETERS IN 101 TRANSMITTANCE IŌ² LOW PASS 2 x 10⁻⁵ 103 FREQ 101 TRANSMITTANCE 102 HIGH PASS 2 x 10⁻⁵ FREQ 10-3 2



REL.WAVENUMBER
FIG. 5-6 COMPUTED TCHEBYSHEV NARROWBAND
FILTER(I6 LAYER, TRIPLE HALFWAVE DESIGN)

FIG. 5.7 SPECTRAL SENSITIVITY (REFLECTIVITY) OF LAYERS IN IO-LAYER RADIOMETER F.P. FILTER

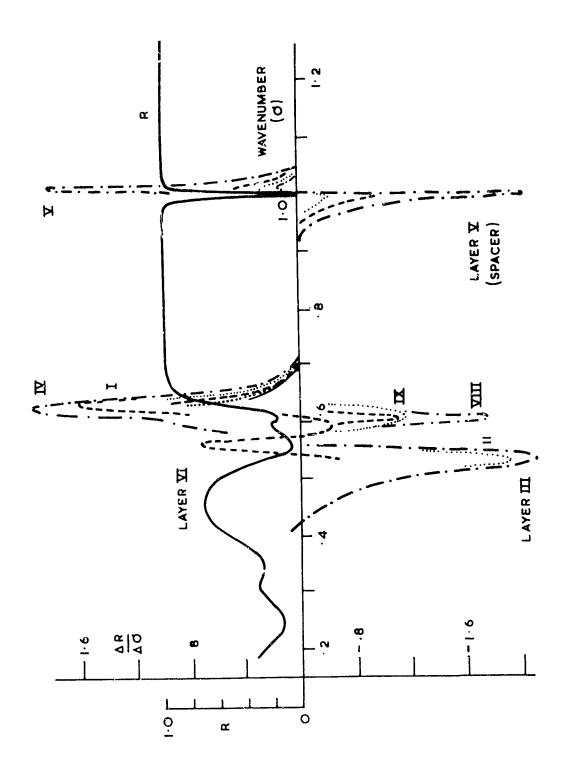
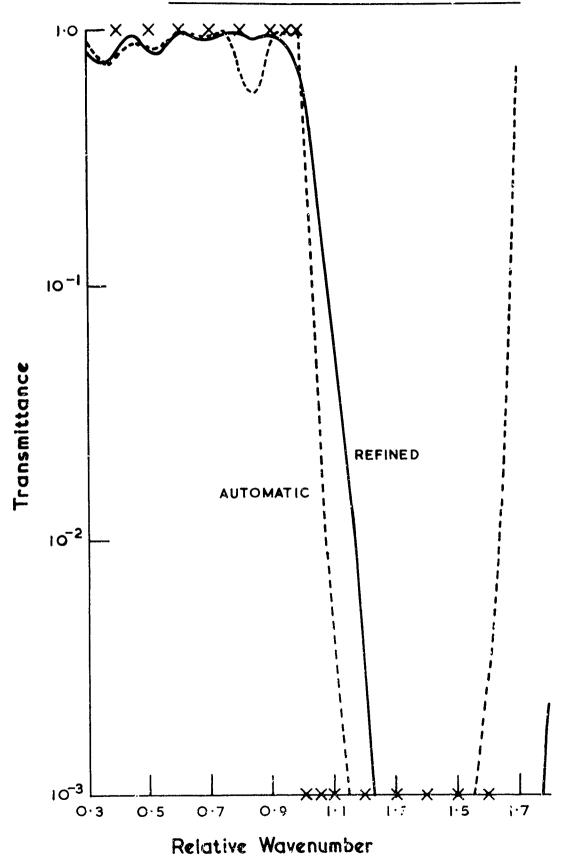
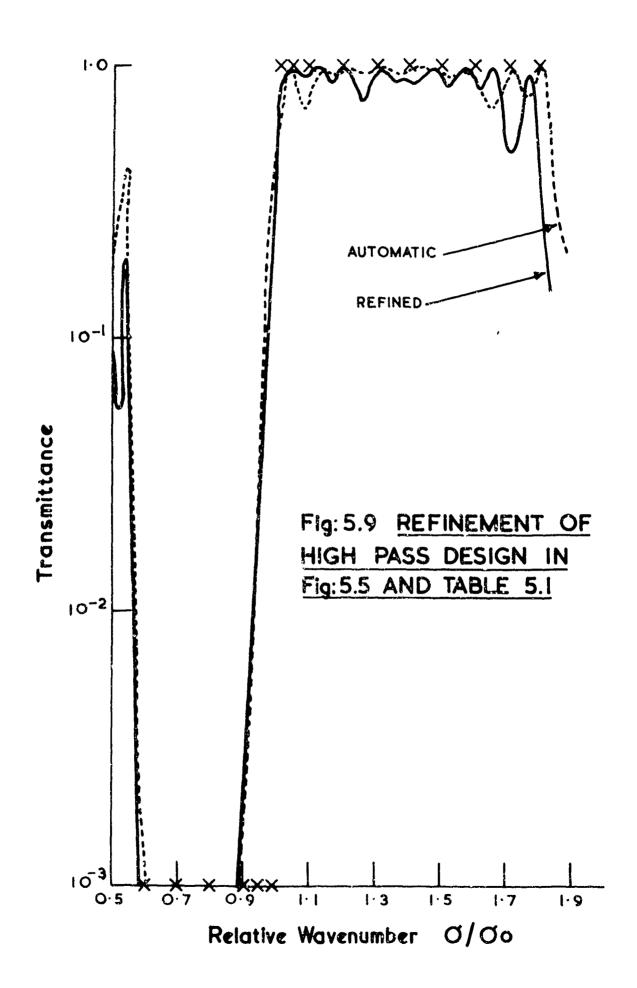


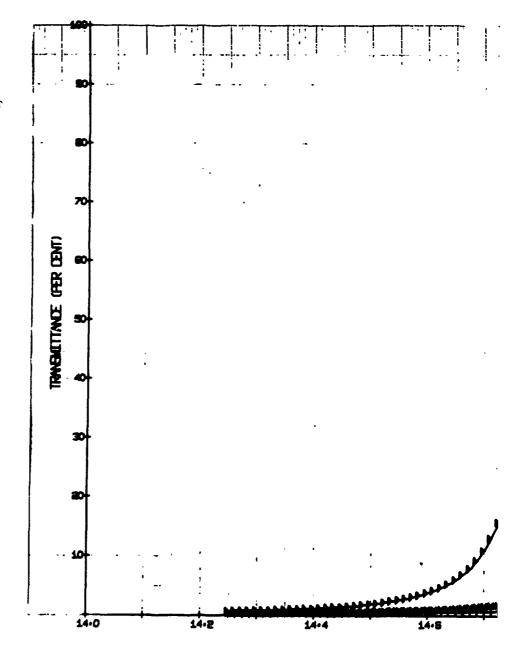
Fig: 5.8 <u>REFINEMENT OF LOW PASS</u>

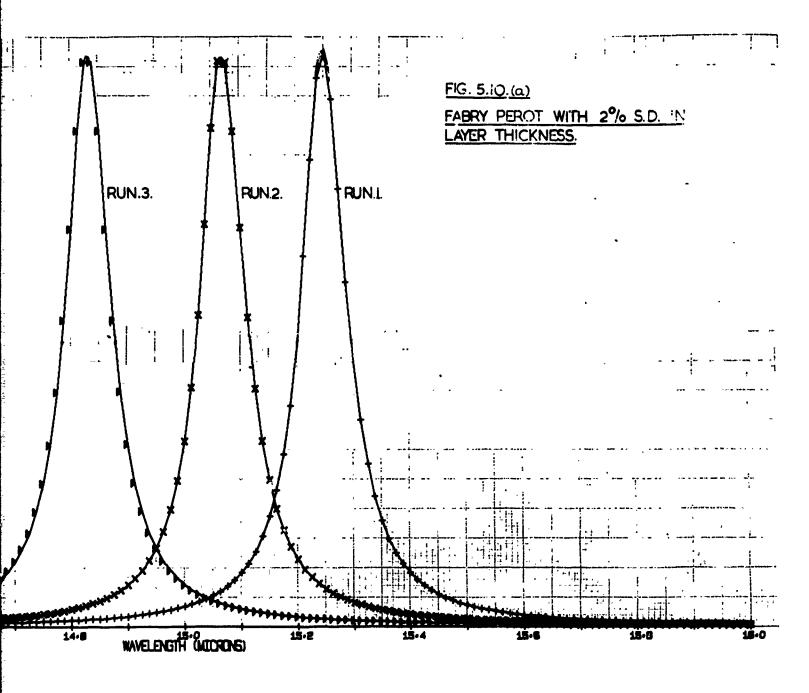
<u>DESIGN IN FIG: 5.5 AND TABLE 5.1</u>



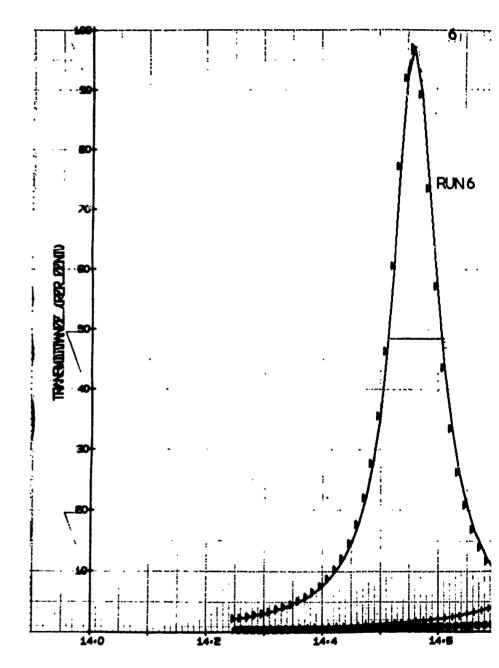


	R FILTER WAVELENG 1,0000	TH* 1	5. 0u90 N	MICRONS
	D DEVIATIO	V=	2.0000 P	ER CENT
CASE NO.	-			
LAYER IN		LAYER TH	HCKNESS	5、
2.350	-	0. 25	-	1
5.300	-	0, 24		1
2,350		0.25		j
5.300		0, 25	30	1
2.350	-	0.26		>1
5.300	_	0.50		1
2.350	-	0, 25		}
5.300		0, 25		
2.350		0. 24]
5.300	U	0, 25	22)
CASE NO.	2			
LAYER IN	DEX	LAYER TH	ICKNESS	ì
2.350		0.25)
5.300	D	0, 24	44	1
2,350	0	0.25	50	1
5.300)	0. 24	54	1
2.350	3	0, 25	54	\ 2
5.300)	0,50	03	ſ
2.350		0, 24	95	1
5.3000		0, 25	86	ı
2.3500		0, 25	24	j
5.3000)	0, 25	58 -	,
CASE NO.				
LAYER IN		AYER TH	CKNESS	
2,3500	•	0, 259	90)
5.3000		0, 246	8	
2,3500		0.249	33	
5.3000		0. 246	55	
2.3500		0. 253	14	∖ 3
5.3000		0.490	-	
2.3500		0. 246		
5.3000		0. 252		
2.3500		0.252		
5.3000		0. 253	2 -	,
END OF CA	LCULATION	S		

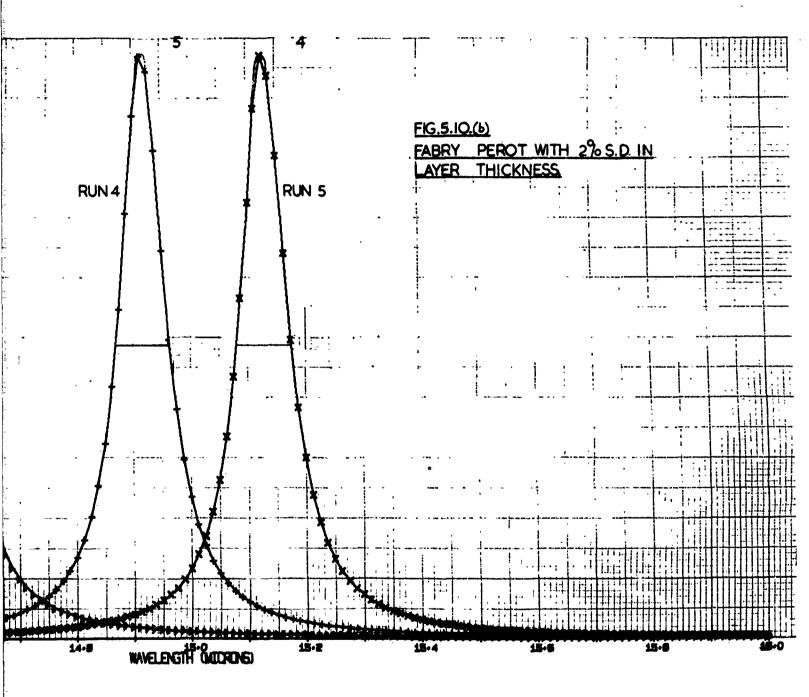




10-LAYER FILTER MONITOR WAVELE		15, 000	00 MICRONS
RAIR* 1.0000			
RSUB* 4.0000			
STANDARD DEVIAT	NON-	2,000	00 PER CENT
CASE NO. 1			
LAYER INDEX	LAYER	THICKNE	:SS _s
2,3500		012493)
5.3000	1	0, 2421	Ì
2.3500	1	0.2552	
5.3000	1	0. 2487	İ
2,3500		0.2474	74
5,3000	:	9, 4929	ſ
2,3500		0. 2558	1
5.3000		0. 2555	i
2,3590		0, 2454	
5,3000	•	0. 2507)
CASE NO. 2			
LAYER INDEX	LAYER	THICKNE	:SS.
2,3500). 2513	1
5.3000		. 2573	
2.3500	C	2385	i
5.3000	O	. 2450	!
2.3500	0	. 2519	5 5
5.3000	0	. 5082	ſ
2.3500	0	. 2515	
5,3000	0	. 2493	
2.3500	0	. 2424	
5.3000	0	2559)
CASE NO. 3			
LAYER INDEX	LAYER	THICKNE	SS、
2.3500		. 2496	·)
5.3000		. 2436	ŀ
2.3500	0	. 2580	
5,3000	0	. 2526	
2.3500	0	. 2526	_ 6
5.3000	0	. 4759	ſ
2.3500	0	. 2435	1
5.3000		. 2444	- 1
2.3500	0.	. 2457	j
5,3000		2572	ノ

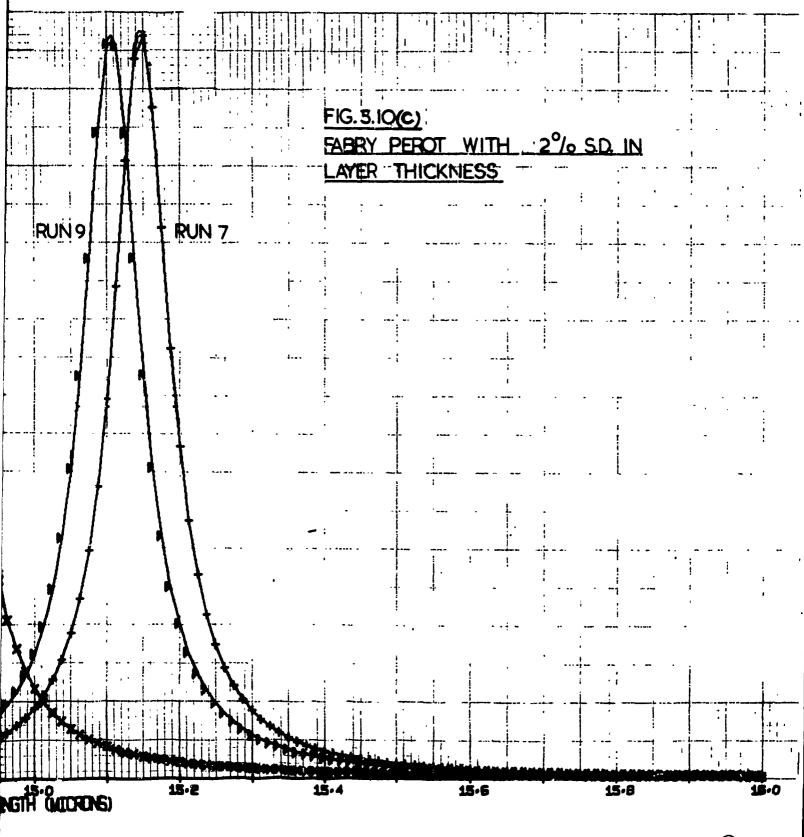


END OF CALCULATIONS

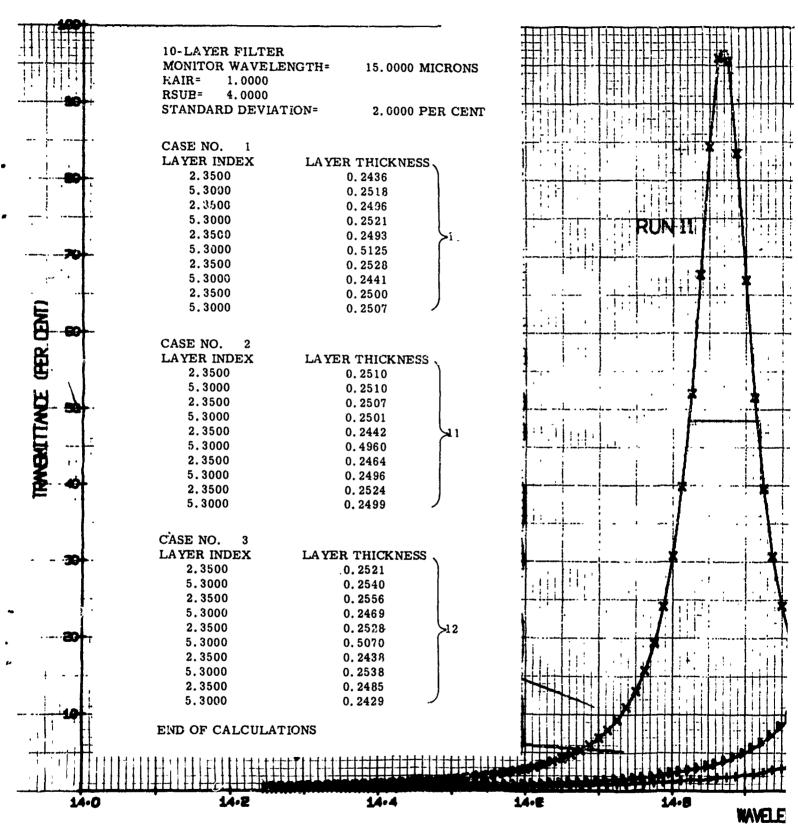


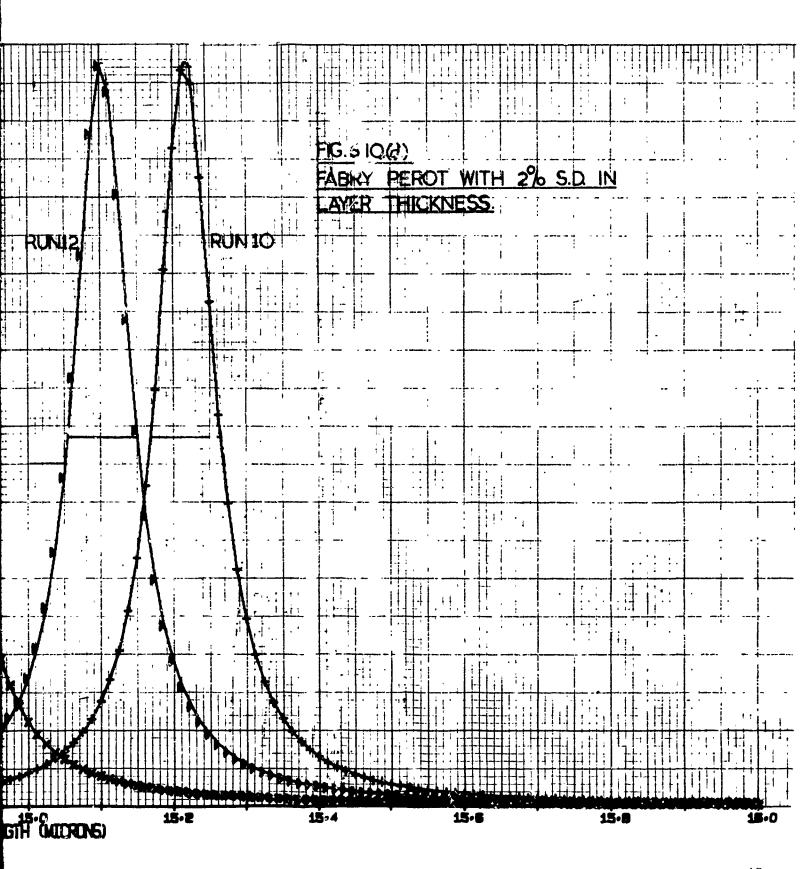


14-0	2.3500 5.3000 END OF CALCULATION	0. 2521 0. 2534 S	14-6	MAVE.
30	CASE NO. 3 LAYER INDEX 2.3500 5.3000 2.3500 5.3000 2.3500 5.3000 2.3500 5.3000 5.3000	0. 2579 0. 2467 0. 2596 0. 2465 0. 2475 0. 5051 0. 2517 0. 2548		
TRANSAUTTANDE 6 88	2.3500 5.3000 2.3500 5.3000 2.3500 5.3000	0.4996 0.2483 0.2408 0.2474 0.2581		
TIMOE (PER CENT)	2.3500 5.3000 2.3500 5.3000	YER THICKNESS 0. 2482 0. 2514 0. 2437 0. 2500 0. 2403	:	
CENT)	2.3500 5.3000 2.3500 5.3000	0. 2511 0. 2531 0. 2490 0. 2491	1	*
70	LAYER INDEX LATE	YER THICKNESS 0.2448 0.2474 0.2440 0.2597 0.2494 0.5065		RUN8
	10-LAYER FILTER MONITOR WAVELENGTH RAIR= 1.0000 RSUB= 4.0000 STANDARD DEVIATION= CASE NO. 1	2.0000 PER CENT		
	Herrich and American	111111111111111111111111111111111111111		

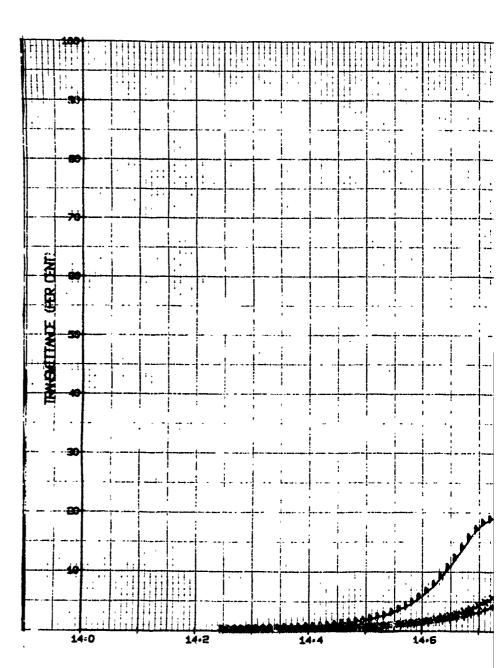


P



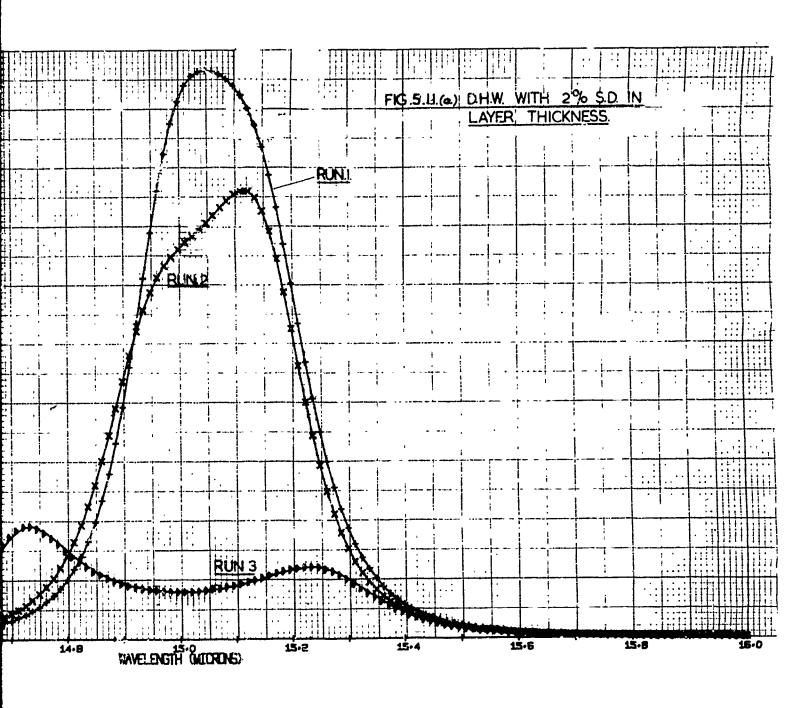


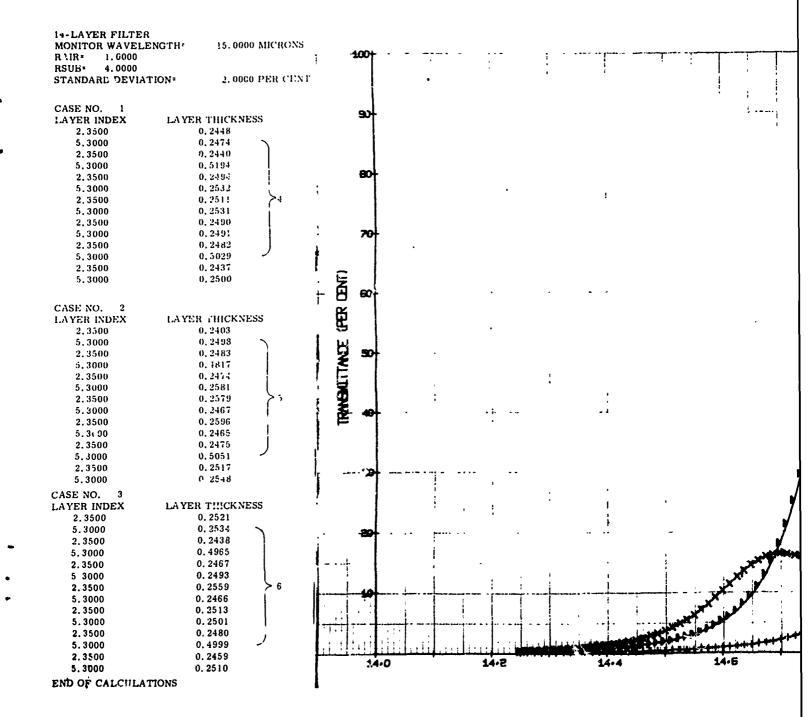
14-LAYER FILTER MONITOR WAVELENC RAIR* 1.0000 RSUB* 4.0000 STANDARD DEVIATIO	TH- 15.0000 MICRONS 2.0000 PER CEN
STANDARD DEVIATION CASE NO. 1 LAYER INDEX 2.3500 5.3000 2.3500 5.3000 2.3500 5.3000 2.3500 5.3000 2.3500 5.3000 2.3500 5.3000 2.3500 5.3000 5.3000 5.3000 5.3000 5.3000 5.3000	N= 2.0000 PER CEN LAYER THICKNESS 0.2436 0.2518 0.2496 0.5043 0.2493 0.2562 0.2528 0.2441 0.2500 0.2507 0.2510 0.5021 0.2507 0.2501
CASE NO. 2 LAYER INDEX 2.3500 5.3000 2.3500 5.3000 2.3500 5.3000 2.3500 5.3000 2.3500 5.3000 2.3500 5.3000 2.3500 5.3000 2.3500 5.3000 2.3500 5.3000	0. 2501 LAYER THICKNESS 0. 2442 0. 2480 0. 2464 (, 4992 0. 2524 0. 2449 0. 2521 0. 2530 0. 2556 0. 2469 0. 2528 0. 5070 0. 2438 0. 2538
CASE NC. 3 LAYER INDEX 2.3500 3.3090 2.3500 5.3000 2.3500 5.3090 2.3500 5.3090 2.3500 5.3090 2.3500 5.3090 2.3500 5.3090 2.3500 5.3090 2.3500 5.3090	LAYER THICKNESS 0, 2485 0, 2429 0, 2620 0, 5116 0, 2442 0, 2574 0, 2502 0, 2477 0, 2449 0, 2518 0, 2434 0, 4894 0, 2457 0, 2513



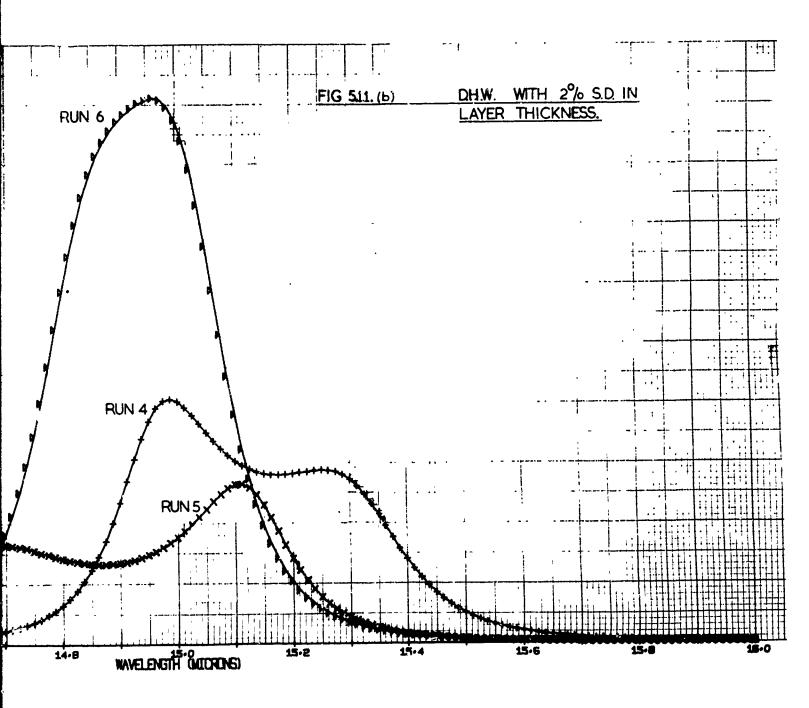
1

END OF CALCULATIONS

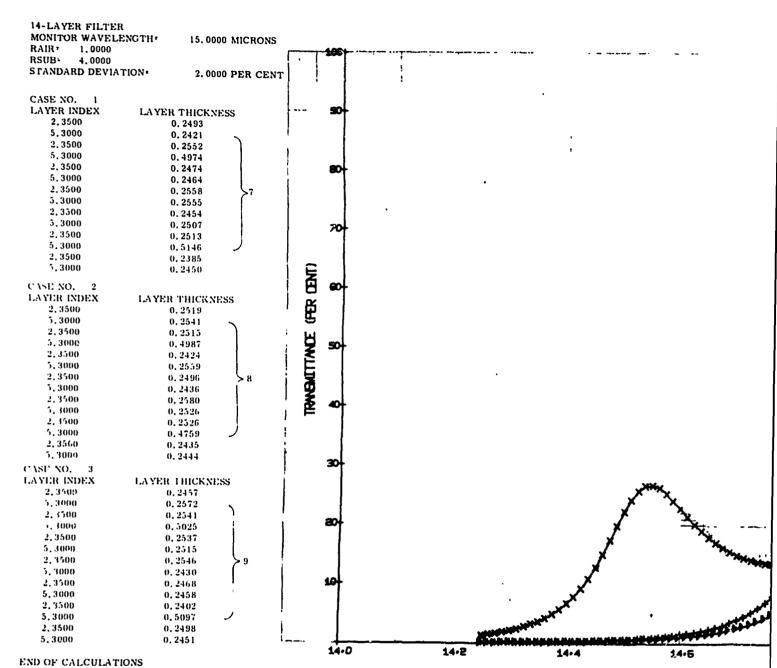


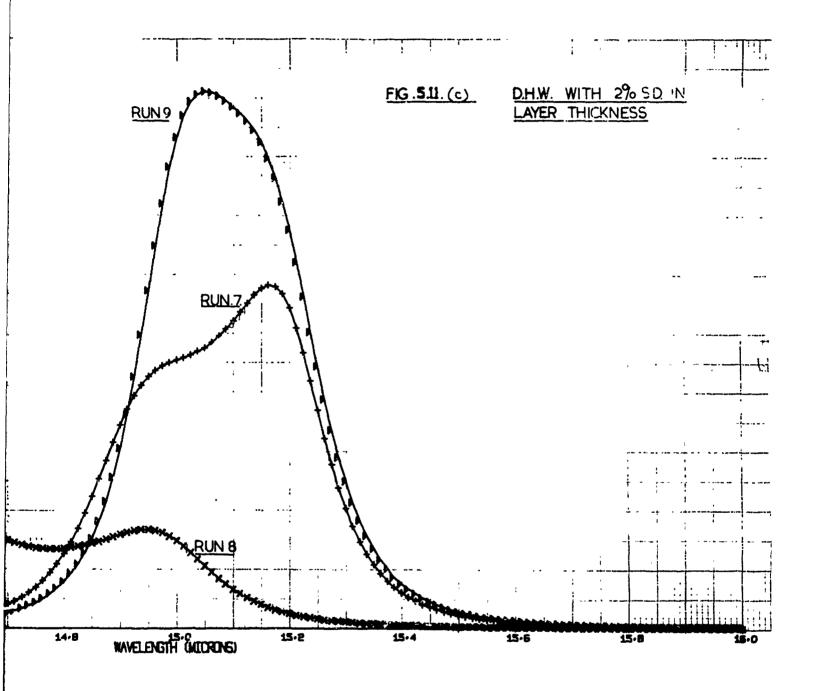


H

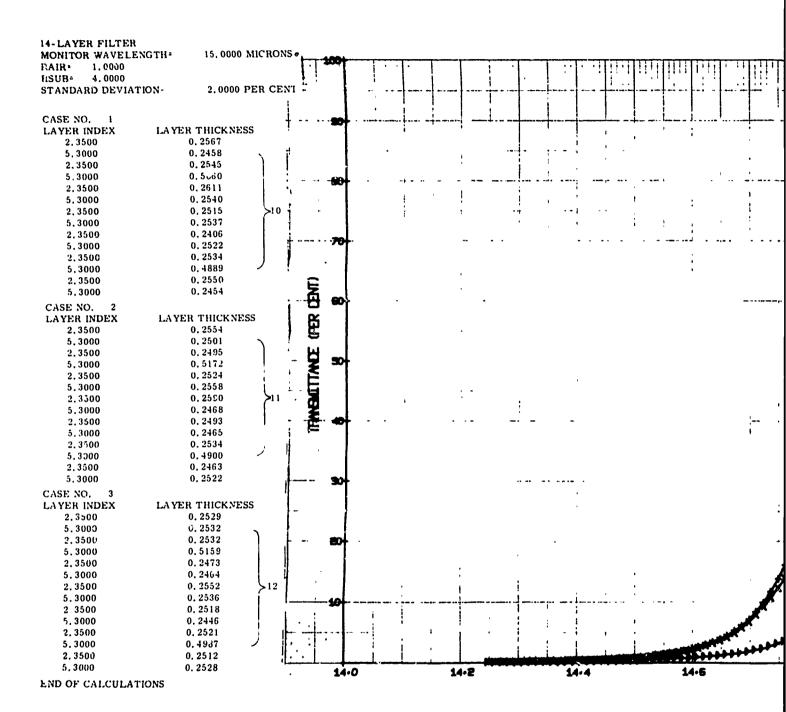


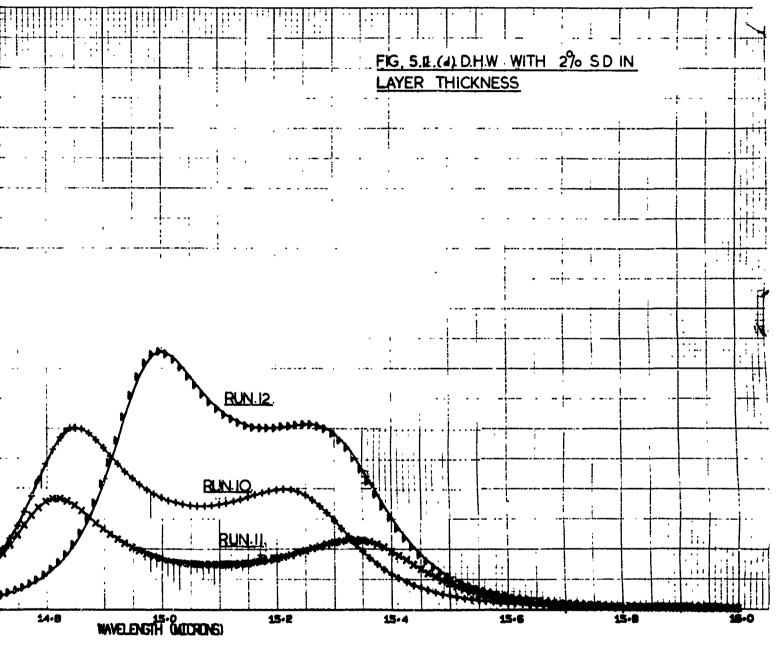






B





B

PEAK TRANSMISSION AS A FUNCTION OF HALF-WIDTH FOR THE DHW Ge/LHL HH LH LH LH LH LH LH EDR 2% 1.4% SD. IN LAYER THICKNESS.

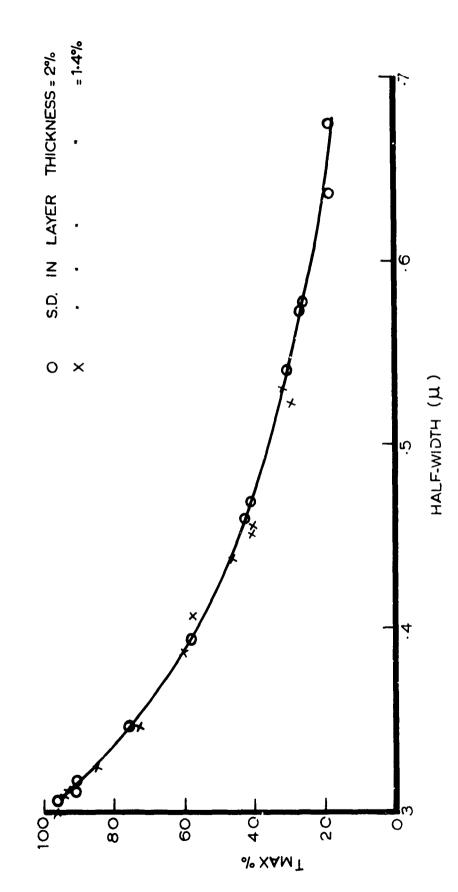
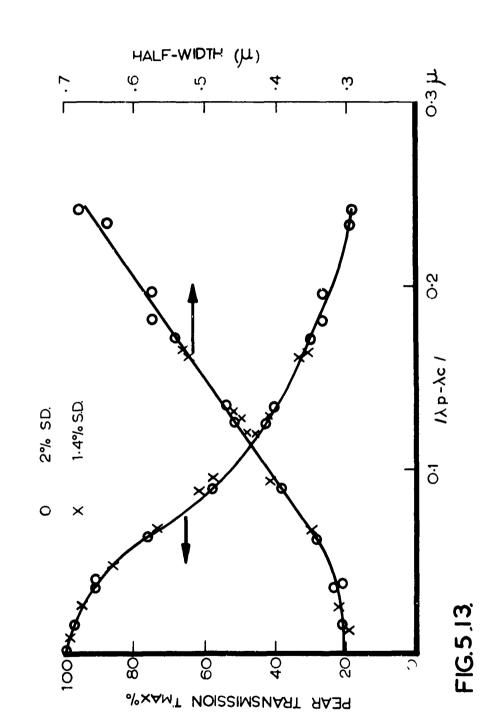
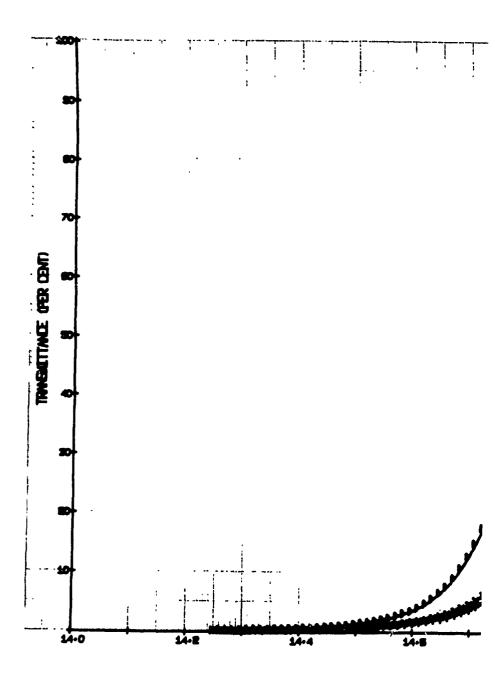


FIG. 5.12.

PEAK TRANSMISSION AND HALFWIDTH OF THE D.H.W. DESIGN Ge/LHLHHLHLHLHHLH HHLH AS A FUNCTION OF 1/20-1/20 FOR 2% AND 1.4% SD IN LAYER THICKNESS.



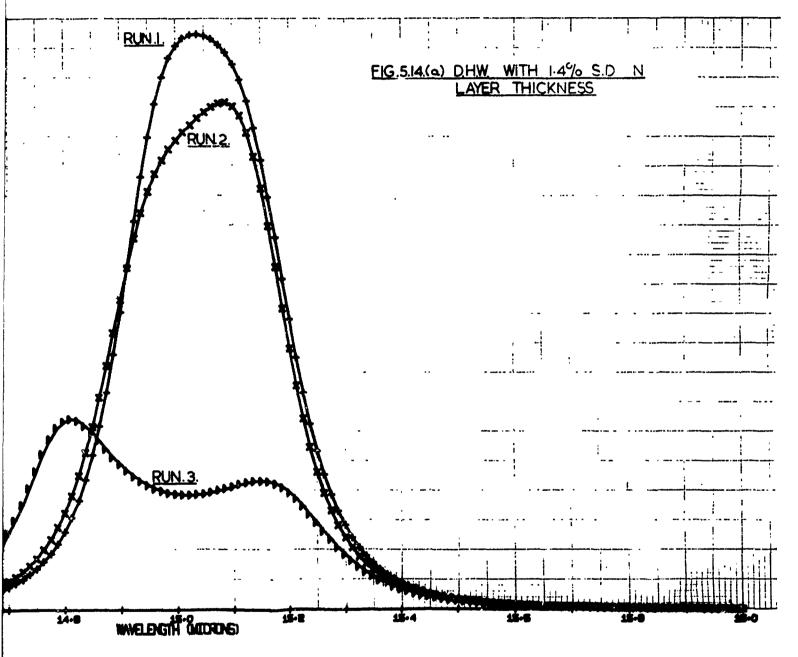
14-LAYER FILTER MONITOR WAVELENGTH: 15,0000 MICRONS RAIR* 1.0000 RSUB* 4.0000 STANDARD DEVIATION: 1.4000 PER CENT CASE NO. LAYER INDEX LAYER THICKNESS 2.3500 5.3000 0.2455 0.2512 2.3500 0.2497 0.5030 5,3000 2.3500 0.2495 5,3000 0.2543 2,3500 0.2519 5.3000 2.3500 5.3000 0.2458 0.2500 0.2505 2.3500 0.2507 5.3000 0.5015 2.3500 0.2505 5.3000 0.2501 CASE NO. LAYER INDEX LAYER THICKNESS 2.3500 0.2459 5.3000 0.2486 2.3500 0.2475 0.4994 5.3000 2.3500 0.2517 5.3000 0.2499 2.3500 0.2515 2 5.3000 2.3500 0.2528 0.2539 5,3000 0.2478 2.3500 0.2520 5.3000 0.5049 2,3500 0.2457 5.3000 0.2527 CASE NO. LAYER INDEX LAYER THICKNESS 2,3500 0.2490 5.3000 0.2450 2,3500 0.2584 5,300 0.5081 2.3500 0.2460 5.3000 0.2552 2,3500 0.2501 5,3000 0.2484 2.3500 0.2464 5.3000 0.2513 2,3500 0.2454 5.3000 0.4926 2,3500 0.2469



A

0.2509

5.3000

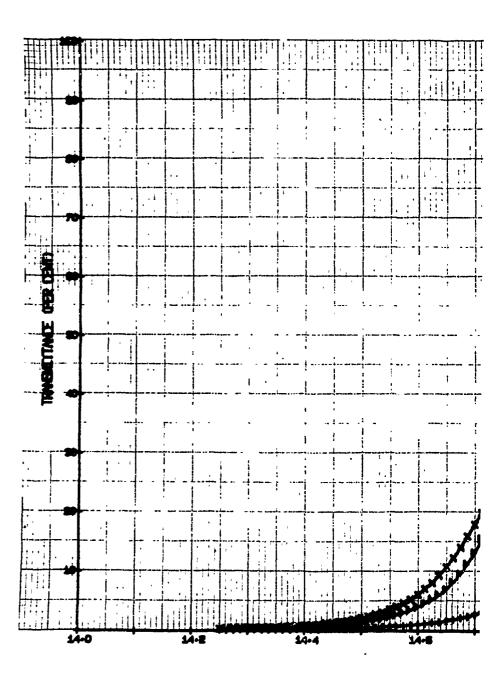


MONITOR WAVELENGTH: 15,0000 MICRONS RAIR= 1.0000 RSUB= 4.0000 STANDARD DEVIATION: 1.4000 PER CENT CASE NO. LAYER INDEX LAYER THICKNESS 2.3500 0.2464 5.3000 0.2482 2.3500 0.2458 5.3000 0.5136 2.3500 0.2496 5.3000 0.2523 2.3500 0.2508 0.2521 5.3000 2.3500 0.2493 5.3000 0.2494 2.3500 0.2487 5.3000 0.5020 2.3500 0.2455 5.3000 0.2500 CASE NO. LAYER INDEX LAYER THICKNESS 2,3500 0.2432 5.3000 0.2498 2.3500 0.2488 5.3000 0.4872 2.3500 0.2482 0. 2557 5,3000 2,3500 0, 2555 5.3000 0.2477 2.3500 0.2567 5.3000 0.2475 2.3500 0.2482 5.3000 0.5036 2,3500 0.2512 5.3000 0.2534 CASE NO. LAYER THICKNESS LAYER INDEX 2.350ນ 5.3000 0.2515 0.2524 2,3400 0.2456 0.4975 5.3000 2.3500 0.2477 5.3000 0.2495 2.3500 0.2541 5.3000 0.2476 2.3500 0.2509 5.3000 0.2501 2.3500 0.2486 5.3000 0.4999

0.2471

0.2507

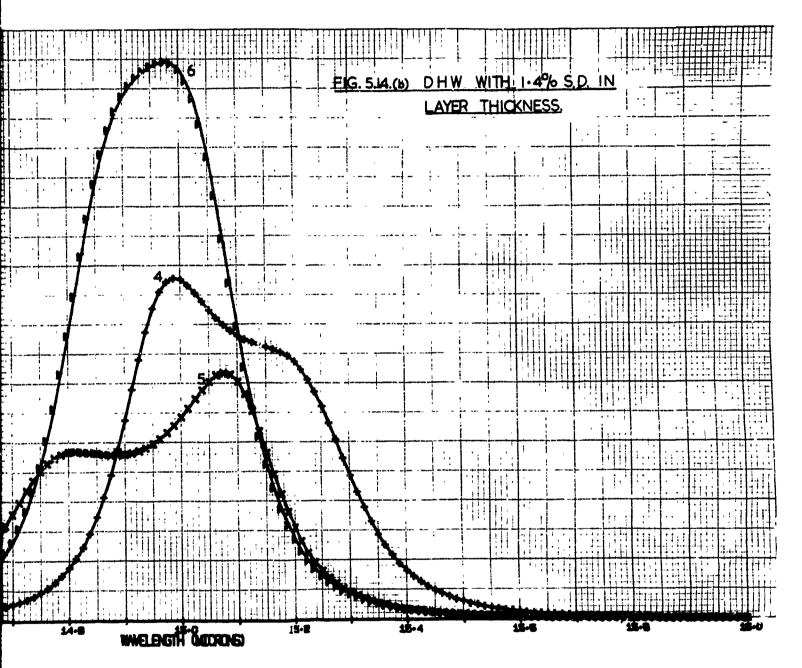
14-LAYER FILTER



A

2.3500

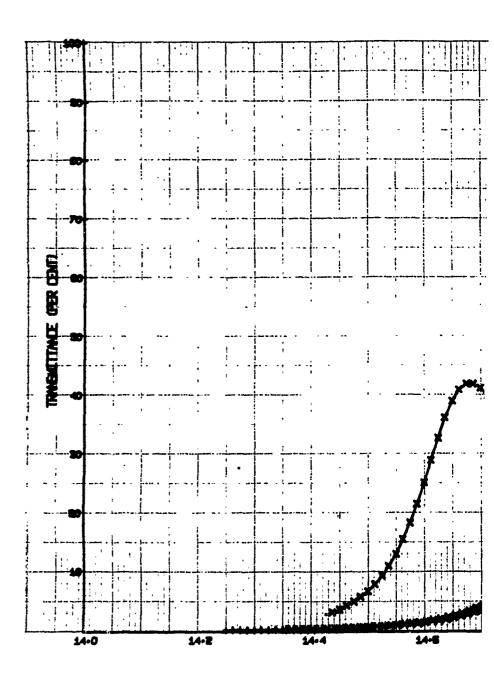
5.3000



B

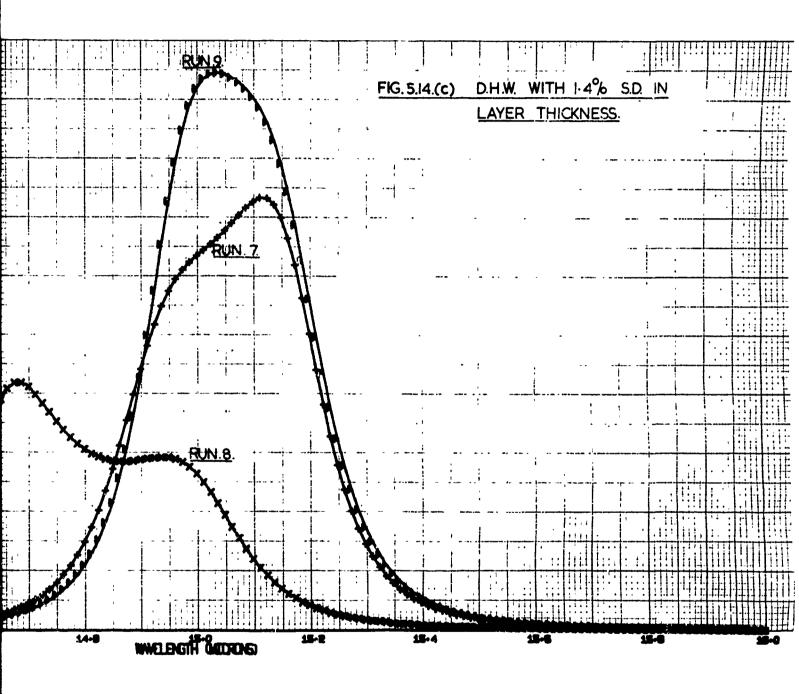
14-LAYER FILTER MONITOR WAVELENGTH: 15.0000 MICRONS RAIR . 1.0000 RSUB* 4.0000 STANDARD DEVIATION: 1.4000 PER CENT CASE NO. LAYER INDEX LAYER THICKNESS 2.3500 0.2495 5.3000 0.2445 2.3500 0.2537 5.3000 0.4981 2.3500 0.2482 5.3000 0.2475 2.3500 0.2540 5.3000 0.2538 2.3500 0.2468 5.3000 0.2505 2.3500 0.2509 5.3000 0.5102 2,3500 0.2419 5.3000 0.2465 CASE NO. LAYER INDEX LAYER THICKNESS 2.3500 0.2513 5.3000 0.2528 2.3500 0.2511 5.3000 0.4991 2.3500 0.2447 5.3000 0.2541 2.3500 0.2497 5.3000 0. 2455 2.3500 5.3009 0.2556 0.2518 2.3500 0.2518 5.3000 0.4831 2.3500 0.2455 5,3000 0.2461 CASE NO. LAYER INDEX LAYER THICKNESS 2.3500 0.2470 5.3000 0.2550 2.3500 0.2528 5.3000 0.5018 2.3500 0.2526 5.3000 0.2510 2.3500 0.2532 5.3000 0.2451 2.3500 0.2477 5.3000 0.2471 2.3500 0.2431 5.3000 0.5068 2.3500 0.2499

0.2466



H

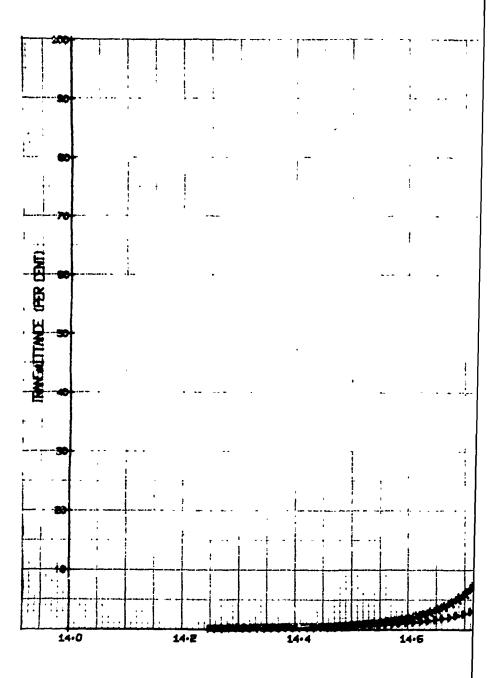
5,3000



MONITOR WAVELENGTH: 15.0000 MICRONS RAIR. 1.0000 4.0000 1.4000 PER CENT STANDARD DEVIATION: CASE NO. LAYER INDEX LAYER THICKNESS 2.3500 0, 2547 5.3000 0,2470 2.3500 0.2532 5,3000 0.5042 2,3500 0,2578 5,3000 0.25282,3500 0.2510 10 5,3000 0.2526 2,3500 0.2434 5,3000 0.2515 2,3500 0.2524 5.3000 2.3500 0.4922 0.2535 5.3000 0.2468 CASE NO. LAYER INDEX LAYER THICKNESS 0, 2538 5.3000 0, 2501 2.3500 0.2496 5,3000 0,5120 2,3500 0,25165,3000 0, 2541 2.3500 0,2563 11 5,3000 0.2477 2.35000, 2495 5,30000.2475 2.3300 0.25245.3000 2.3500 0.49300.2474 0.2515 5,3000 CASE NO. LAYER INDEX LAYER THICKNESS 2.3500 0.2520 0.2522 5.3000 2.3500 0,2522 5.3000 0.5111 2.3500 0.2481 5.3000 2.3500 0.24750.253612 5.3000 0, 2525 2.3500 0.2512 5,3000 0.2462 2,3500 0, 2515 5.30000.4991 2,3500 0.2508

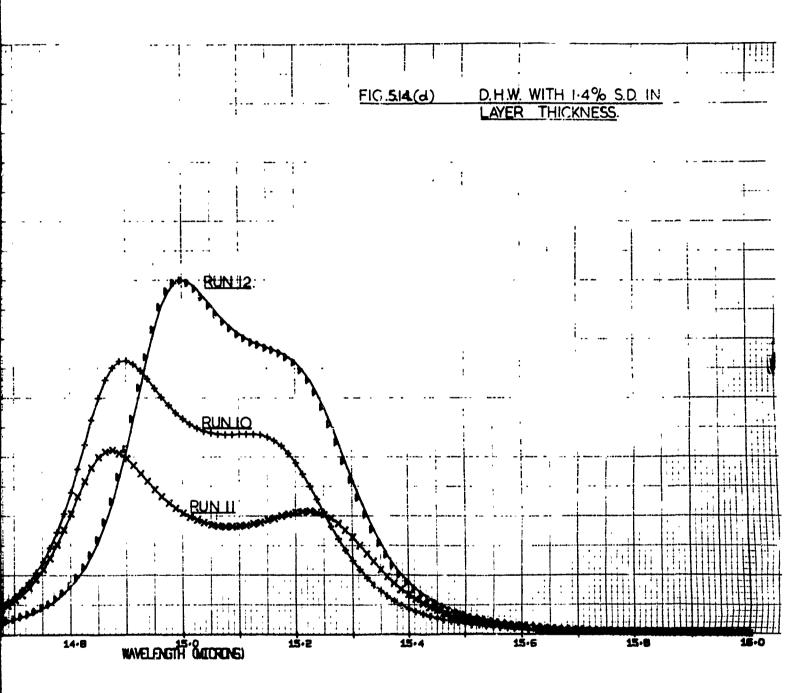
0.2519

14-LAYER FILTER



A

5.3000



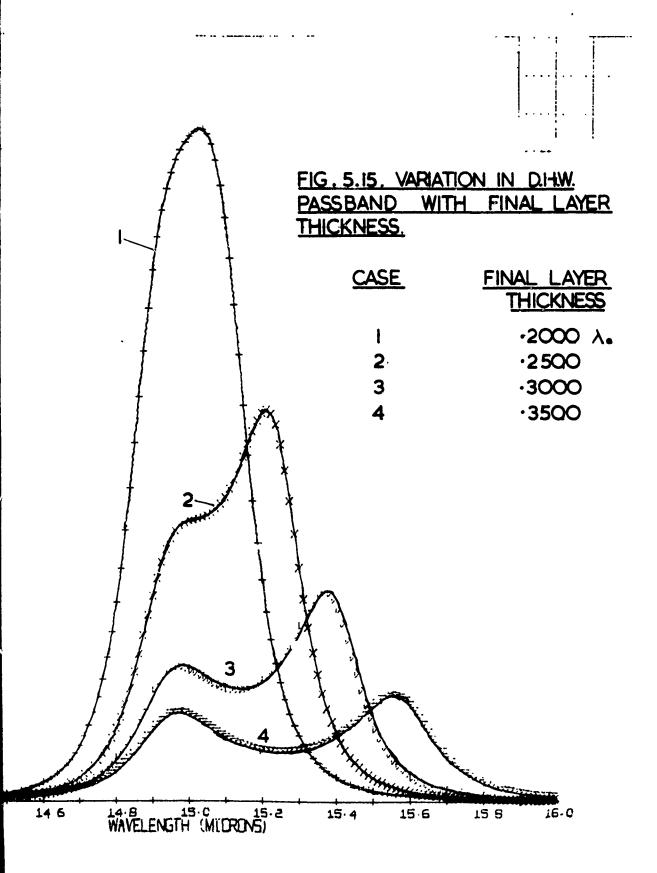
901 BOi. 14-LAYER FILTER MONITOR WAVELENGTH= 14.8200 MICRONS 1.0000 RAIR= RSUB= 4.0000 70i CASE NO. LAYER INDEX LAYER THICKNESS TRANSMITTANCE (PER CENT) 2.3500 0.2454 5.3000 0.2565 E0+ 2.3500 0.2557 5.3000 0.5075 2.3500 0.2467 5.3000 0.2419 2.3500 0.2491 **50**+ 5.3000 0.2492 2.3500 J. 2604 5.3000 0.2478 0.2518 2.3500 5.3000 0.5184 2,3500 0.2564 5.3000 0.2000 (1) (2) 0.2500 (3) 0.3000 0.3500 (4) 30+ **20**+ 10+

14.2

14.4

14 6

F



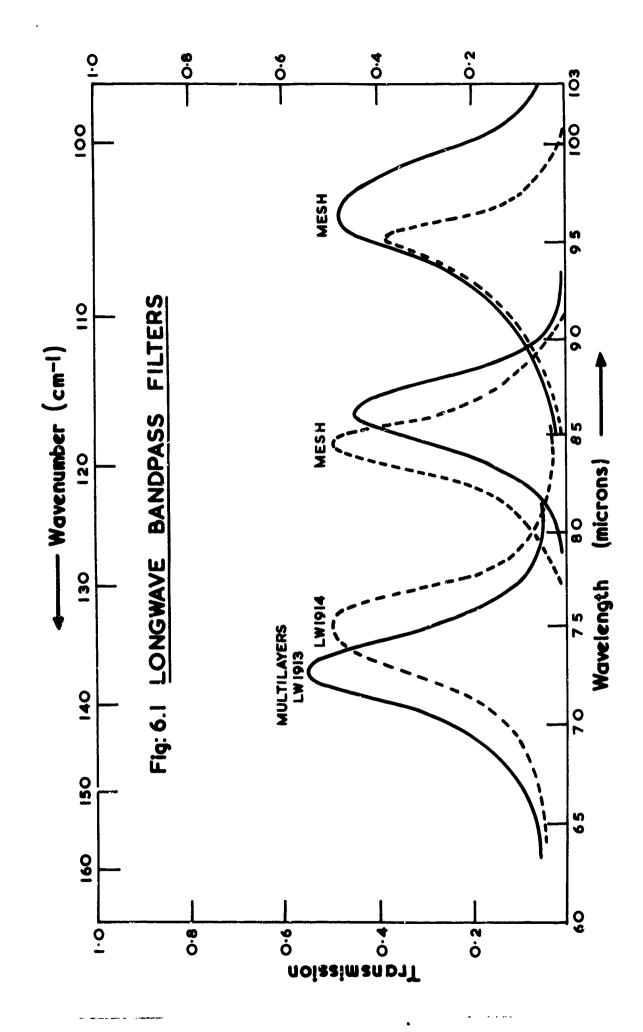
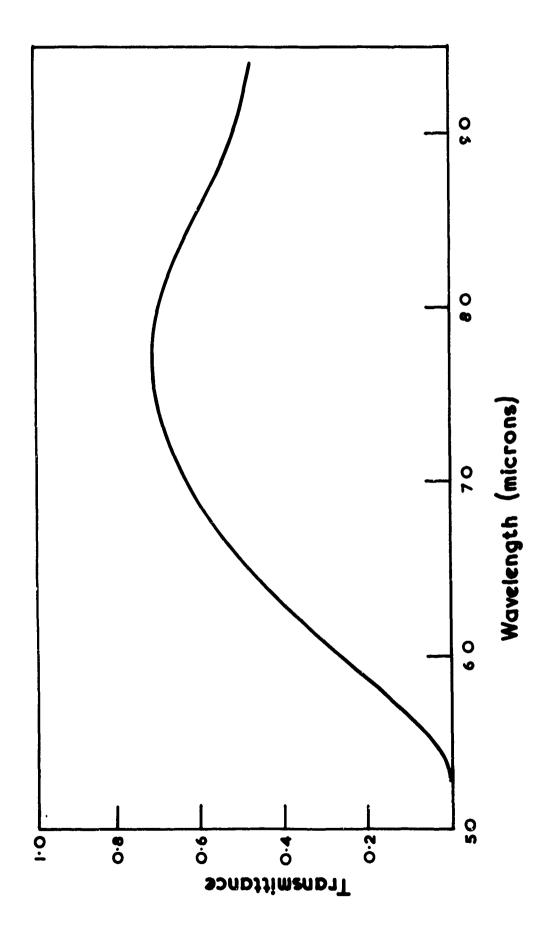


Fig: 6.2 LONGWAVE LOWPASS FILTER



Security Classification			المتاريخ الم	
DOCUMENT	CONTROL DATA - R &	0		
(Security classification of title, boos of abstract and i				
ORIGINATING ACTIVITY (Corporate author)		28. REPORT SECURITY CLASSIFICATION		
Physics Department		Unclassified		
University of Reading Reading, England		26. GROUP		
				REPORT TITLE
" Multilayer Filters for the r	region 0.8 to 100 mi	.crons ^H		
DESCRIPTIVE NOTES (Type of report and inclusive dates)	Scientific	Final.		
AUTHOR(S) (First name, middle initial, last name)	BOATURE TALL	FIUEL.		
S.D. Smith	J.S. Seele	y		
REPORT DATE	T		. NO. OF REFS	
7th May 1968	71927 in Vol.	1	28	
M. CONTRACT OR GRANT NO	Se. ORIGINATOR'S		R(\$)	
AF61(052)-833	Í			
B. PROJECT NO	1			
8662	ŀ			
c.	95, OTHER REPORT		r numbers that may be essioned	
4730		IN THE VOLUMES. AOT. I LEXT SEC LEGISE		
d.		Vol. 2	2 Illustrations	
This document has been approved for unlimited.	public release and	sale; its	distribution is	
II SUPPLEMENTARY NOTES	12 SPONSORING MIT		•	
TECH, OTHER	AIR FORCE (AIR FORCE CAMBRIDGE RESEARCH LABORATORIE		
ibon, ornan	•	L.G. Hanscom Field		
	Bedford, MAS	9 01730		

A study of materials for multilayer evaporated film filters for the region 1-100 μ has yielded several successful high index-low index combinations, notably PbTe/ZnS (5 - 25 μ) and Ge/CsI (10 - 80 μ).

Filters of $\frac{1}{26}$ bandwidth, sentred to $\frac{1}{46}$ can be produced on a routine basis for the $15\,\mu$ region. Band pass filters of 10% bandwidth between 50μ and 100μ have been achieved and evaporated film and mesh techniques have overlapped in the $60\text{--}70\mu$ region. Good blocking filters with edges out to 70μ have also been obtained with performance better than other methods of filtering for this region.

DD FORM .. 1473

INCLASSIVIED
Security Classification

UNCLASSIFIED
Security Classification LINK A LINK B LINK C KEY WORDS ROLE WT ROLE ROLE Multilayer filters, near infra-red, far infra-red, vacuum evaporation, micro-mesh; rediometry, semi-conductors.

UNCLASSIFIED

Security Classification